

# XMC4500

Microcontroller Series  
for Industrial Applications

XMC4000 Family

ARM<sup>®</sup> Cortex<sup>®</sup>-M4  
32-bit processor core

Data Sheet

V1.6 2023-04

Microcontrollers

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<b>118</b>	Table 64: Added package details: PG-LQFP-100-29 and PG-LQFP-144-26. Deleted package details: PG-LQFP-100-11 and PG-LQFP-144-18.
<b>121, 123</b>	Added package diagrams: PG-LQFP-100-29 and PG-LQFP-144-26.
<b>118</b>	Deleted package diagrams: PG-LQFP-100-11 and PG-LQFP-144-18.

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## About this Document

This Data Sheet is addressed to embedded hardware and software developers. It provides the reader with detailed descriptions about the ordering designations, available features, electrical and physical characteristics of the XMC4[12]00 series devices.

The document describes the characteristics of a superset of the XMC4[12]00 series devices. For simplicity, the various device types are referred to by the collective term XMC4[12]00 throughout this manual.

### XMC4000 Family User Documentation

The set of user documentation includes:

- **Reference Manual**
  - describes the functionality of the superset of devices.
- **Data Sheets**
  - list the complete ordering designations, available features and electrical characteristics of derivative devices.
- **Errata Sheets**
  - list deviations from the specifications given in the related Reference Manual or Data Sheets. Errata Sheets are provided for the superset of devices.

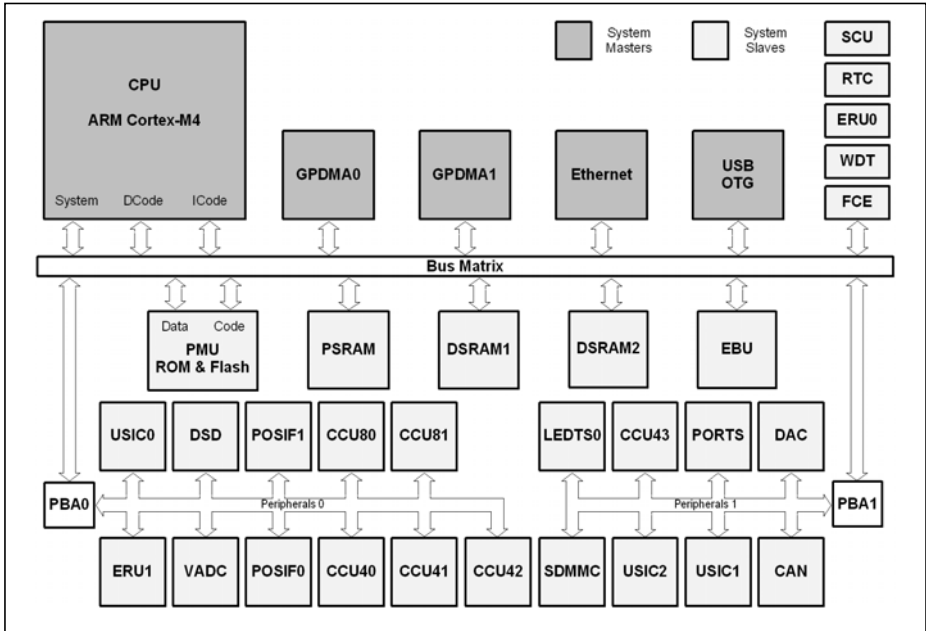
***Attention: Please consult all parts of the documentation set to attain consolidated knowledge about your device.***

Application related guidance is provided by **Users Guides** and **Application Notes**.

Please refer to <http://www.infineon.com/xmc4000> to get access to the latest versions of those documents.

# 1 Summary of Features

The XMC4500 devices are members of the XMC4000 Family of microcontrollers based on the ARM Cortex-M4 processor core. The XMC4000 is a family of high performance and energy efficient microcontrollers optimized for Industrial Connectivity, Industrial Control, Power Conversion, Sense & Control.



**Figure 1 System Block Diagram**



**CPU Subsystem**

- CPU Core
  - High Performance 32-bit ARM Cortex-M4 CPU
  - 16-bit and 32-bit Thumb2 instruction set
  - DSP/MAC instructions
  - System timer (SysTick) for Operating System support
- Floating Point Unit
- Memory Protection Unit
- Nested Vectored Interrupt Controller
- Two General Purpose DMA with up-to 12 channels
- Event Request Unit (ERU) for programmable processing of external and internal service requests
- Flexible CRC Engine (FCE) for multiple bit error detection

**On-Chip Memories**

- 16 KB on-chip boot ROM
- 64 KB on-chip high-speed program memory
- 64 KB on-chip high speed data memory
- 32 KB on-chip high-speed communication
- 1024 KB on-chip Flash Memory with 4 KB instruction cache

**Communication Peripherals**

- Ethernet MAC module capable of 10/100 Mbit/s transfer rates
- Universal Serial Bus, USB 2.0 host, Full-Speed OTG, with integrated PHY
- Controller Area Network interface (MultiCAN), Full-CAN/Basic-CAN with 3 nodes, 64 message objects (MO), data rate up to 1MBit/s
- Six Universal Serial Interface Channels (USIC), providing 6 serial channels, usable as UART, double-SPI, quad-SPI, IIC, IIS and LIN interfaces
- LED and Touch-Sense Controller (LEDTS) for Human-Machine interface
- SD and Multi-Media Card interface (SDMMC) for data storage memory cards
- External Bus Interface Unit (EBU) enabling communication with external memories and off-chip peripherals

**Analog Frontend Peripherals**

- Four Analog-Digital Converters (VADC) of 12-bit resolution, 8 channels each, with input out-of-range comparators
- Delta Sigma Demodulator with four channels, digital input stage for A/D signal conversion
- Digital-Analogue Converter (DAC) with two channels of 12-bit resolution

## Industrial Control Peripherals

- Two Capture/Compare Units 8 (CCU8) for motor control and power conversion
- Four Capture/Compare Units 4 (CCU4) for use as general purpose timers
- Two Position Interfaces (POSIF) for servo motor positioning
- Window Watchdog Timer (WDT) for safety sensitive applications
- Die Temperature Sensor (DTS)
- Real Time Clock module with alarm support
- System Control Unit (SCU) for system configuration and control

## Input/Output Lines

- Programmable port driver control module (PORTS)
- Individual bit addressability
- Tri-stated in input mode
- Push/pull or open drain output mode
- Boundary scan test support over JTAG interface

## On-Chip Debug Support

- Full support for debug features: 8 breakpoints, CoreSight, trace
- Various interfaces: ARM-JTAG, SWD, single wire trace

## 1.1 Ordering Information

The ordering code for an Infineon microcontroller provides an exact reference to a specific product. The code “XMC4<DDD>-<Z><PPP><T><FFFF>” identifies:

- <DDD> the derivatives function set
- <Z> the package variant
  - E: LFBGA
  - F: LQFP
  - Q: VQFN
- <PPP> package pin count
- <T> the temperature range:
  - F: -40°C to 85°C
  - X: -40°C to 105°C
  - K: -40°C to 125°C
- <FFFF> the Flash memory size.

For ordering codes for the XMC4500 please contact your sales representative or local distributor.

This document describes several derivatives of the XMC4500 series, some descriptions may not apply to a specific product.

For simplicity the term **XMC4500** is used for all derivatives throughout this document.

## 1.2 Device Types

These device types are available and can be ordered through Infineon's direct and/or distribution channels.

**Table 1 Synopsis of XMC4500 Device Types**

<b>Derivative<sup>1)</sup></b>	<b>Package</b>	<b>Flash Kbytes</b>	<b>SRAM Kbytes</b>
XMC4500-E144x1024	PG-LFBGA-144	1024	160
XMC4500-F144x1024	PG-LQFP-144	1024	160
XMC4500-F100x1024	PG-LQFP-100	1024	160
XMC4500-F144x768	PG-LQFP-144	768	160
XMC4500-F100x768	PG-LQFP-100	768	160
XMC4502-F100x768	PG-LQFP-100	768	160
XMC4504-F144x512	PG-LQFP-144	512	128
XMC4504-F100x512	PG-LQFP-100	512	128

1) x is a placeholder for the supported temperature range.

### 1.3 Device Type Features

The following table lists the available features per device type.

**Table 2 Features of XMC4500 Device Types**

Derivative <sup>1)</sup>	LEDTS Intf.	SDMMC Intf.	EBU Intf. <sup>2)</sup>	ETH Intf. <sup>3)</sup>	USB Intf.	USIC Chan.	MultiCAN Nodes, MO
XMC4500-E144x1024	1	1	SDM	MR	1	3 x 2	N0, N1, N2 MO[0..63]
XMC4500-F144x1024	1	1	SDM	MR	1	3 x 2	N0, N1, N2 MO[0..63]
XMC4500-F100x1024	1	1	M16	R	1	3 x 2	N0, N1, N2 MO[0..63]
XMC4500-F144x768	1	1	SDM	MR	1	3 x 2	N0, N1, N2 MO[0..63]
XMC4500-F100x768	1	1	M16	R	1	3 x 2	N0, N1, N2 MO[0..63]
XMC4502-F100x768	1	1	M16	-	1	3 x 2	N0, N1, N2 MO[0..63]
XMC4504-F144x512	1	1	SDM	-	-	3 x 2	-
XMC4504-F100x512	1	1	M16	-	-	3 x 2	-

1) x is a placeholder for the supported temperature range.

2) Memory types supported S=SDRAM, D=DEMUX, M=MUX 16-bit and 32-bit, M16=MUX 16-bit

3) Supported interfaces, M=MII, R=RMII.

**Table 3 Features of XMC4500 Device Types**

<b>Derivative<sup>1)</sup></b>	<b>ADC Chan.</b>	<b>DSD Chan.</b>	<b>DAC Chan.</b>	<b>CCU4 Slice</b>	<b>CCU8 Slice</b>	<b>POSIF Intf.</b>
XMC4500-E144x1024	32	4	2	4 x 4	2 x 4	2
XMC4500-F144x1024	32	4	2	4 x 4	2 x 4	2
XMC4500-F100x1024	24	4	2	4 x 4	2 x 4	2
XMC4500-F144x768	32	4	2	4 x 4	2 x 4	2
XMC4500-F100x768	24	4	2	4 x 4	2 x 4	2
XMC4502-F100x768	24	4	2	4 x 4	2 x 4	2
XMC4504-F144x512	32	4	2	4 x 4	2 x 4	2
XMC4504-F100x512	24	4	2	4 x 4	2 x 4	2

1) x is a placeholder for the supported temperature range.

## 1.4 Definition of Feature Variants

The XMC4500 types are offered with several memory sizes and number of available VADC channels. **Table 4** describes the location of the available Flash memory, **Table 5** describes the location of the available SRAMs, **Table 6** the available VADC channels.

**Table 4 Flash Memory Ranges**

Total Flash Size	Cached Range	Uncached Range
512 Kbytes	0800 0000 <sub>H</sub> – 0807 FFFF <sub>H</sub>	0C00 0000 <sub>H</sub> – 0C07 FFFF <sub>H</sub>
768 Kbytes	0800 0000 <sub>H</sub> – 080B FFFF <sub>H</sub>	0C00 0000 <sub>H</sub> – 0C0B FFFF <sub>H</sub>
1,024 Kbytes	0800 0000 <sub>H</sub> – 080F FFFF <sub>H</sub>	0C00 0000 <sub>H</sub> – 0C0F FFFF <sub>H</sub>

**Table 5 SRAM Memory Ranges**

Total SRAM Size	Program SRAM	System Data SRAM	Communication Data SRAM
128 Kbytes	1000 0000 <sub>H</sub> – 1000 FFFF <sub>H</sub>	2000 0000 <sub>H</sub> – 2000 FFFF <sub>H</sub>	–
160 Kbytes	1000 0000 <sub>H</sub> – 1000 FFFF <sub>H</sub>	2000 0000 <sub>H</sub> – 2000 FFFF <sub>H</sub>	3000 0000 <sub>H</sub> – 3000 7FFF <sub>H</sub>

**Table 6 ADC Channels<sup>1)</sup>**

Package	VADC G0	VADC G1	VADC G2	VADC G3
PG-LQFP-144 PG-LFBGA-144	CH0..CH7	CH0..CH7	CH0..CH7	CH0..CH7
PG-LQFP-100	CH0..CH7	CH0..CH7	CH0..CH3	CH0..CH3

1) Some pins in a package may be connected to more than one channel. For the detailed mapping see the Port I/O Function table.

## 1.5 Identification Registers

The identification registers allow software to identify the marking.

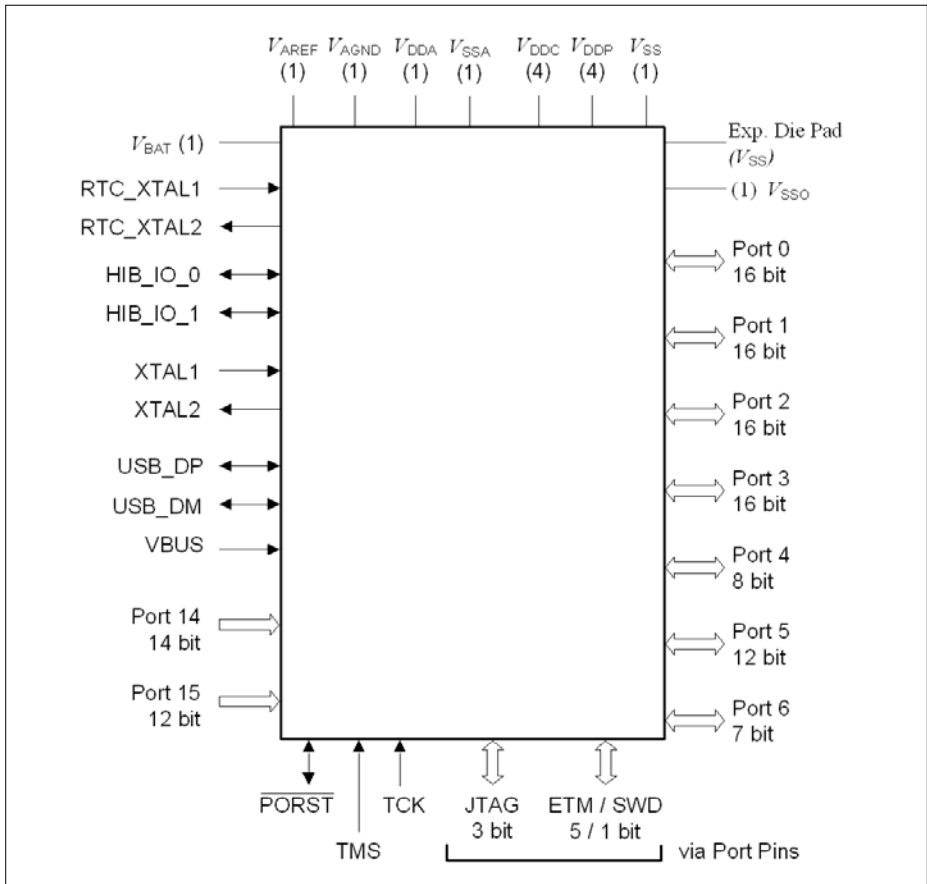
**Table 7 XMC4500 Identification Registers**

<b>Register Name</b>	<b>Value</b>	<b>Marking</b>
SCU_IDCHIP	0004 5002 <sub>H</sub>	EES-AA, ES-AA
SCU_IDCHIP	0004 5003 <sub>H</sub>	ES-AB, AB
SCU_IDCHIP	0004 5004 <sub>H</sub>	AC
JTAG IDCODE	101D B083 <sub>H</sub>	EES-AA, ES-AA
JTAG IDCODE	101D B083 <sub>H</sub>	ES-AB, AB
JTAG IDCODE	401D B083 <sub>H</sub>	AC

## 2 General Device Information

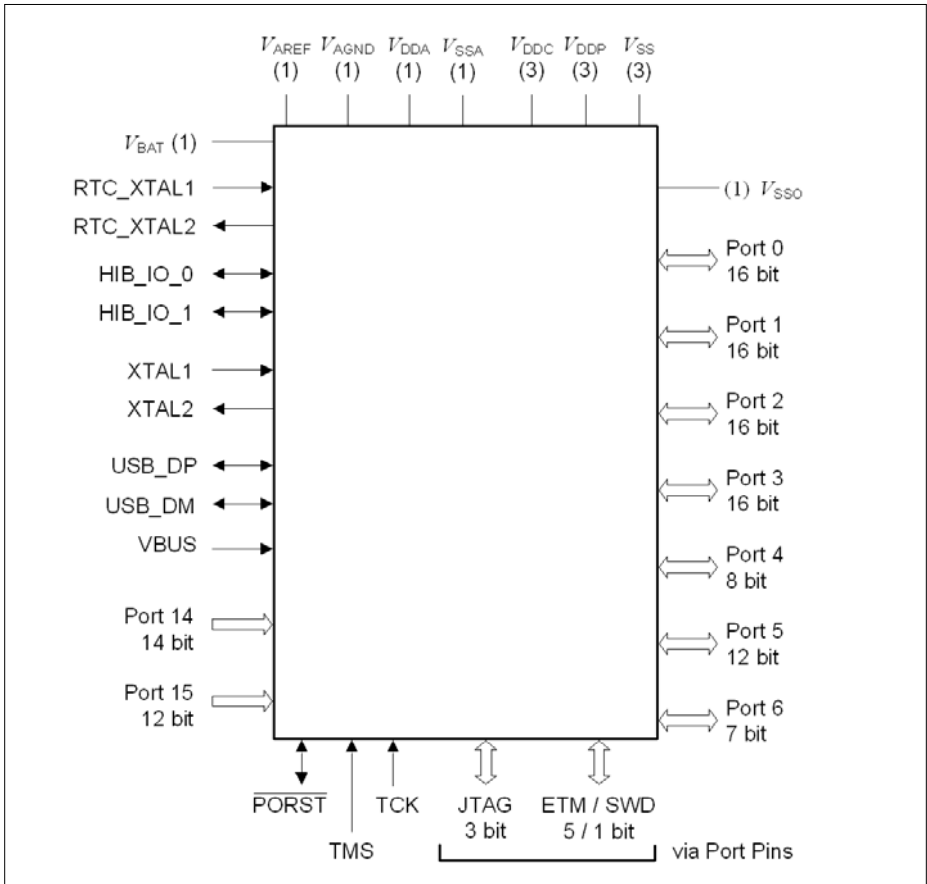
This section summarizes the logic symbols and package pin configurations with a detailed list of the functional I/O mapping.

### 2.1 Logic Symbols

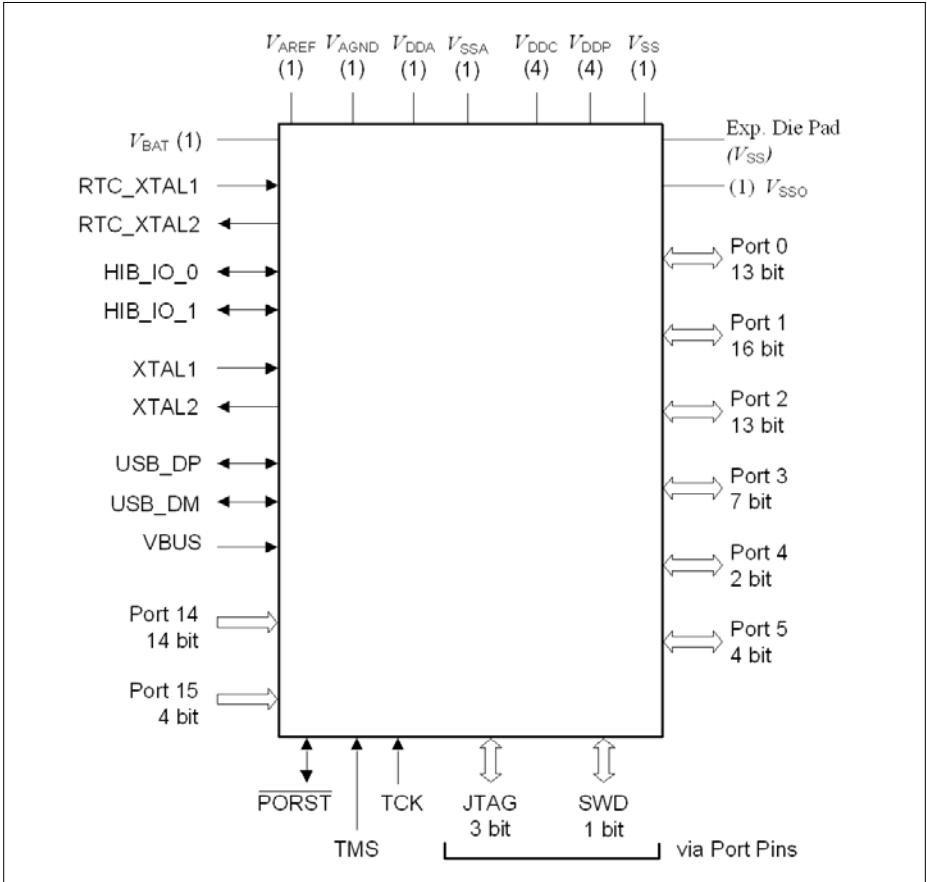


**Figure 2 XMC4500 Logic Symbol PG-LQFP-144**





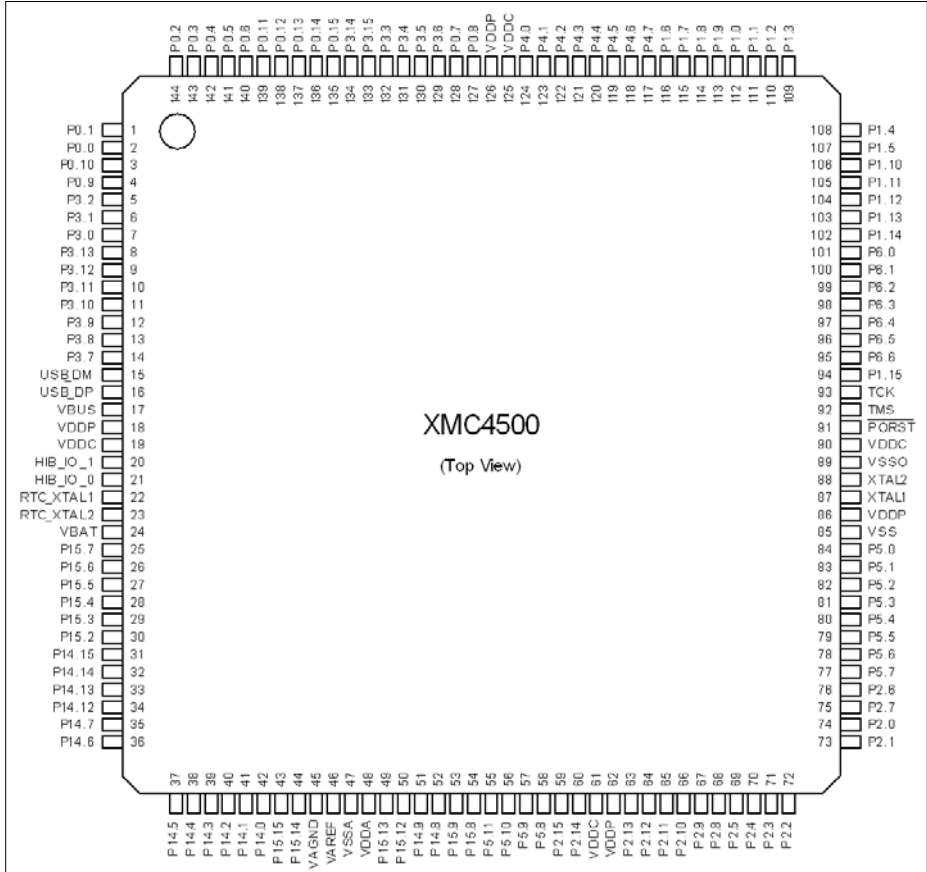
**Figure 3 XMC4500 Logic Symbol PG-LFBGA-144**



**Figure 4 XMC4500 Logic Symbol PG-LQFP-100**

## 2.2 Pin Configuration and Definition

The following figures summarize all pins, showing their locations on the four sides of the different packages.



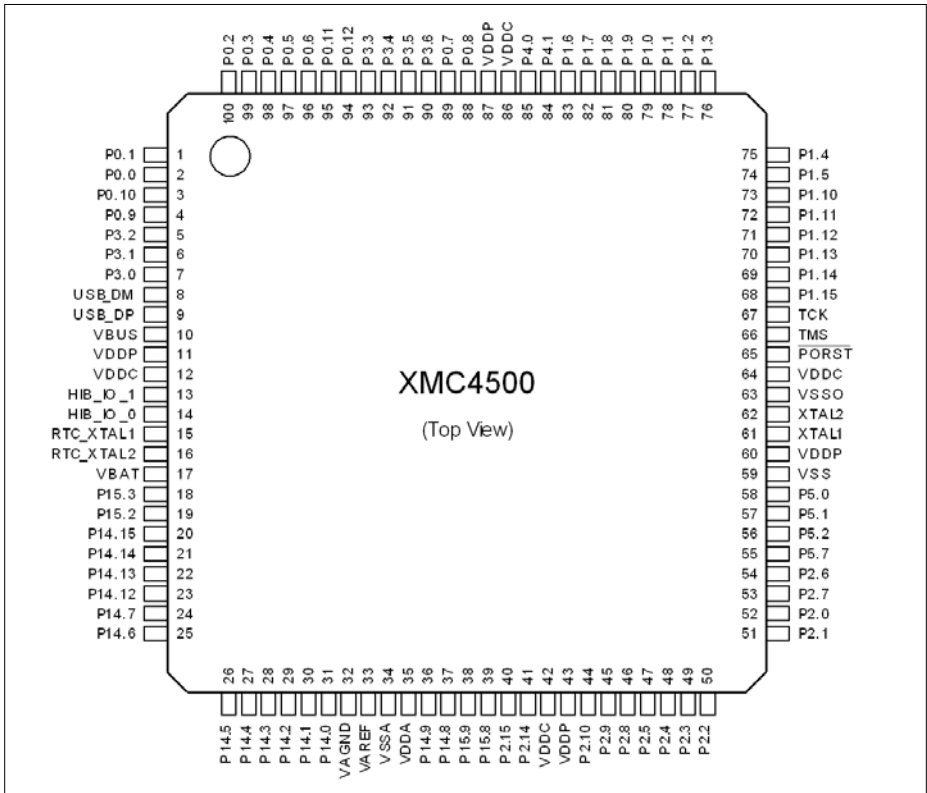
**Figure 5 XMC4500 PG-LQFP-144 Pin Configuration (top view)**

**General Device Information**

	1	2	3	4	5	6	7	8	9	10	11	12	
A	VSS	VDDC	P0.2	P0.3	P0.5	P0.6	P3.6	P0.8	P4.1	P1.8	VDDP	VSS	A
B	VDDP	P3.1	P3.2	P0.10	P0.4	P3.5	P0.7	P4.0	P1.6	P1.7	P1.9	VDDC	B
C	P3.0	P3.13	P0.1	P0.0	P0.13	P0.15	P4.4	P4.6	P4.7	P1.4	P1.2	P1.3	C
D	USB_D M	P3.12	P3.11	P0.9	P0.12	P3.14	P3.15	P4.5	P1.0	P1.5	P1.11	P1.10	D
E	USB_D P	VBUS	P3.8	P3.7	P0.11	P0.14	P3.4	P4.2	P1.1	P1.14	P1.12	P1.13	E
F	RTC_X TAL2	RTC_X TAL1	HB_I O_1	HB_I O_0	P3.9	P3.10	P3.3	P4.3	P6.1	P6.4	P6.5	P6.6	F
G	VBAT	P15.3	P15.5	P15.4	P15.6	P15.7	TMS	TCK	P6.3	P6.0	$\overline{\text{PORST}}$	P1.15	G
H	P15.2	P14.15	P14.14	P14.13	P5.10	P5.8	P5.2	P5.1	P5.0	P6.2	XTAL1	XTAL2	H
J	P14.12	P14.7	P14.6	P14.3	P5.11	P2.15	P5.7	P5.5	P2.6	P5.3	P2.0	VSSO	J
K	P14.4	P14.5	P14.2	P15.15	P15.12	P5.9	P2.14	P5.6	P2.7	P5.4	P2.2	P2.1	K
L	VDDA	P14.1	P14.0	P15.14	P14.9	P15.9	P2.12	P2.10	P2.8	P2.4	P2.3	VDDP	L
M	VSSA	VAGND	VAREF	P15.13	P14.8	P15.8	P2.13	P2.11	P2.9	P2.5	VDDC	VSS	M
	1	2	3	4	5	6	7	8	9	10	11	12	

XMC4500- (top view)

**Figure 6 XMC4500 PG-LFBGA-144 Pin Configuration (top view)**



**Figure 7 XMC4500 PG-LQFP-100 Pin Configuration (top view)**

### 2.2.1 Package Pin Summary

The following general scheme is used to describe each pin:

**Table 8 Package Pin Mapping Description**

Function	Package A	Package B	...	Pad Type	Notes
Name	N	Ax	...	A2	

The table is sorted by the “Function” column, starting with the regular Port pins (Px.y), followed by the dedicated pins (i.e.  $\overline{\text{PORST}}$ ) and supply pins.

The following columns, titled with the supported package variants, lists the package pin number to which the respective function is mapped in that package.

The “Pad Type” indicates the employed pad type (A1, A1+, A2, special=special pad, In=input pad, AN/DIG\_IN=analog and digital input, Power=power supply). Details about the pad properties are defined in the Electrical Parameters.

In the “Notes”, special information to the respective pin/function is given, i.e. deviations from the default configuration after reset. Per default the regular Port pins are configured as direct input with no internal pull device active.

**Table 9 Package Pin Mapping**

Function	LQFP-144	LFBGA-144	LQFP-100	Pad Type	Notes
P0.0	2	C4	2	A1+	
P0.1	1	C3	1	A1+	
P0.2	144	A3	100	A2	
P0.3	143	A4	99	A2	
P0.4	142	B5	98	A2	
P0.5	141	A5	97	A2	
P0.6	140	A6	96	A2	
P0.7	128	B7	89	A2	After a system reset, via HWSEL this pin selects the DB.TDI function.
P0.8	127	A8	88	A2	After a system reset, via HWSEL this pin selects the $\overline{\text{DB.TRST}}$ function, with a weak pull-down active.
P0.9	4	D4	4	A2	
P0.10	3	B4	3	A1+	

**General Device Information**

**Table 9 Package Pin Mapping (cont'd)**

Function	LQFP-144	LFBGA-144	LQFP-100	Pad Type	Notes
P0.11	139	E5	95	A1+	
P0.12	138	D5	94	A1+	
P0.13	137	C5	-	A1+	
P0.14	136	E6	-	A1+	
P0.15	135	C6	-	A1+	
P1.0	112	D9	79	A1+	
P1.1	111	E9	78	A1+	
P1.2	110	C11	77	A2	
P1.3	109	C12	76	A2	
P1.4	108	C10	75	A1+	
P1.5	107	D10	74	A1+	
P1.6	116	B9	83	A2	
P1.7	115	B10	82	A2	
P1.8	114	A10	81	A2	
P1.9	113	B11	80	A2	
P1.10	106	D12	73	A1+	
P1.11	105	D11	72	A1+	
P1.12	104	E11	71	A2	
P1.13	103	E12	70	A2	
P1.14	102	E10	69	A2	
P1.15	94	G12	68	A2	
P2.0	74	J11	52	A2	
P2.1	73	K12	51	A2	After a system reset, via HWSEL this pin selects the DB.TDO function.
P2.2	72	K11	50	A2	
P2.3	71	L11	49	A2	
P2.4	70	L10	48	A2	
P2.5	69	M10	47	A2	
P2.6	76	J9	54	A1+	
P2.7	75	K9	53	A1+	
P2.8	68	L9	46	A2	
P2.9	67	M9	45	A2	

**General Device Information**

**Table 9 Package Pin Mapping (cont'd)**

Function	LQFP-144	LFBGA-144	LQFP-100	Pad Type	Notes
P2.10	66	L8	44	A2	
P2.11	65	M8	-	A2	
P2.12	64	L7	-	A2	
P2.13	63	M7	-	A2	
P2.14	60	K7	41	A2	
P2.15	59	J6	40	A2	
P3.0	7	C1	7	A2	
P3.1	6	B2	6	A2	
P3.2	5	B3	5	A2	
P3.3	132	F7	93	A1+	
P3.4	131	E7	92	A1+	
P3.5	130	B6	91	A2	
P3.6	129	A7	90	A2	
P3.7	14	E4	-	A1+	
P3.8	13	E3	-	A1+	
P3.9	12	F5	-	A1+	
P3.10	11	F6	-	A1+	
P3.11	10	D3	-	A1+	
P3.12	9	D2	-	A2	
P3.13	8	C2	-	A2	
P3.14	134	D6	-	A1+	
P3.15	133	D7	-	A1+	
P4.0	124	B8	85	A2	
P4.1	123	A9	84	A2	
P4.2	122	E8	-	A1+	
P4.3	121	F8	-	A1+	
P4.4	120	C7	-	A1+	
P4.5	119	D8	-	A1+	
P4.6	118	C8	-	A1+	
P4.7	117	C9	-	A1+	
P5.0	84	H9	58	A1+	
P5.1	83	H8	57	A1+	
P5.2	82	H7	56	A1+	



**General Device Information**

**Table 9 Package Pin Mapping (cont'd)**

Function	LQFP-144	LFBGA-144	LQFP-100	Pad Type	Notes
P5.3	81	J10	-	A2	
P5.4	80	K10	-	A2	
P5.5	79	J8	-	A2	
P5.6	78	K8	-	A2	
P5.7	77	J7	55	A1+	
P5.8	58	H6	-	A2	
P5.9	57	K6	-	A2	
P5.10	56	H5	-	A1+	
P5.11	55	J5	-	A1+	
P6.0	101	G10	-	A2	
P6.1	100	F9	-	A2	
P6.2	99	H10	-	A2	
P6.3	98	G9	-	A1+	
P6.4	97	F10	-	A2	
P6.5	96	F11	-	A2	
P6.6	95	F12	-	A2	
P14.0	42	L3	31	AN/DIG_IN	
P14.1	41	L2	30	AN/DIG_IN	
P14.2	40	K3	29	AN/DIG_IN	
P14.3	39	J4	28	AN/DIG_IN	
P14.4	38	K1	27	AN/DIG_IN	
P14.5	37	K2	26	AN/DIG_IN	
P14.6	36	J3	25	AN/DIG_IN	
P14.7	35	J2	24	AN/DIG_IN	
P14.8	52	M5	37	AN/DAC/DI G_IN	
P14.9	51	L5	36	AN/DAC/DI G_IN	
P14.12	34	J1	23	AN/DIG_IN	
P14.13	33	H4	22	AN/DIG_IN	
P14.14	32	H3	21	AN/DIG_IN	
P14.15	31	H2	20	AN/DIG_IN	
P15.2	30	H1	19	AN/DIG_IN	

**General Device Information**
**Table 9 Package Pin Mapping (cont'd)**

Function	LQFP-144	LFBGA-144	LQFP-100	Pad Type	Notes
P15.3	29	G2	18	AN/DIG_IN	
P15.4	28	G4	-	AN/DIG_IN	
P15.5	27	G3	-	AN/DIG_IN	
P15.6	26	G5	-	AN/DIG_IN	
P15.7	25	G6	-	AN/DIG_IN	
P15.8	54	M6	39	AN/DIG_IN	
P15.9	53	L6	38	AN/DIG_IN	
P15.12	50	K5	-	AN/DIG_IN	
P15.13	49	M4	-	AN/DIG_IN	
P15.14	44	L4	-	AN/DIG_IN	
P15.15	43	K4	-	AN/DIG_IN	
USB_DP	16	E1	9	special	
USB_DM	15	D1	8	special	
HIB_IO_0	21	F4	14	A1 special	At the first power-up and with every reset of the hibernate domain this pin is configured as open-drain output and drives "0". As output the medium driver mode is active.
HIB_IO_1	20	F3	13	A1 special	At the first power-up and with every reset of the hibernate domain this pin is configured as input with no pull device active. As output the medium driver mode is active.
TCK	93	G8	67	A1	Weak pull-down active.
TMS	92	G7	66	A1+	Weak pull-up active. As output the strong-soft driver mode is active.
PORST	91	G11	65	special	Weak pull-up permanently active, strong pull-down controlled by EVR.
XTAL1	87	H11	61	clock_IN	
XTAL2	88	H12	62	clock_O	

**General Device Information**

**Table 9 Package Pin Mapping (cont'd)**

Function	LQFP-144	LFBGA-144	LQFP-100	Pad Type	Notes
RTC_XTAL1	22	F2	15	clock_IN	
RTC_XTAL2	23	F1	16	clock_O	
VBAT	24	G1	17	Power	When VDDP is supplied VBAT has to be supplied as well.
VBUS	17	E2	10	special	
VAREF	46	M3	33	AN_Ref	
VAGND	45	M2	32	AN_Ref	
VDDA	48	L1	35	AN_Power	
VSSA	47	M1	34	AN_Power	
VDDC	19	-	12	Power	
VDDC	61	-	42	Power	
VDDC	90	-	64	Power	
VDDC	125	-	86	Power	
VDDC	-	A2	-	Power	
VDDC	-	B12	-	Power	
VDDC	-	M11	-	Power	
VDDP	18	-	11	Power	
VDDP	62	-	43	Power	
VDDP	86	-	60	Power	
VDDP	126	-	87	Power	
VDDP	-	A11	-	Power	
VDDP	-	B1	-	Power	
VDDP	-	L12	-	Power	
VSS	85	-	59	Power	
VSS	-	A1	-	Power	
VSS	-	A12	-	Power	
VSS	-	M12	-	Power	

**General Device Information**

**Table 9 Package Pin Mapping (cont'd)**

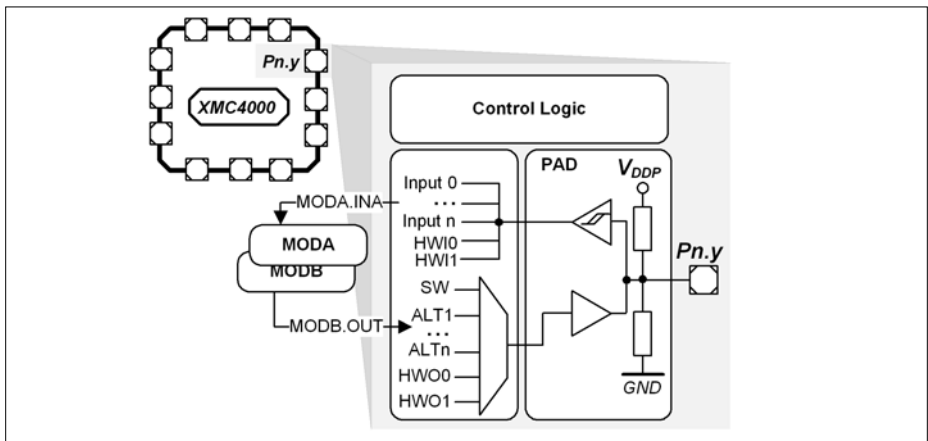
Function	LQFP-144	LFBGA-144	LQFP-100	Pad Type	Notes
VSSO	89	J12	63	Power	
VSS	Exp. Pad	-	Exp. Pad	Power	<p><b>Exposed Die Pad</b> The exposed die pad is connected internally to VSS. For proper operation, it is mandatory to connect the exposed pad directly to the common ground on the board. For thermal aspects, please refer to the Data Sheet. Board layout examples are given in an application note.</p>

### 2.2.2 Port I/O Functions

The following general scheme is used to describe each Port pin:

**Table 10 Port I/O Function Description**

Function	Outputs			Inputs		
	ALT1	ALTn	HWO0	HWI0	Input	Input
P0.0		MODA.OUT	MODB.OUT	MODB.INA	MODC.INA	
Pn.y	MODA.OUT				MODA.INA	MODC.INB



**Figure 8 Simplified Port Structure**

Pn.y is the port pin name, defining the control and data bits/registers associated with it. As GPIO, the port is under software control. Its input value is read via Pn\_IN.y, Pn\_OUT defines the output value.

Up to four alternate output functions (ALT1/2/3/4) can be mapped to a single port pin, selected by Pn\_IOCR.PC. The output value is directly driven by the respective module, with the pin characteristics controlled by the port registers (within the limits of the connected pad).

The port pin input can be connected to multiple peripherals. Most peripherals have an input multiplexer to select between different possible input sources.

The input path is also active while the pin is configured as output. This allows to feedback an output to on-chip resources without wasting an additional external pin.

By Pn\_HWSEL it is possible to select between different hardware “masters” (HWO0/HWI0, HWO1/HWI1). The selected peripheral can take control of the pin(s). Hardware control overrules settings in the respective port pin registers.

## 2.2.2.1 Port I/O Function Table

**Table 11 Port I/O Functions**

Function	Outputs						Inputs									
	ALT1	ALT2	ALT3	ALT4	HWC0	HWC1	HWC0	HWC1	HW11	Input	Input	Input	Input	Input	Input	
P0.0		CAN_ML7XD	CC180_OUT12	LED7S0_C0L2						U1C1_DX0D	ETH0_CK1_RMIB	ERL0_0B0			ETH0_CK1_RMIB	
P0.1	USB_DRV6V/BUS	U1C1_DOU70	CC180_OUT11	LED7S0_C0L3						ETH0_CRS_DVB	ERL0_0A0	ERL0_0A0			ETH0_RXD7B	
P0.2		U1C1_SEL01	CC180_OUT10		U1C0_DOU73	ERL1_A09	U1C0_HWN3	ERL1_D0	ERL1_RXD0B		ERL1_3B3	ERL1_3B3				
P0.3		CC180_OUT20	CC180_OUT19		U1C0_DOU72	ERL1_A08	U1C0_HWN2	ERL1_DX0D	ERL1_RXD1B		ERL1_3B0	ERL1_3B0				
P0.4	ETH0_TALEN		CC180_OUT18		U1C0_DOU71	ERL1_A07	U1C0_HWN1	ERL1_D0	ERL1_RXD2B	U1C0_D0XA	ERL0_2D5	ERL0_2D5				
P0.5	ETH0_T0D0	U1C0_DOU70	CC180_OUT17		U1C0_DOU70	ERL1_A05	U1C0_HWN0	ERL1_D3	ERL1_DX0B	U1C0_DX0B	ERL1_5A0	ERL1_5A0				
P0.6	ETH0_T0D1	U1C0_SEL00	CC180_OUT16		ER1_A07	ERL1_A07				U1C0_DX2A	ERL0_3B2	ERL0_3B2	CC180_N2B			CC180_N2B
P0.7	WWDT_SERVICE_OUT	U1C0_SEL00	CC180_OUT15		U1C0_A06	ERL1_A06	DB	ERL1_D6	U1C0_DX2B	DS0_DIN1A	ERL0_2B1	ERL0_2B1	CC180_N2A	CC180_N2A	CC180_N2A	CC180_N2A
P0.8	SQU_EXCLK	U1C0_SCLK_OUT	CC180_OUT14		ER1_A07	ERL1_A07	TRST	ERL1_D7	U1C0_DX1B	DS0_DIN1A	ERL0_2A1	ERL0_2A1	CC180_N1B			
P0.9		U1C1_SEL00	CC180_OUT12	LED7S0_C0L0	ETH0_M0S	ER1_A07	SDPA	ERL1_D0	U1C1_DX0A	USB_D	ERL0_5B1	ERL0_5B1				
P0.10	ETH0_M0C	U1C1_SCLK_OUT	CC180_OUT11	LED7S0_C0L1					U1C1_DX1A	U1C1_DX1A	ERL0_1A0	ERL0_1A0				
P0.11		U1C0_SCLK_OUT	CC180_OUT10		SDMMC_RST	ER1_BREQ			ETH0_RXERR	U1C0_DX1A	ERL0_3A2	ERL0_3A2	CC180_N2A			
P0.12		U1C1_SEL00	CC180_OUT9		ER1_HELD	ER1_HELD				U1C1_DX2B	ERL0_2B2	ERL0_2B2				
P0.13		U1C1_SCLK_OUT	CC180_OUT8						U1C1_DX1B	U1C1_DX1B	ERL0_2A2	ERL0_2A2				
P0.14		U1C0_SEL00	CC180_OUT7		U1C1_DOU73		U1C1_HWN3				CC180_N2C	CC180_N2C				
P0.15		U1C0_SEL00	CC180_OUT6		U1C1_DOU72		U1C1_HWN2				CC180_N2C	CC180_N2C				
P1.0	DS0_CSPWM1	U1C0_SEL00	CC180_OUT5	ERL1_PDOUT3					U1C0_DX0A	U1C0_DX0A	ERL0_3B0	ERL0_3B0	CC180_N2A			
P1.1	DS0_CSPWMP	U1C0_SCLK_OUT	CC180_OUT4	ERL1_PDOUT2	SDMMC_SDWC				U1C0_DX1A	POSREF0_N2A	ERL0_N2A	ERL0_N2A	CC180_N2A			
P1.2		U1C0_SEL00	CC180_OUT3	ERL1_PDOUT1	U1C0_A04	ERL1_D14	U1C0_HWN3	ERL1_D14	POSREF0_N1A	POSREF0_N1A	ERL1_2B0	ERL1_2B0	CC180_N1A			
P1.3		U1C0_MCLK_OUT	CC180_OUT2	ERL1_PDOUT0	U1C0_A05	ERL1_D15	U1C0_HWN2	ERL1_D15	POSREF0_N2A	POSREF0_N2A	ERL1_2A0	ERL1_2A0	CC180_N2A			
P1.4	WWDT_SERVICE_OUT	CAN_ML7XD	CC180_OUT1	COB1_OUT1B	U1C0_DOU71		U1C0_HWN1	U1C0_DOU71	U1C0_DX0B	CAN_PL3_RXD0	ERL0_2B5	ERL0_2B5	CC180_N1C			CC180_N1C

**Table 11** Port I/O Functions (cont'd)

Function	Outputs					Inputs										
	AL71	AL72	AL73	AL74	HW00	HW01	HW10	HW11	Input	Input	Input	Input	Input	Input	Input	Input
P1.5	CAN_NL_TXD	UC03_DOUT0	CC081_OUT10	UC03_DOUT0	UC03_DOUT0	UC03_DOUT0	UC03_HW10	UC03_DOUT0	UC03_DOUT0	CAN_NL_RXDA	ERU0_ZAD	ERU1_GAO	CC041_NVIC	DS0_DIN2B		
P1.6	UC03_SCKOUT	UC03_SCKOUT	DS0_MCLK2	DS0_MCLK2	DS0_MCLK2	DS0_MCLK2	DS0_MCLK2	DS0_MCLK2	DS0_MCLK2	DS0_MCLK2						
P1.7	UC03_SEL0	UC03_SEL0	UC03_SEL0	UC03_SEL0	UC03_SEL0	UC03_SEL0	UC03_SEL0	UC03_SEL0	UC03_SEL0	UC03_SEL0						
P1.8	UC03_SEL1	UC03_SEL1	UC03_SEL1	UC03_SEL1	UC03_SEL1	UC03_SEL1	UC03_SEL1	UC03_SEL1	UC03_SEL1	UC03_SEL1						
P1.9	UC03_SEL2	UC03_SEL2	UC03_SEL2	UC03_SEL2	UC03_SEL2	UC03_SEL2	UC03_SEL2	UC03_SEL2	UC03_SEL2	UC03_SEL2						
P1.10	ETH0_MDC	UC03_SCKOUT	CC081_OUT11	UC03_SCKOUT	UC03_SCKOUT	UC03_SCKOUT	UC03_SCKOUT	UC03_SCKOUT	UC03_SCKOUT	UC03_SCKOUT						
P1.11	ETH0_SEL0	UC03_SEL0	UC03_SEL0	UC03_SEL0	UC03_SEL0	UC03_SEL0	UC03_SEL0	UC03_SEL0	UC03_SEL0	UC03_SEL0						
P1.12	ETH0_TX_EN	UC03_NL_TXD	CC081_OUT12	UC03_NL_TXD	UC03_NL_TXD	UC03_NL_TXD	UC03_NL_TXD	UC03_NL_TXD	UC03_NL_TXD	UC03_NL_TXD						
P1.13	ETH0_TXD0	UC03_SEL0	UC03_OUT10	UC03_SEL0	UC03_SEL0	UC03_SEL0	UC03_SEL0	UC03_SEL0	UC03_SEL0	UC03_SEL0						
P1.14	ETH0_TXD1	UC03_SEL1	UC03_OUT11	UC03_SEL1	UC03_SEL1	UC03_SEL1	UC03_SEL1	UC03_SEL1	UC03_SEL1	UC03_SEL1						
P1.15	SCU_EXCLK	DS0_MCLK2	CC081_OUT13	DS0_MCLK2	DS0_MCLK2	DS0_MCLK2	DS0_MCLK2	DS0_MCLK2	DS0_MCLK2	DS0_MCLK2						
P2.0	UC03_SEL0	UC03_SEL0	UC03_SEL0	UC03_SEL0	UC03_SEL0	UC03_SEL0	UC03_SEL0	UC03_SEL0	UC03_SEL0	UC03_SEL0						
P2.1	VADC_EMU000	UC03_SEL1	UC03_OUT14	UC03_SEL1	UC03_SEL1	UC03_SEL1	UC03_SEL1	UC03_SEL1	UC03_SEL1	UC03_SEL1						
P2.2	VADC_EMU001	UC03_SEL2	UC03_OUT15	UC03_SEL2	UC03_SEL2	UC03_SEL2	UC03_SEL2	UC03_SEL2	UC03_SEL2	UC03_SEL2						
P2.3	VADC_EMU002	UC03_SEL3	UC03_OUT16	UC03_SEL3	UC03_SEL3	UC03_SEL3	UC03_SEL3	UC03_SEL3	UC03_SEL3	UC03_SEL3						
P2.4	VADC_EMU003	UC03_SEL4	UC03_OUT17	UC03_SEL4	UC03_SEL4	UC03_SEL4	UC03_SEL4	UC03_SEL4	UC03_SEL4	UC03_SEL4						
P2.5	VADC_EMU004	UC03_SEL5	UC03_OUT18	UC03_SEL5	UC03_SEL5	UC03_SEL5	UC03_SEL5	UC03_SEL5	UC03_SEL5	UC03_SEL5						
P2.6	VADC_EMU005	UC03_SEL6	UC03_OUT19	UC03_SEL6	UC03_SEL6	UC03_SEL6	UC03_SEL6	UC03_SEL6	UC03_SEL6	UC03_SEL6						
P2.7	ETH0_MDC	UC03_NL_TXD	CC081_OUT20	UC03_NL_TXD	UC03_NL_TXD	UC03_NL_TXD	UC03_NL_TXD	UC03_NL_TXD	UC03_NL_TXD	UC03_NL_TXD						
P2.8	ETH0_TXD0	UC03_SEL0	UC03_OUT21	UC03_SEL0	UC03_SEL0	UC03_SEL0	UC03_SEL0	UC03_SEL0	UC03_SEL0	UC03_SEL0						
P2.9	ETH0_TXD1	UC03_SEL1	UC03_OUT22	UC03_SEL1	UC03_SEL1	UC03_SEL1	UC03_SEL1	UC03_SEL1	UC03_SEL1	UC03_SEL1						
P2.10	VADC_EMU010	UC03_SEL2	UC03_OUT23	UC03_SEL2	UC03_SEL2	UC03_SEL2	UC03_SEL2	UC03_SEL2	UC03_SEL2	UC03_SEL2						
P2.11	ETH0_TXR	UC03_SEL3	UC03_OUT24	UC03_SEL3	UC03_SEL3	UC03_SEL3	UC03_SEL3	UC03_SEL3	UC03_SEL3	UC03_SEL3						

**Table 11 Port I/O Functions (cont'd)**

Function	Outputs						Inputs							
	ALT1	ALT2	ALT3	ALT4	HW00	HW01	HWI0	HWI1	Input	Input	Input	Input	Input	Input
P2.12	ETH0_TMD2	ETH0_TMD2	COH41_OUT33	ETH0_TXD0	DB_ETM_TRACE_DA TA1	ERU_AD30	ERU_D30	ERU_D30	UIC0_D30	UIC0_D30	COH43_IN3C	COH43_IN3C	COH43_IN3C	COH43_IN3C
P2.13	ETH0_TMD3	ETH0_TXD1	COH40_OUT21	ETH0_TXD1	DB_ETM_TRACE_DA TA0	ERU_AD31	ERU_D31	ERU_D31	UIC0_D30	UIC0_D30	COH43_IN3B	COH43_IN3B	COH43_IN3B	COH43_IN3B
P2.14	VADC_EMU_A11	UIC0_DOUT0	COH40_OUT21	ETM_TRACE_CLK_B02	DB_ETM_TRACE_DA TA0	ERU_AD31	ERU_D31	ERU_D31	UIC0_D30	UIC0_D30	COH43_IN3B	COH43_IN3B	COH43_IN3B	COH43_IN3B
P2.15	VADC_EMU_A12	UIC0_DOUT0	COH40_OUT21	LEDTS0_LINE9	LEDTS0_EXTENDED06	ERU_B02	LEDTS0_TSINA	ETH0_COA	UIC0_D30	UIC0_D30	COH42_IN3B	COH42_IN3B	COH42_IN3B	COH42_IN3B
P3.0	UIC1_SELO0	UIC1_SCLKOUT	COH42_OUT0	COH42_OUT0	ERU_B02	ERU_B02	UIC1_D31	UIC1_D31	UIC1_D31	UIC1_D31	COH40_IN3C	COH40_IN3C	COH40_IN3C	COH40_IN3C
P3.1	USB_DRIVE/US	CAN_M0_TXD	LEDTS0_COA	LEDTS0_COA	ERU_B02	ERU_B02	UIC1_D31	UIC1_D31	UIC1_D31	UIC1_D31	COH40_IN3C	COH40_IN3C	COH40_IN3C	COH40_IN3C
P3.2	USB_DRIVE/US	CAN_M0_TXD	LEDTS0_COA	LEDTS0_COA	ERU_B02	ERU_B02	UIC1_D31	UIC1_D31	UIC1_D31	UIC1_D31	COH40_IN3C	COH40_IN3C	COH40_IN3C	COH40_IN3C
P3.3	UIC1_SELO1	UIC1_SELO1	COH42_OUT3	COH42_OUT3	SWMMC_LED	SWMMC_LED	ERU_D31	ERU_D31	UIC1_D31	UIC1_D31	COH42_IN3A	COH42_IN3A	COH42_IN3A	COH42_IN3A
P3.4	UIC1_MCLKOUT	UIC1_SELO2	COH42_OUT2	DSO_MCLK3	SWMMC_BIS_POWER	SWMMC_BIS_POWER	ERU_D31	ERU_D31	UIC1_D31	UIC1_D31	COH42_IN3A	COH42_IN3A	COH42_IN3A	COH42_IN3A
P3.5	UIC1_DOUT0	UIC1_SELO3	COH42_OUT1	UIC1_DOUT0	SWMMC_CMD_OUT	SWMMC_CMD_OUT	ERU_D4	ERU_D4	UIC1_D31	UIC1_D31	COH42_IN3A	COH42_IN3A	COH42_IN3A	COH42_IN3A
P3.6	UIC1_SCLKOUT	UIC1_SELO4	COH42_OUT0	UIC1_SCLKOUT	SWMMC_CLK_OUT	SWMMC_CLK_OUT	ERU_D5	ERU_D5	UIC1_D31	UIC1_D31	COH42_IN3A	COH42_IN3A	COH42_IN3A	COH42_IN3A
P3.7	CAN_M0_TXD	CAN_M0_TXD	COH41_OUT3	LEDTS0_LINE0	COH41_OUT3	COH41_OUT3	LEDTS0_LINE0	LEDTS0_LINE0	UIC0_D30	UIC0_D30	COH42_IN3A	COH42_IN3A	COH42_IN3A	COH42_IN3A
P3.8	UIC0_DOUT0	UIC0_SELO3	COH41_OUT2	LEDTS0_LINE1	COH41_OUT2	COH41_OUT2	LEDTS0_LINE1	LEDTS0_LINE1	CAN_M0_RXD0	CAN_M0_RXD0	POSIF1_IN3B	POSIF1_IN3B	POSIF1_IN3B	POSIF1_IN3B
P3.9	UIC0_SCLKOUT	CAN_M0_TXD	COH41_OUT1	LEDTS0_LINE2	COH41_OUT1	COH41_OUT1	LEDTS0_LINE2	LEDTS0_LINE2	CAN_M0_RXD0	CAN_M0_RXD0	POSIF1_IN3B	POSIF1_IN3B	POSIF1_IN3B	POSIF1_IN3B
P3.10	UIC0_SELO0	CAN_M0_TXD	COH41_OUT0	LEDTS0_LINE3	UIC1_DOUT3	UIC1_DOUT3	LEDTS0_LINE3	LEDTS0_LINE3	UIC1_D31	UIC1_D31	POSIF1_IN3B	POSIF1_IN3B	POSIF1_IN3B	POSIF1_IN3B
P3.11	UIC1_SELO3	UIC1_SELO3	COH42_OUT3	LEDTS0_LINE4	UIC1_DOUT2	UIC1_DOUT2	LEDTS0_LINE4	LEDTS0_LINE4	CAN_M0_RXD0	CAN_M0_RXD0	COH40_IN3C	COH40_IN3C	COH40_IN3C	COH40_IN3C
P3.12	UIC1_SELO1	UIC1_SELO1	COH42_OUT2	LEDTS0_LINE5	UIC1_DOUT1	UIC1_DOUT1	LEDTS0_LINE5	LEDTS0_LINE5	CAN_M0_RXD0	CAN_M0_RXD0	COH40_IN3C	COH40_IN3C	COH40_IN3C	COH40_IN3C
P3.13	UIC1_SCLKOUT	UIC1_DOUT0	COH42_OUT1	LEDTS0_LINE6	UIC1_DOUT0	UIC1_DOUT0	LEDTS0_LINE6	LEDTS0_LINE6	UIC1_D30	UIC1_D30	COH40_IN3C	COH40_IN3C	COH40_IN3C	COH40_IN3C
P3.14	UIC0_SELO3	UIC0_SELO3	COH41_OUT0	LEDTS0_LINE7	UIC1_DOUT1	UIC1_DOUT1	LEDTS0_LINE7	LEDTS0_LINE7	UIC1_D30	UIC1_D30	COH42_IN3C	COH42_IN3C	COH42_IN3C	COH42_IN3C
P3.15	UIC1_DOUT0	UIC1_DOUT0	COH41_OUT0	LEDTS0_LINE8	UIC1_DOUT0	UIC1_DOUT0	LEDTS0_LINE8	LEDTS0_LINE8	UIC1_D30	UIC1_D30	COH42_IN3C	COH42_IN3C	COH42_IN3C	COH42_IN3C
P4.0	UIC1_SELO0	UIC1_SELO0	COH41_OUT0	LEDTS0_LINE9	SWMMC_DATA_OUT	SWMMC_DATA_OUT	LEDTS0_LINE9	LEDTS0_LINE9	UIC1_D30	UIC1_D30	UIC1_D30	UIC1_D30	UIC1_D30	UIC1_D30
P4.1	UIC1_SELO0	UIC1_SELO0	COH41_OUT0	LEDTS0_LINE9	SWMMC_DATA_OUT	SWMMC_DATA_OUT	LEDTS0_LINE9	LEDTS0_LINE9	UIC1_D30	UIC1_D30	UIC1_D30	UIC1_D30	UIC1_D30	UIC1_D30
P4.2	UIC1_SELO1	UIC1_DOUT0	UIC1_DOUT0	SCLKOUT	UIC1_DOUT0	UIC1_DOUT0	SCLKOUT	SCLKOUT	UIC1_D30	UIC1_D30	UIC1_D30	UIC1_D30	UIC1_D30	UIC1_D30



**Table 11** Port I/O Functions (cont'd)

Function	Outputs					Inputs										
	ALT1	ALT2	ALT3	ALT4	HW00	HW01	HW10	HW11	Input	Input	Input	Input	Input	Input	Input	Input
P4.3	UC11 SELO2	UC00 SELO5	CC143 OUT3												CC143 IN5A	
P4.4		UC01 SELO4	UC143 OUT2	UC11 DOU13			UC01 HW10								CC143 IN5A	
P4.5		UC00 SELO3	CC143 OUT1	UC11 DOU12			UC11 HW10								CC143 IN5A	
P4.6		UC00 SELO2	CC143 OUT0	UC11 DOU11			UC11 HW11	CAN, NZ_PWD							CC143 IN5A	
P4.7		CAN, NZ_TXD		UC11 DOU10			UC11 HW10	UC11 DX5C							CC143 IN5C	
P5.0	UC00 DOU10	PSD, COP_PWIN	CC181 OUT3	UC00 DOU10			UC00 HW10	UC00 DX0B	ETH0, RXD0D						CC181 IN5A	CC181 IN5A
P5.1	UC01 DOU10	PSD, COP_PWP	CC181 OUT2	UC00 DOU11			UC00 HW11	UC00 DX0A	ETH0, RXD1D						CC181 IN5B	
P5.2	UC00 SCK/OUT		CC181 OUT1					UC00 DX1A	ETH0, CARE_DV1D						CC181 IN1B	ETH0, RXD1D
P5.3	UC00 SELO0		CC181 OUT2	ERU CNE				UC00 DX0A	ETH0, RXERD						CC181 IN2B	
P5.4	UC00 SELO1		CC181 OUT13	ER17 RCS					ETH0, CRSD						CC181 IN3B	
P5.5	UC00 SELO2		CC181 OUT12	ER17 CNS					ETH0, COLD							
P5.6	UC00 SELO3		CC181 OUT103	ERU BFCL1D				ERU BFCL1I								
P5.7			CC181 OUT102	UC00 DOU12			UC00 HW10									
P5.8	UC00 SCK/OUT		CC180 OUT01	ERU SCK1MD				ETH0, RXD1A	ETH0, D1XB							
P5.9	UC00 SELO0		CC180 OUT120	ERU BFCL1D				ETH0, RXD1A	ETH0, D1XB							
P5.10	UC00 MCK/OUT		CC180 OUT10	LED150, LINE7				ETH0, CLK_T1A								
P5.11	UC00 SELO1		CC180 OUT100					ETH0, CR5A								
P6.0	ETH0, TAD3	UC11 SELO1	CC181 OUT131	DB, ETM_TRACECLK												
P6.1	ETH0, TAG3	UC11 SELO0	CC181 OUT130	DB, ETM_TRACE1A				UC11 DX5C								
P6.2	ETH0, TAGER	UC11 SCK/OUT	CC143 OUT15	DB, ETM_TRACE1A				UC11 DX1C								
P6.3			CC143 OUT12	TA2				UC11 DX5C	ETH0, RXD3B							
P6.4		UC11 DOU10	CC143 OUT11	ERU SCK1MD				ERU SCK1MI	ETH0, RXD2B							
P6.5		UC11 MCK/OUT	CC143 OUT10	DB, ETM_TRACE1A				ETH0, D1XA	ETH0, CLK_RM1D							ETH0, CURV0

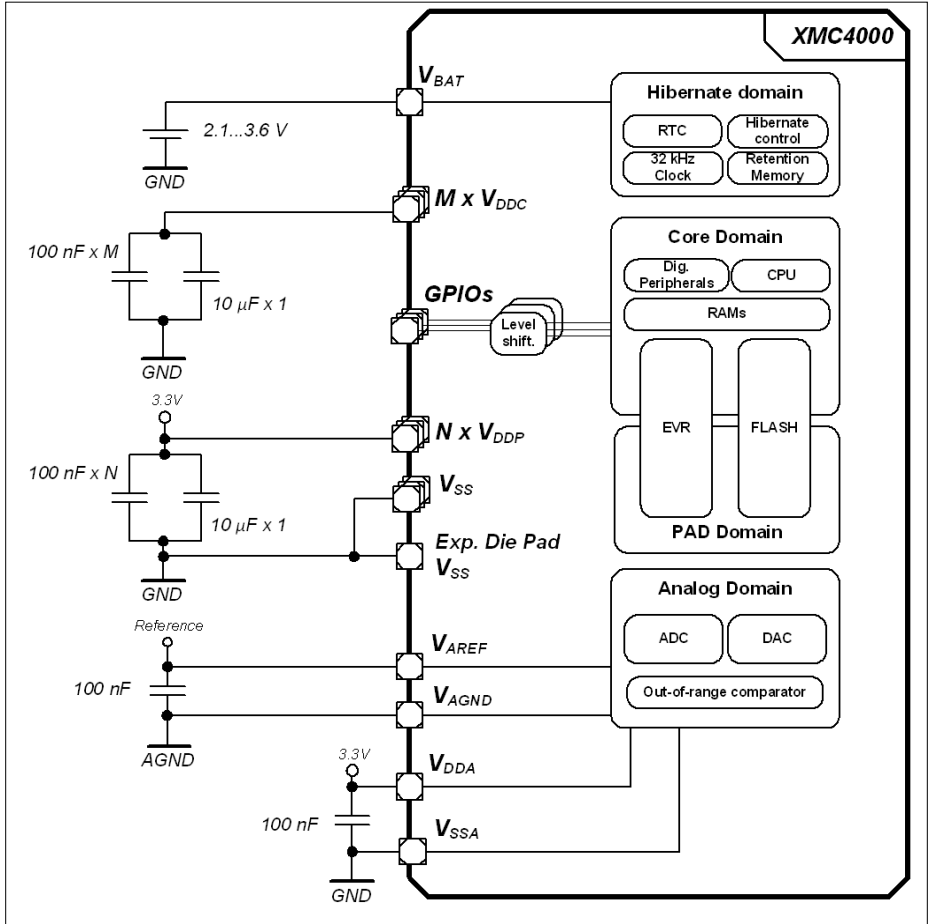
**Table 11** Port I/O Functions (cont'd)

Function	Outputs					Inputs											
	ALT1	ALT2	ALT3	ALT4		HW00	HW01	HWI0	HWI1	Input	Input	Input	Input	Input	Input	Input	Input
P16.6			RSD_MCLK3	RSD_MCLK3	RE_ETM_TRACE/EDA_TAO		BRIT_BCS			RSD_MCLK3A	ETH0_CLK_TXB						
P14.0										VADC_G0CH0							
P14.1										VADC_G0CH1							
P14.2										VADC_G0CH2							
P14.3										VADC_G1CH3					CAN_NO_RX0B		
P14.4										VADC_G0CH4	VADC_G2CH0						
P14.5										VADC_G0CH5	VADC_G2CH1				POSIF0_INZB		
P14.6										VADC_G0CH6	VADC_G2CH1				POSIF0_INTB	GIORC6	
P14.7										VADC_G0CH7					POSIF0_INTB	GIORC7	
P14.8					DAC_OUT_0					VADC_G1CH9		VADC_G3CH2			ETH0_RX0DC		
P14.9					DAC_OUT_1					VADC_G1CH1		VADC_G3CH3			ETH0_RX0DC		
P14.12										VADC_G1CH4							
P14.13										VADC_G1CH6							
P14.14										VADC_G1CH6						GIORC6	
P14.15										VADC_G1CH6						GIORC7	
P15.2										VADC_G2CH2							
P15.3										VADC_G2CH3							
P15.4										VADC_G2CH3							
P15.4										VADC_G2CH4							
P15.5										VADC_G2CH5							
P15.6										VADC_G2CH5							
P15.6										VADC_G2CH6							
P15.7										VADC_G2CH7							
P15.8										VADC_G2CH7		VADC_G3CH0		ETH0_CLK_RM1C		ETH0_CHRRVC	
P15.9											VADC_G3CH1	VADC_CRS_DVC		ETH0_CRS_DVC		ETH0_RX0VC	



### 2.3 Power Connection Scheme

Figure 9 shows a reference power connection scheme for the XMC4500.



**Figure 9 Power Connection Scheme**

Every power supply pin needs to be connected. Different pins of the same supply need also to be externally connected. As example, all  $V_{DDP}$  pins must be connected externally to one  $V_{DDP}$  net. In this reference scheme one 100 nF capacitor is connected at each supply pin against  $V_{SS}$ . An additional 10  $\mu$ F capacitor is connected to the  $V_{DDP}$  nets and an additional 10  $\mu$ F capacitor to the  $V_{DDC}$  nets.

The XMC4500 has a common ground concept, all  $V_{SS}$ ,  $V_{SSA}$  and  $V_{SSO}$  pins share the same ground potential. In packages with an exposed die pad it must be connected to the common ground as well.

$V_{AGND}$  is the low potential to the analog reference  $V_{AREF}$ . Depending on the application it can share the common ground or have a different potential.

When  $V_{DDP}$  is supplied,  $V_{BAT}$  must be supplied as well. If no other supply source (e.g. battery) is connected to  $V_{BAT}$ , the  $V_{BAT}$  pin can also be connected directly to  $V_{DDP}$ .

## **3 Electrical Parameters**

### **3.1 General Parameters**

#### **3.1.1 Parameter Interpretation**

The parameters listed in this section partly represent the characteristics of the XMC4500 and partly its requirements on the system. To aid interpreting the parameters easily when evaluating them for a design, they are marked with a two-letter abbreviation in column "Symbol":

- **CC**  
Such parameters indicate **C**ontroller **C**haracteristics, which are a distinctive feature of the XMC4500 and must be regarded for system design.
- **SR**  
Such parameters indicate **S**ystem **R**equirements, which must be provided by the application system in which the XMC4500 is designed in.

### 3.1.2 Absolute Maximum Ratings

Stresses above the values listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions may affect device reliability.

**Table 12 Absolute Maximum Rating Parameters**

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
Storage temperature	$T_{ST}$	SR	-65	–	150	°C	–
Junction temperature	$T_J$	SR	-40	–	150	°C	–
Voltage at 3.3 V power supply pins with respect to $V_{SS}$	$V_{DDP}$	SR	–	–	4.3	V	–
Voltage on any Class A and dedicated input pin with respect to $V_{SS}$	$V_{IN}$	SR	-1.0	–	$V_{DDP} + 1.0$ or max. 4.3	V	whichever is lower
Voltage on any analog input pin with respect to $V_{AGND}$	$V_{AIN}$ $V_{AREF}$	SR	-1.0	–	$V_{DDP} + 1.0$ or max. 4.3	V	whichever is lower
Input current on any pin during overload condition	$I_{IN}$	SR	-10	–	+10	mA	
Absolute maximum sum of all input circuit currents for one port group during overload condition <sup>1)</sup>	$\Sigma I_{IN}$	SR	-25	–	+25	mA	
Absolute maximum sum of all input circuit currents during overload condition	$\Sigma I_{IN}$	SR	-100	–	+100	mA	

1) The port groups are defined in [Table 16](#).

**Figure 10** explains the input voltage ranges of  $V_{IN}$  and  $V_{AIN}$  and its dependency to the supply level of  $V_{DDP}$ . The input voltage must not exceed 4.3 V, and it must not be more than 1.0 V above  $V_{DDP}$ . For the range up to  $V_{DDP} + 1.0$  V also see the definition of the overload conditions in [Section 3.1.3](#).

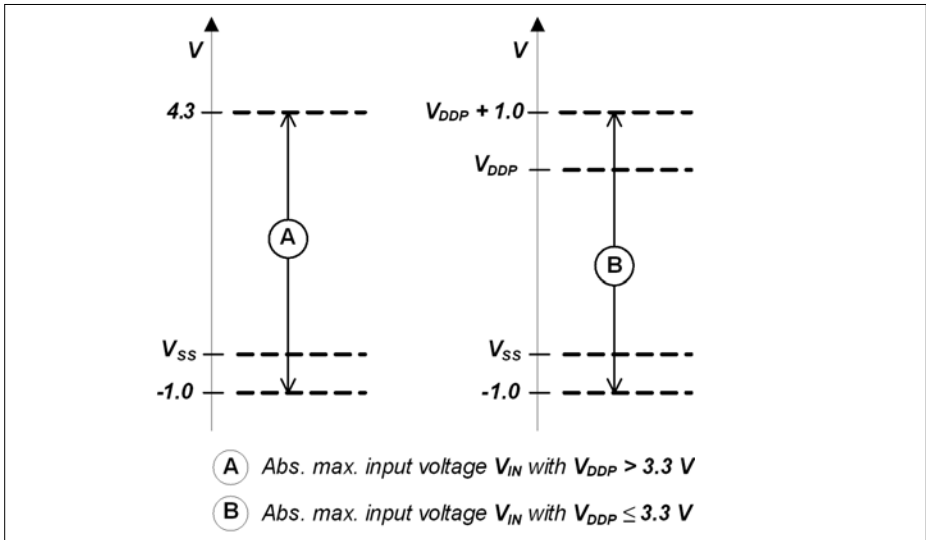


Figure 10 Absolute Maximum Input Voltage Ranges

### 3.1.3 Pin Reliability in Overload

When receiving signals from higher voltage devices, low-voltage devices experience overload currents and voltages that go beyond their own IO power supplies specification.

**Table 13** defines overload conditions that will not cause any negative reliability impact if all the following conditions are met:

- full operation life-time is not exceeded
- **“Operating Conditions”** are met for
  - pad supply levels ( $V_{DDP}$  or  $V_{DDA}$ )
  - temperature

If a pin current is outside of the **“Operating Conditions”** but within the overload conditions, then the parameters of this pin as stated in the Operating Conditions can no longer be guaranteed. Operation is still possible in most cases but with relaxed parameters.

*Note: An overload condition on one or more pins does not require a reset.*

*Note: A series resistor at the pin to limit the current to the maximum permitted overload current is sufficient to handle failure situations like short to battery.*

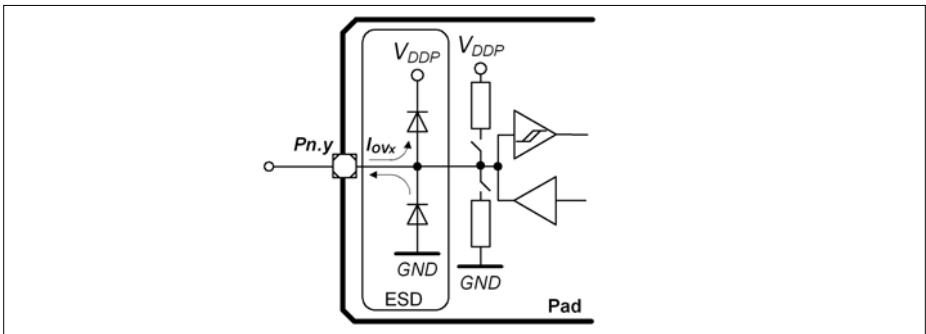


**Table 13**    **Overload Parameters**

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
Input current on any port pin during overload condition	$I_{OV}$	SR	-5	–	5	mA	
Absolute sum of all input circuit currents for one port group during overload condition <sup>1)</sup>	$I_{OVG}$	SR	–	–	20	mA	$\Sigma  I_{OVx} $ , for all $I_{OVx} < 0$ mA
			–	–	20	mA	$\Sigma  I_{OVx} $ , for all $I_{OVx} > 0$ mA
Absolute sum of all input circuit currents during overload condition	$I_{OVS}$	SR	–	–	80	mA	$\Sigma I_{OVG}$

1) The port groups are defined in [Table 16](#).

**Figure 11** shows the path of the input currents during overload via the ESD protection structures. The diodes against  $V_{DDP}$  and ground are a simplified representation of these ESD protection structures.



**Figure 11**    **Input Overload Current via ESD structures**

[Table 14](#) and [Table 15](#) list input voltages that can be reached under overload conditions. Note that the absolute maximum input voltages as defined in the “**Absolute Maximum Ratings**” must not be exceeded during overload.

**Table 14 PN-Junction Characteristics for positive Overload**

Pad Type	$I_{OV} = 5 \text{ mA}, T_J = -40 \text{ }^\circ\text{C}$	$I_{OV} = 5 \text{ mA}, T_J = 150 \text{ }^\circ\text{C}$
A1 / A1+	$V_{IN} = V_{DDP} + 1.0 \text{ V}$	$V_{IN} = V_{DDP} + 0.75 \text{ V}$
A2	$V_{IN} = V_{DDP} + 0.7 \text{ V}$	$V_{IN} = V_{DDP} + 0.6 \text{ V}$
AN/DIG_IN	$V_{IN} = V_{DDP} + 1.0 \text{ V}$	$V_{IN} = V_{DDP} + 0.75 \text{ V}$

**Table 15 PN-Junction Characteristics for negative Overload**

Pad Type	$I_{OV} = 5 \text{ mA}, T_J = -40 \text{ }^\circ\text{C}$	$I_{OV} = 5 \text{ mA}, T_J = 150 \text{ }^\circ\text{C}$
A1 / A1+	$V_{IN} = V_{SS} - 1.0 \text{ V}$	$V_{IN} = V_{SS} - 0.75 \text{ V}$
A2	$V_{IN} = V_{SS} - 0.7 \text{ V}$	$V_{IN} = V_{SS} - 0.6 \text{ V}$
AN/DIG_IN	$V_{IN} = V_{DDP} - 1.0 \text{ V}$	$V_{IN} = V_{DDP} - 0.75 \text{ V}$

**Table 16 Port Groups for Overload and Short-Circuit Current Sum Parameters**

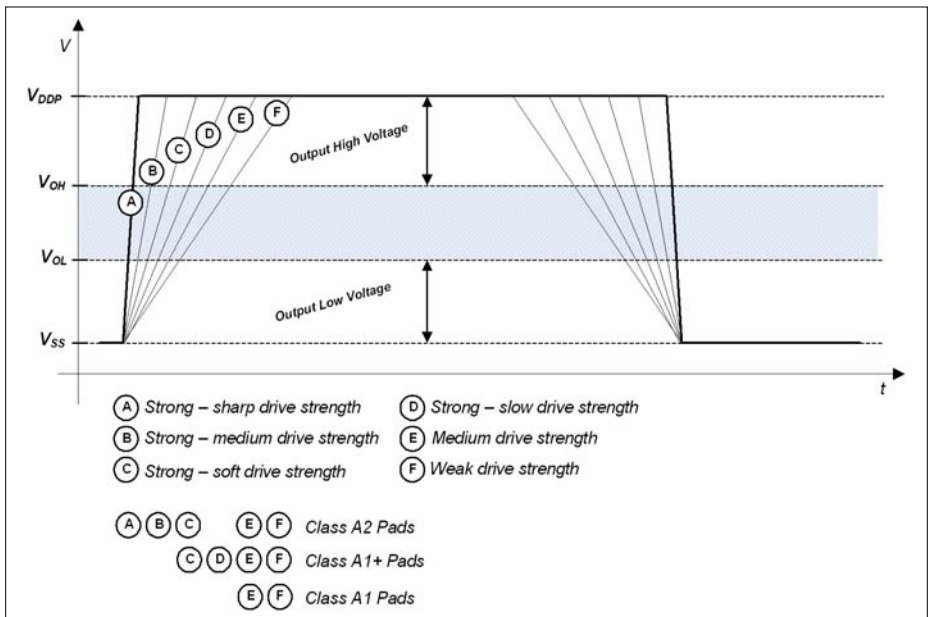
Group	Pins
1	P0.[15:0], P3.[15:0]
2	P14.[15:0], P15.[15:0]
3	P2.[15:0], P5.[11:0]
4	P1.[15:0], P4.[7:0], P6.[6:0]

### 3.1.4 Pad Driver and Pad Classes Summary

This section gives an overview on the different pad driver classes and their basic characteristics.

**Table 17 Pad Driver and Pad Classes Overview**

Class	Power Supply	Type	Sub-Class	Speed Grade	Load	Termination
A	3.3 V	LVTTTL I/O	<b>A1</b> (e.g. GPIO)	6 MHz	100 pF	No
			<b>A1+</b> (e.g. serial I/Os)	25 MHz	50 pF	Series termination recommended
			<b>A2</b> (e.g. ext. Bus)	80 MHz	15 pF	Series termination recommended



**Figure 12 Output Slopes with different Pad Driver Modes**

**Figure 12** is a qualitative display of the resulting output slope performance with different output driver modes. The detailed input and output characteristics are listed in **Section 3.2.1**.

### 3.1.5 Operating Conditions

The following operating conditions must not be exceeded in order to ensure correct operation and reliability of the XMC4500. All parameters specified in the following sections refer to these operating conditions, unless noted otherwise.

**Table 18 Operating Conditions Parameters**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Ambient Temperature	$T_A$ SR	-40	–	85	°C	Temp. Range F
		-40	–	105	°C	Temp. Range X
		-40	–	125	°C	Temp. Range K
Digital supply voltage	$V_{DDP}$ SR	3.13 <sup>1)</sup>	3.3	3.63 <sup>2)</sup>	V	
Core Supply Voltage	$V_{DDC}$ CC	– <sup>1)</sup>	1.3	–	V	Generated internally
Digital ground voltage	$V_{SS}$ SR	0	–	–	V	
Analog supply voltage	$V_{DDA}$ SR	3.0	3.3	3.6 <sup>2)</sup>	V	
Analog ground voltage for $V_{DDA}$	$V_{SSA}$ SR	-0.1	0	0.1	V	
Battery Supply Voltage for Hibernate Domain	$V_{BAT}$ SR	1.95 <sup>3)</sup>	–	3.63	V	When $V_{DDP}$ is supplied $V_{BAT}$ has to be supplied as well.
System Frequency	$f_{SYS}$ SR	–	–	120	MHz	
Short circuit current of digital outputs	$I_{SC}$ SR	-5	–	5	mA	
Absolute sum of short circuit currents per pin group <sup>4)</sup>	$\Sigma I_{SC\_PG}$ SR	–	–	20	mA	
Absolute sum of short circuit currents of the device	$\Sigma I_{SC\_D}$ SR	–	–	100	mA	

1) See also the Supply Monitoring thresholds, [Section 3.3.2](#).

2) Voltage overshoot to 4.0 V is permissible at Power-Up and  $\overline{PORST}$  low, provided the pulse duration is less than 100  $\mu$ s and the cumulated sum of the pulses does not exceed 1 h over lifetime.

3) To start the hibernate domain it is required that  $V_{BAT} \geq 2.1$  V, for a reliable start of the oscillation of RTC\_XTAL in crystal mode it is required that  $V_{BAT} \geq 3.0$  V.

4) The port groups are defined in [Table 16](#).

## 3.2 DC Parameters

### 3.2.1 Input/Output Pins

The digital input stage of the shared analog/digital input pins is identical to the input stage of the standard digital input/output pins.

The Pull-up on the  $\overline{\text{PORST}}$  pin is identical to the Pull-up on the standard digital input/output pins.

*Note: These parameters are not subject to production test, but verified by design and/or characterization.*

**Table 19 Standard Pad Parameters**

Parameter	Symbol	Values		Unit	Note / Test Condition
		Min.	Max.		
Pin capacitance (digital inputs/outputs)	$C_{IO}$ CC	–	10	pF	
Pull-down current	$ I_{PDL} $ CC	150	–	$\mu\text{A}$	<sup>1)</sup> $V_{IN} \geq 0.6 \times V_{DDP}$
		–	10	$\mu\text{A}$	<sup>2)</sup> $V_{IN} \leq 0.36 \times V_{DDP}$
Pull-Up current	$ I_{PUH} $ CC	–	10	$\mu\text{A}$	<sup>2)</sup> $V_{IN} \geq 0.6 \times V_{DDP}$
		100	–	$\mu\text{A}$	<sup>1)</sup> $V_{IN} \leq 0.36 \times V_{DDP}$
Input Hysteresis for pads of all A classes <sup>3)</sup>	$HYS_A$ CC	$0.1 \times V_{DDP}$	–	V	
$\overline{\text{PORST}}$ spike filter always blocked pulse duration	$t_{SF1}$ CC	–	10	ns	
$\overline{\text{PORST}}$ spike filter pass-through pulse duration	$t_{SF2}$ CC	100	–	ns	
$\overline{\text{PORST}}$ pull-down current	$ I_{PPD} $ CC	13	–	mA	$V_{IN} = 1.0 \text{ V}$

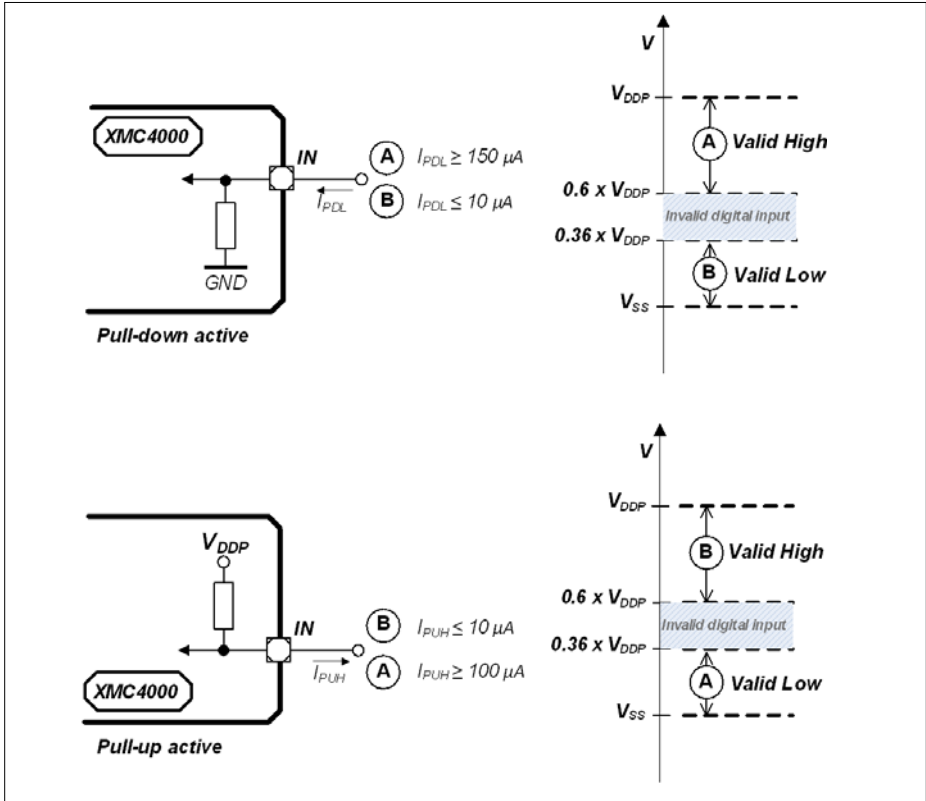
1) Current required to override the pull device with the opposite logic level (“force current”).

With active pull device, at load currents between force and keep current the input state is undefined.

2) Load current at which the pull device still maintains the valid logic level (“keep current”).

With active pull device, at load currents between force and keep current the input state is undefined.

3) Hysteresis is implemented to avoid metastable states and switching due to internal ground bounce. It can not be guaranteed that it suppresses switching due to external system noise.



**Figure 13 Pull Device Input Characteristics**

**Figure 13** visualizes the input characteristics with an active internal pull device:

- in the cases “A” the internal pull device is overridden by a strong external driver;
- in the cases “B” the internal pull device defines the input logical state against a weak external load.

**Electrical Parameters**
**Table 20 Standard Pads Class\_A1**

Parameter	Symbol	Values		Unit	Note / Test Condition
		Min.	Max.		
Input leakage current	$I_{OZA1}$ CC	-500	500	nA	$0\text{ V} \leq V_{IN} \leq V_{DDP}$
Input high voltage	$V_{IHA1}$ SR	$0.6 \times V_{DDP}$	$V_{DDP} + 0.3$	V	max. 3.6 V
Input low voltage	$V_{ILA1}$ SR	-0.3	$0.36 \times V_{DDP}$	V	
Output high voltage, POD <sup>1)</sup> = weak	$V_{OHA1}$ CC	$V_{DDP} - 0.4$	–	V	$I_{OH} \geq -400\ \mu\text{A}$
		2.4	–	V	$I_{OH} \geq -500\ \mu\text{A}$
Output high voltage, POD <sup>1)</sup> = medium		$V_{DDP} - 0.4$	–	V	$I_{OH} \geq -1.4\ \text{mA}$
		2.4	–	V	$I_{OH} \geq -2\ \text{mA}$
Output low voltage	$V_{OLA1}$ CC	–	0.4	V	$I_{OL} \leq 500\ \mu\text{A}$ ; POD <sup>1)</sup> = weak
		–	0.4	V	$I_{OL} \leq 2\ \text{mA}$ ; POD <sup>1)</sup> = medium
Fall time	$t_{FA1}$ CC	–	150	ns	$C_L = 20\ \text{pF}$ ; POD <sup>1)</sup> = weak
		–	50	ns	$C_L = 50\ \text{pF}$ ; POD <sup>1)</sup> = medium
Rise time	$t_{RA1}$ CC	–	150	ns	$C_L = 20\ \text{pF}$ ; POD <sup>1)</sup> = weak
		–	50	ns	$C_L = 50\ \text{pF}$ ; POD <sup>1)</sup> = medium

1) POD = Pin Out Driver

**Table 21 Standard Pads Class\_A1+**

Parameter	Symbol	Values		Unit	Note / Test Condition
		Min.	Max.		
Input leakage current	$I_{OZA1+}$ CC	-1	1	$\mu\text{A}$	$0\text{ V} \leq V_{IN} \leq V_{DDP}$
Input high voltage	$V_{IHA1+}$ SR	$0.6 \times V_{DDP}$	$V_{DDP} + 0.3$	V	max. 3.6 V
Input low voltage	$V_{ILA1+}$ SR	-0.3	$0.36 \times V_{DDP}$	V	

**Electrical Parameters**
**Table 21 Standard Pads Class\_A1+**

Parameter	Symbol	Values		Unit	Note / Test Condition	
		Min.	Max.			
Output high voltage, POD <sup>1)</sup> = weak	V <sub>OHA1+</sub> CC	V <sub>DDP</sub> - 0.4	–	V	I <sub>OH</sub> ≥ -400 μA	
		2.4	–	V	I <sub>OH</sub> ≥ -500 μA	
Output high voltage, POD <sup>1)</sup> = medium		V <sub>DDP</sub> - 0.4	–	V	I <sub>OH</sub> ≥ -1.4 mA	
		2.4	–	V	I <sub>OH</sub> ≥ -2 mA	
Output high voltage, POD <sup>1)</sup> = strong		V <sub>DDP</sub> - 0.4	–	V	I <sub>OH</sub> ≥ -1.4 mA	
		2.4	–	V	I <sub>OH</sub> ≥ -2 mA	
Output low voltage		V <sub>OLA1+</sub> CC	–	0.4	V	I <sub>OL</sub> ≤ 500 μA; POD <sup>1)</sup> = weak
			–	0.4	V	I <sub>OL</sub> ≤ 2 mA; POD <sup>1)</sup> = medium
	–		0.4	V	I <sub>OL</sub> ≤ 2 mA; POD <sup>1)</sup> = strong	
Fall time	t <sub>FA1+</sub> CC	–	150	ns	C <sub>L</sub> = 20 pF; POD <sup>1)</sup> = weak	
		–	50	ns	C <sub>L</sub> = 50 pF; POD <sup>1)</sup> = medium	
		–	28	ns	C <sub>L</sub> = 50 pF; POD <sup>1)</sup> = strong; edge = slow	
		–	16	ns	C <sub>L</sub> = 50 pF; POD <sup>1)</sup> = strong; edge = soft;	
Rise time	t <sub>RA1+</sub> CC	–	150	ns	C <sub>L</sub> = 20 pF; POD <sup>1)</sup> = weak	
		–	50	ns	C <sub>L</sub> = 50 pF; POD <sup>1)</sup> = medium	
		–	28	ns	C <sub>L</sub> = 50 pF; POD <sup>1)</sup> = strong; edge = slow	
		–	16	ns	C <sub>L</sub> = 50 pF; POD <sup>1)</sup> = strong; edge = soft	

1) POD = Pin Out Driver



**Table 22 Standard Pads Class\_A2**

Parameter	Symbol	Values		Unit	Note / Test Condition
		Min.	Max.		
Input Leakage current	$I_{OZA2}$ CC	-6	6	$\mu\text{A}$	$0\text{ V} \leq V_{IN} < 0.5 \cdot V_{DDP} - 1\text{ V};$ $0.5 \cdot V_{DDP} + 1\text{ V} < V_{IN} \leq V_{DDP}$
		-3	3	$\mu\text{A}$	$0.5 \cdot V_{DDP} - 1\text{ V} < V_{IN} < 0.5 \cdot V_{DDP} + 1\text{ V}$
Input high voltage	$V_{IHA2}$ SR	$0.6 \times V_{DDP}$	$V_{DDP} + 0.3$	V	max. 3.6 V
Input low voltage	$V_{ILA2}$ SR	-0.3	$0.36 \times V_{DDP}$	V	
Output high voltage, POD = weak	$V_{OHA2}$ CC	$V_{DDP} - 0.4$	–	V	$I_{OH} \geq -400\ \mu\text{A}$
		2.4	–	V	$I_{OH} \geq -500\ \mu\text{A}$
Output high voltage, POD = medium		$V_{DDP} - 0.4$	–	V	$I_{OH} \geq -1.4\ \text{mA}$
		2.4	–	V	$I_{OH} \geq -2\ \text{mA}$
Output high voltage, POD = strong		$V_{DDP} - 0.4$	–	V	$I_{OH} \geq -1.4\ \text{mA}$
		2.4	–	V	$I_{OH} \geq -2\ \text{mA}$
Output low voltage, POD = weak	$V_{OLA2}$ CC	–	0.4	V	$I_{OL} \leq 500\ \mu\text{A}$
Output low voltage, POD = medium		–	0.4	V	$I_{OL} \leq 2\ \text{mA}$
Output low voltage, POD = strong		–	0.4	V	$I_{OL} \leq 2\ \text{mA}$

**Electrical Parameters**

**Table 22 Standard Pads Class\_A2**

Parameter	Symbol	Values		Unit	Note / Test Condition
		Min.	Max.		
Fall time	$t_{FA2}$ CC	–	150	ns	$C_L = 20$ pF; POD = weak
		–	50	ns	$C_L = 50$ pF; POD = medium
		–	3.7	ns	$C_L = 50$ pF; POD = strong; edge = sharp
		–	7	ns	$C_L = 50$ pF; POD = strong; edge = medium
		–	16	ns	$C_L = 50$ pF; POD = strong; edge = soft
Rise time	$t_{RA2}$ CC	–	150	ns	$C_L = 20$ pF; POD = weak
		–	50	ns	$C_L = 50$ pF; POD = medium
		–	3.7	ns	$C_L = 50$ pF; POD = strong; edge = sharp
		–	7.0	ns	$C_L = 50$ pF; POD = strong; edge = medium
		–	16	ns	$C_L = 50$ pF; POD = strong; edge = soft

### 3.2.2 Analog to Digital Converters (VADC)

Note: These parameters are not subject to production test, but verified by design and/or characterization.

**Table 23 VADC Parameters (Operating Conditions apply)**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Analog reference voltage <sup>5)</sup>	$V_{AREF}$ SR	$V_{AGND} + 1$	–	$V_{DDA} + 0.05^{1)}$	V	
Analog reference ground <sup>5)</sup>	$V_{AGND}$ SR	$V_{SSM} - 0.05$	–	$V_{AREF} - 1$	V	
Analog reference voltage range <sup>2)5)</sup>	$V_{AREF} - V_{AGND}$ SR	1	–	$V_{DDA} + 0.1$	V	
Analog input voltage	$V_{AIN}$ SR	$V_{AGND}$	–	$V_{DDA}$	V	
Input leakage at analog inputs <sup>3)</sup>	$I_{OZ1}$ CC	-100	–	200	nA	$0.03 \times V_{DDA} < V_{AIN} < 0.97 \times V_{DDA}$
		-500	–	100	nA	$0 V \leq V_{AIN} \leq 0.03 \times V_{DDA}$
		-100	–	500	nA	$0.97 \times V_{DDA} \leq V_{AIN} \leq V_{DDA}$
Input leakage current at VAREF	$I_{OZ2}$ CC	-1	–	1	$\mu A$	$0 V \leq V_{AREF} \leq V_{DDA}$
Input leakage current at VAGND	$I_{OZ3}$ CC	-1	–	1	$\mu A$	$0 V \leq V_{AGND} \leq V_{DDA}$
Internal ADC clock	$f_{ADCI}$ CC	2	–	30	MHz	$V_{DDA} = 3.3 V$
Switched capacitance at the analog voltage inputs <sup>4)</sup>	$C_{AINSW}$ CC	–	7	20	pF	
Total capacitance of an analog input	$C_{AINTOT}$ CC	–	25	30	pF	
Switched capacitance at the positive reference voltage input <sup>5)6)</sup>	$C_{AREFSW}$ CC	–	15	30	pF	
Total capacitance of the voltage reference inputs <sup>5)</sup>	$C_{AREFTOT}$ CC	–	20	40	pF	

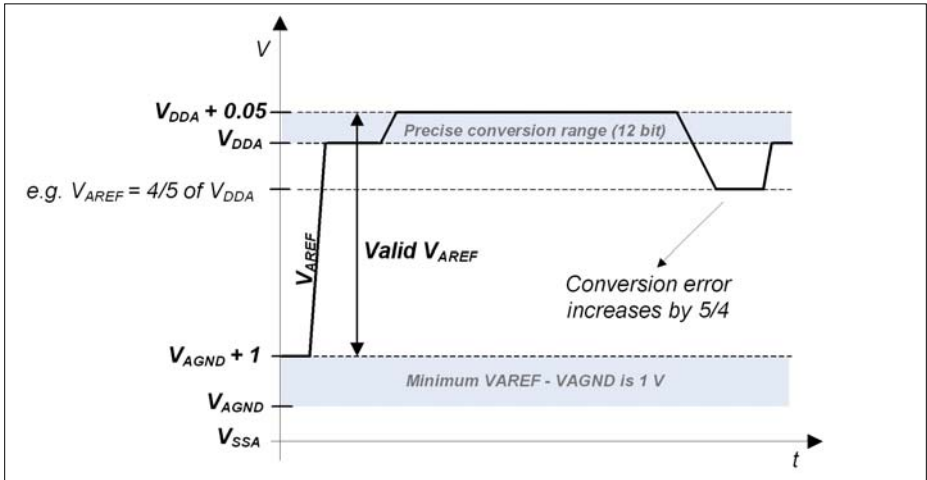
**Electrical Parameters**
**Table 23 VADC Parameters (Operating Conditions apply)**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Total Unadjusted Error	$TUE_{CC}$	-4	–	4	LSB	12-bit resolution; $V_{DDA} = 3.3\text{ V}$ ; $V_{AREF} = V_{DDA}$ <sup>7)</sup>
Differential Non-Linearity Error <sup>8)</sup>	$EA_{DNL_{CC}}$	-3	–	3	LSB	
Gain Error <sup>8)</sup>	$EA_{GAIN_{CC}}$	-4	–	4	LSB	
Integral Non-Linearity <sup>8)</sup>	$EA_{INL_{CC}}$	-3	–	3	LSB	
Offset Error <sup>8)</sup>	$EA_{OFF_{CC}}$	-4	–	4	LSB	
RMS Noise <sup>9)</sup>	$EN_{RMS_{CC}}$	–	1	2 <sup>10/11)</sup>	LSB	
Worst case ADC $V_{DDA}$ power supply current per active converter	$I_{DDAA_{CC}}$	–	1.5	2	mA	during conversion $V_{DDP} = 3.6\text{ V}$ , $T_J = 150\text{ °C}$
Charge consumption on $V_{AREF}$ per conversion <sup>5)</sup>	$Q_{CONV_{CC}}$	–	30	–	pC	$0\text{ V} \leq V_{AREF} \leq V_{DDA}$ <sup>12)</sup>
ON resistance of the analog input path	$R_{AIN_{CC}}$	–	700	1 700	Ohm	
ON resistance for the ADC test (pull down for AIN7)	$R_{AIN7T_{CC}}$	180	550	900	Ohm	
Resistance of the reference voltage input path	$R_{AREF_{CC}}$	–	700	1 700	Ohm	

- 1) A running conversion may become imprecise in case the normal conditions are violated (voltage overshoot).
- 2) If the analog reference voltage is below  $V_{DDA}$ , then the ADC converter errors increase. If the reference voltage is reduced by the factor  $k$  ( $k < 1$ ), TUE, DNL, INL, Gain, and Offset errors increase also by the factor  $1/k$ .
- 3) The leakage current definition is a continuous function, as shown in figure ADCx Analog Inputs Leakage. The numerical values defined determine the characteristic points of the given continuous linear approximation - they do not define step function (see [Figure 16](#)).
- 4) The sampling capacity of the conversion C-network is pre-charged to  $V_{AREF}/2$  before the sampling moment. Because of the parasitic elements, the voltage measured at AINx can deviate from  $V_{AREF}/2$ .
- 5) Applies to AINx, when used as alternate reference input.
- 6) This represents an equivalent switched capacitance. This capacitance is not switched to the reference voltage at once. Instead, smaller capacitances are successively switched to the reference voltage.
- 7) For 10-bit conversions, the errors are reduced to 1/4; for 8-bit conversions, the errors are reduced to 1/16. Never less than  $\pm 1$  LSB.
- 8) The sum of DNL/INL/GAIN/OFF errors does not exceed the related total unadjusted error TUE.

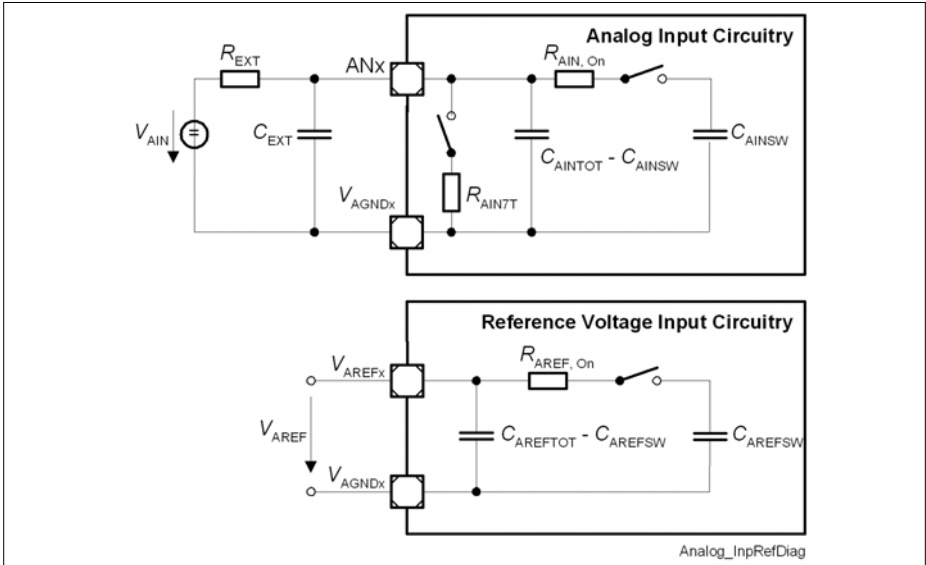
**Electrical Parameters**

- 9) This parameter is valid for soldered devices and requires careful analog board design.
- 10) Resulting worst case combined error is arithmetic combination of TUE and  $EN_{RMS}$ .
- 11) Value is defined for one sigma Gauss distribution.
- 12) The resulting current for a conversion can be calculated with  $I_{AREF} = Q_{CONV} / t_c$ .  
The fastest 12-bit post-calibrated conversion of  $t_c = 550$  ns results in a typical average current of  $I_{AREF} = 54.5 \mu A$ .

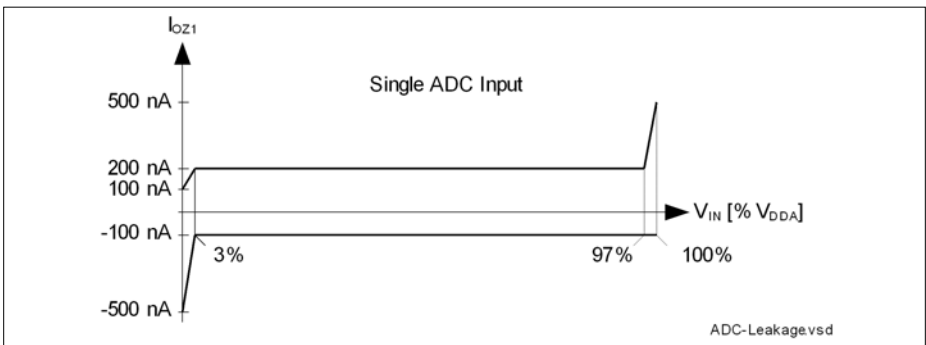


**Figure 14 VADC Reference Voltage Range**

The power-up calibration of the VADC requires a maximum number of  $4 \cdot 352 \cdot f_{ADCI}$  cycles.



**Figure 15 VADC Input Circuits**



**Figure 16 VADC Analog Input Leakage Current**

## Conversion Time

**Table 24 Conversion Time** (Operating Conditions apply)

Parameter	Symbol	Values	Unit	Note
Conversion time	$t_C$ CC	$2 \times T_{ADC} + (2 + N + STC + PC + DM) \times T_{ADCI}$	$\mu\text{s}$	N = 8, 10, 12 for N-bit conversion $T_{ADC} = 1 / f_{PERIPH}$ $T_{ADCI} = 1 / f_{ADCI}$

- STC defines additional clock cycles to extend the sample time
- PC adds two cycles if post-calibration is enabled
- DM adds one cycle for an extended conversion time of the MSB

### Conversion Time Examples

System assumptions:

$$f_{ADC} = 120 \text{ MHz i.e. } t_{ADC} = 8.33 \text{ ns, DIVA} = 3, f_{ADCI} = 30 \text{ MHz i.e. } t_{ADCI} = 33.3 \text{ ns}$$

According to the given formulas the following minimum conversion times can be achieved (STC = 0, DM = 0):

12-bit post-calibrated conversion (PC = 2):

$$t_{CN12C} = (2 + 12 + 2) \times t_{ADCI} + 2 \times t_{ADC} = 16 \times 33.3 \text{ ns} + 2 \times 8.33 \text{ ns} = 550 \text{ ns}$$

12-bit uncalibrated conversion:

$$t_{CN12} = (2 + 12) \times t_{ADCI} + 2 \times t_{ADC} = 14 \times 33.3 \text{ ns} + 2 \times 8.33 \text{ ns} = 483 \text{ ns}$$

10-bit uncalibrated conversion:

$$t_{CN10} = (2 + 10) \times t_{ADCI} + 2 \times t_{ADC} = 12 \times 33.3 \text{ ns} + 2 \times 8.33 \text{ ns} = 417 \text{ ns}$$

8-bit uncalibrated:

$$t_{CN8} = (2 + 8) \times t_{ADCI} + 2 \times t_{ADC} = 10 \times 33.3 \text{ ns} + 2 \times 8.33 \text{ ns} = 350 \text{ ns}$$

### 3.2.3 Digital to Analog Converters (DAC)

*Note: These parameters are not subject to production test, but verified by design and/or characterization.*

**Electrical Parameters**
**Table 25 DAC Parameters (Operating Conditions apply)**

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
RMS supply current	$I_{DD}$	CC	–	2.5	4	mA	per active DAC channel, without load currents of DAC outputs
Resolution	$RES$	CC	–	12	–	Bit	
Update rate	$f_{URATE\_A}$	CC	–		2	Msam ple/s	data rate, where DAC can follow 64 LSB code jumps to $\pm 1$ LSB accuracy
Update rate	$f_{URATE\_F}$	CC	–		5	Msam ple/s	data rate, where DAC can follow 64 LSB code jumps to $\pm 4$ LSB accuracy
Settling time	$t_{SETTLE}$	CC	–	1	2	$\mu$ s	at full scale jump, output voltage reaches target value $\pm 20$ LSB
Slew rate	$SR$	CC	2	5	–	V/ $\mu$ s	
Minimum output voltage	$V_{OUT\_MIN}$	CC	–	0.3	–	V	code value unsigned: 000 <sub>H</sub> ; signed: 800 <sub>H</sub>
Maximum output voltage	$V_{OUT\_MAX}$	CC	–	2.5	–	V	code value unsigned: FFF <sub>H</sub> ; signed: 7FF <sub>H</sub>
Integral non-linearity	$INL$	CC	-4	$\pm 2.5$	4	LSB	$R_L \geq 5$ kOhm, $C_L \leq 50$ pF
Differential non-linearity	$DNL$	CC	-2	$\pm 1$	2	LSB	$R_L \geq 5$ kOhm, $C_L \leq 50$ pF
Offset error	$ED_{OFF}$	CC		$\pm 20$		mV	
Gain error	$ED_{G\_IN}$	CC	-6.5	-1.5	3	%	
Startup time	$t_{STARTUP}$	CC	–	15	30	$\mu$ s	time from output enabling till code valid $\pm 16$ LSB



**Electrical Parameters**

**Table 25 DAC Parameters (Operating Conditions apply) (cont'd)**

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
3dB Bandwidth of Output Buffer	$f_{C1}$	CC	2.5	5	–	MHz	verified by design
Output sourcing current	$I_{OUT\_SOURCE}$	CC	–	-30	–	mA	
Output sinking current	$I_{OUT\_SINK}$	CC	–	0.6	–	mA	
Output resistance	$R_{OUT}$	CC	–	50	–	Ohm	
Load resistance	$R_L$	SR	5	–	–	kOhm	
Load capacitance	$C_L$	SR	–	–	50	pF	
Signal-to-Noise Ratio	SNR	CC	–	70	–	dB	examination bandwidth < 25 kHz
Total Harmonic Distortion	THD	CC	–	70	–	dB	examination bandwidth < 25 kHz
Power Supply Rejection Ratio	PSRR	CC	–	56	–	dB	to $V_{DDA}$ verified by design

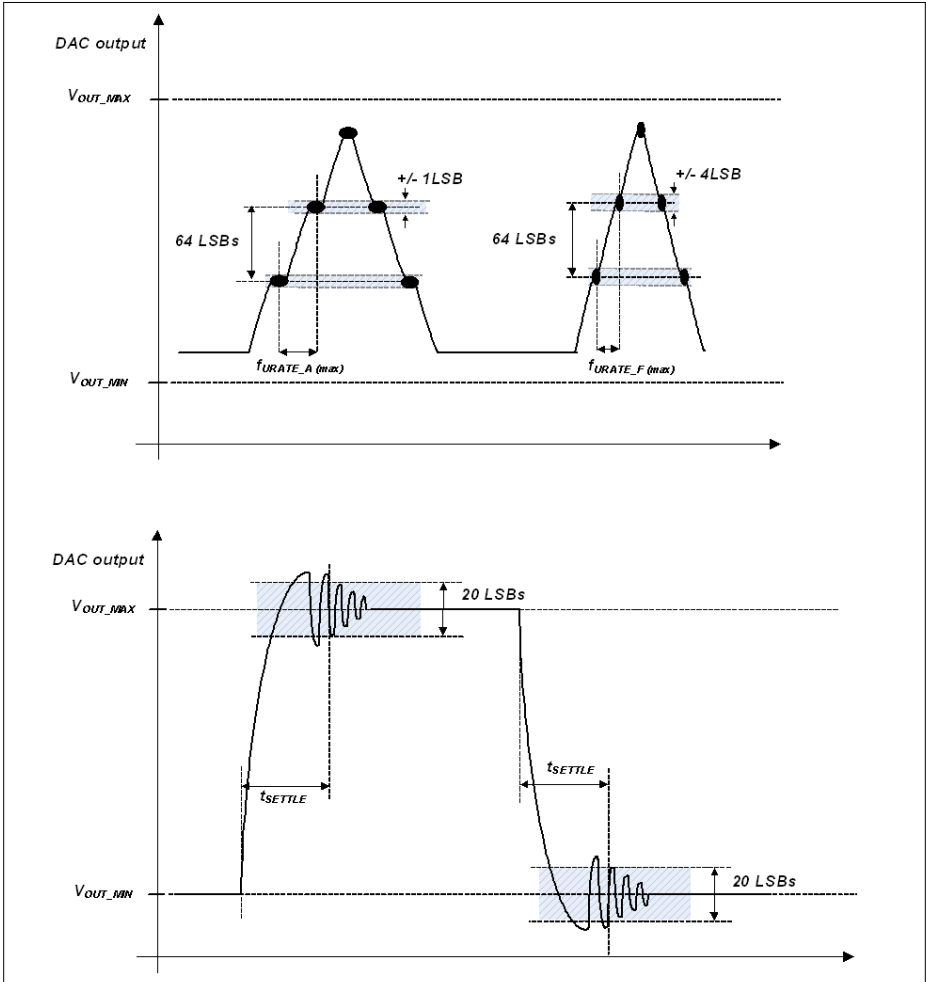
**Conversion Calculation**

Unsigned:

$$DACxDATA = 4095 \times (V_{OUT} - V_{OUT\_MIN}) / (V_{OUT\_MAX} - V_{OUT\_MIN})$$

Signed:

$$DACxDATA = 4095 \times (V_{OUT} - V_{OUT\_MIN}) / (V_{OUT\_MAX} - V_{OUT\_MIN}) - 2048$$



**Figure 17 DAC Conversion Examples**

### 3.2.4 Out-of-Range Comparator (ORC)

The Out-of-Range Comparator (ORC) triggers on analog input voltages ( $V_{AIN}$ ) above the analog reference<sup>1)</sup> ( $V_{AREF}$ ) on selected input pins (GxORCy) and generates a service request trigger (GxORCOUTy).

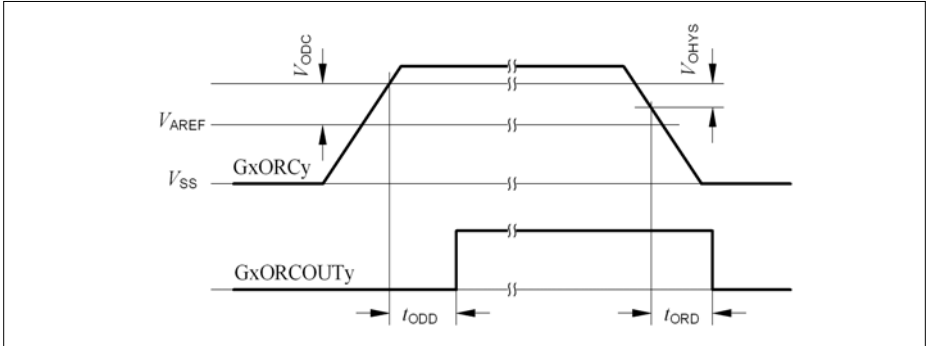
*Note: These parameters are not subject to production test, but verified by design and/or characterization.*

The parameters in **Table 26** apply for the maximum reference voltage  $V_{AREF} = V_{DDA} + 50 \text{ mV}$ .

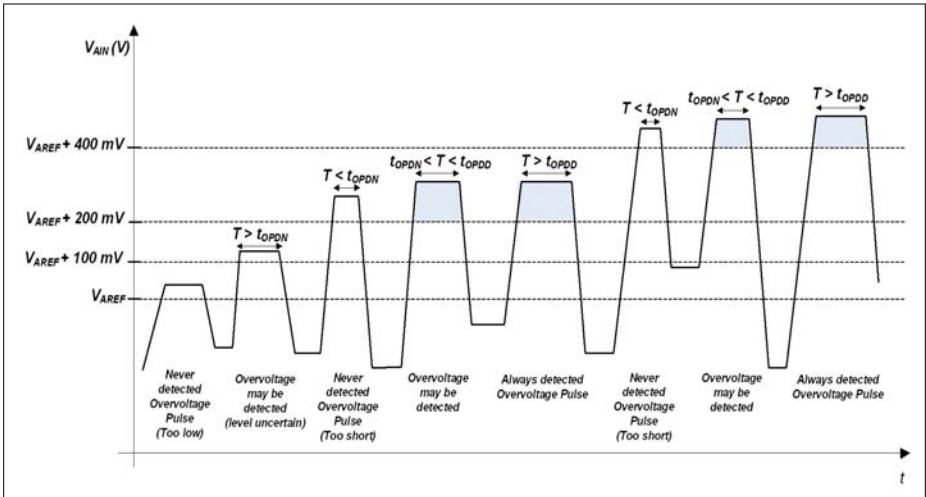
**Table 26 ORC Parameters** (Operating Conditions apply)

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
DC Switching Level	$V_{ODC}$	CC	100	125	200	mV	$V_{AIN} \geq V_{AREF} + V_{ODC}$
Hysteresis	$V_{OHYS}$	CC	50	–	$V_{ODC}$	mV	
Detection Delay of a persistent Overvoltage	$t_{ODD}$	CC	55	–	450	ns	$V_{AIN} \geq V_{AREF} + 200 \text{ mV}$
			45	–	105	ns	$V_{AIN} \geq V_{AREF} + 400 \text{ mV}$
Always detected Overvoltage Pulse	$t_{OPDD}$	CC	440	–	–	ns	$V_{AIN} \geq V_{AREF} + 200 \text{ mV}$
			90	–	–	ns	$V_{AIN} \geq V_{AREF} + 400 \text{ mV}$
Never detected Overvoltage Pulse	$t_{OPDN}$	CC	–	–	49	ns	$V_{AIN} \geq V_{AREF} + 200 \text{ mV}$
			–	–	30	ns	$V_{AIN} \geq V_{AREF} + 400 \text{ mV}$
Release Delay	$t_{ORD}$	CC	65	–	105	ns	$V_{AIN} \leq V_{AREF}$
Enable Delay	$t_{OED}$	CC	–	100	200	ns	

1) Always the standard VADC reference, alternate references do not apply to the ORC.



**Figure 18 GxORCOUTy Trigger Generation**



**Figure 19 ORC Detection Ranges**

### 3.2.5 Die Temperature Sensor

The Die Temperature Sensor (DTS) measures the junction temperature  $T_J$ .

*Note: These parameters are not subject to production test, but verified by design and/or characterization.*

**Table 27 Die Temperature Sensor Parameters**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Temperature sensor range	$T_{SR}$ SR	-40	–	150	°C	
Linearity Error (to the below defined formula)	$\Delta T_{LE}$ CC	–	$\pm 1$	–	°C	per $\Delta T_J \leq 30$ °C
Offset Error	$\Delta T_{OE}$ CC	–	$\pm 6$	–	°C	$\Delta T_{OE} = T_J - T_{DTS}$ $V_{DDP} \leq 3.3$ V <sup>1)</sup>
Measurement time	$t_M$ CC	–	–	100	μs	
Start-up time after reset inactive	$t_{TSST}$ SR	–	–	10	μs	

1) At  $V_{DDP\_max} = 3.63$  V the typical offset error increases by an additional  $\Delta T_{OE} = \pm 1$  °C.

The following formula calculates the temperature measured by the DTS in [°C] from the RESULT bit field of the DTSSTAT register.

$$\text{Temperature } T_{DTS} = (\text{RESULT} - 605) / 2.05 \text{ [°C]}$$

This formula and the values defined in **Table 27** apply with the following calibration values:

- DTSCON.BGTRIM =  $8_H$
- DTSCON.REFTRIM =  $4_H$

### 3.2.6 USB OTG Interface DC Characteristics

The Universal Serial Bus (USB) Interface is compliant to the USB Rev. 2.0 Specification and the OTG Specification Rev. 1.3. High-Speed Mode is not supported.

*Note: These parameters are not subject to production test, but verified by design and/or characterization.*

**Table 28 USB OTG VBUS and ID Parameters (Operating Conditions apply)**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
VBUS input voltage range	$V_{IN}$ CC	0.0	–	5.25	V	
A-device VBUS valid threshold	$V_{B1}$ CC	4.4	–	–	V	
A-device session valid threshold	$V_{B2}$ CC	0.8	–	2.0	V	
B-device session valid threshold	$V_{B3}$ CC	0.8	–	4.0	V	
B-device session end threshold	$V_{B4}$ CC	0.2	–	0.8	V	
VBUS input resistance to ground	$R_{VBUS\_IN}$ CC	40	–	100	kOhm	
B-device VBUS pull-up resistor	$R_{VBUS\_PU}$ CC	281	–	–	Ohm	Pull-up voltage = 3.0 V
B-device VBUS pull-down resistor	$R_{VBUS\_PD}$ CC	656	–	–	Ohm	
USB.ID pull-up resistor	$R_{UID\_PU}$ CC	14	–	25	kOhm	
VBUS input current	$I_{VBUS\_IN}$ CC	–	–	150	$\mu$ A	$0\text{ V} \leq V_{IN} \leq 5.25\text{ V}$ : $T_{AVG} = 1\text{ ms}$

**Electrical Parameters**

**Table 29 USB OTG Data Line (USB\_DP, USB\_DM) Parameters** (Operating Conditions apply)

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
Input low voltage	$V_{IL}$	SR	–	–	0.8	V	
Input high voltage (driven)	$V_{IH}$	SR	2.0	–	–	V	
Input high voltage (floating) <sup>1)</sup>	$V_{IHZ}$	SR	2.7	–	3.6	V	
Differential input sensitivity	$V_{DIS}$	CC	0.2	–	–	V	
Differential common mode range	$V_{CM}$	CC	0.8	–	2.5	V	
Output low voltage	$V_{OL}$	CC	0.0	–	0.3	V	1.5 kOhm pull-up to 3.6 V
Output high voltage	$V_{OH}$	CC	2.8	–	3.6	V	15 kOhm pull-down to 0 V
DP pull-up resistor (idle bus)	$R_{PUI}$	CC	900	–	1 575	Ohm	
DP pull-up resistor (upstream port receiving)	$R_{PUA}$	CC	1 425	–	3 090	Ohm	
DP, DM pull-down resistor	$R_{PD}$	CC	14.25	–	24.8	kOhm	
Input impedance DP, DM	$Z_{INP}$	CC	300	–	–	kOhm	$0 V \leq V_{IN} \leq V_{DDP}$
Driver output resistance DP, DM	$Z_{DRV}$	CC	28	–	44	Ohm	

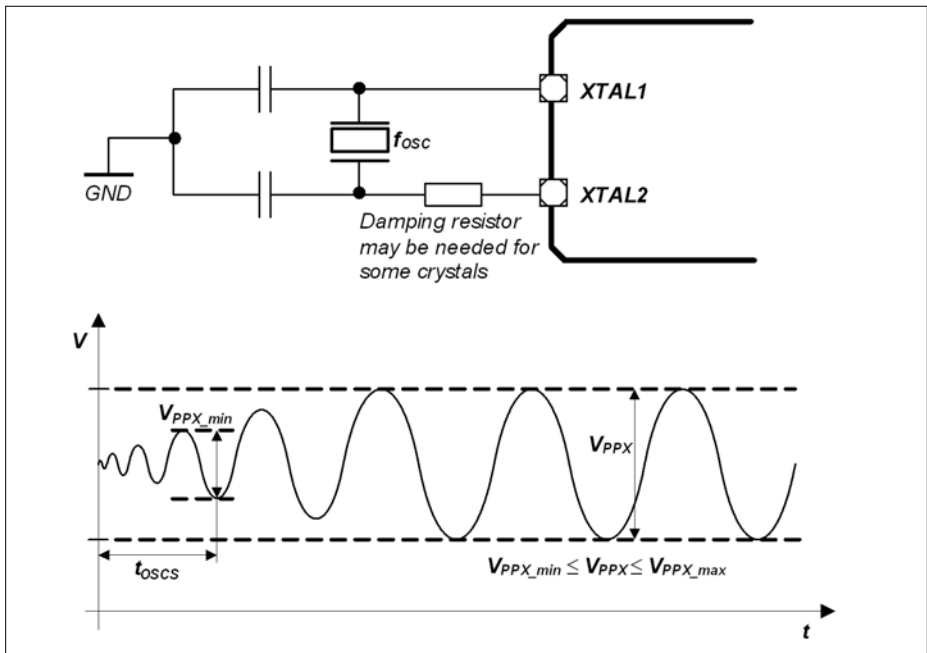
1) Measured at A-connector with 1.5 kOhm  $\pm$  5% to 3.3 V  $\pm$  0.3 V connected to USB\_DP or USB\_DM and at B-connector with 15 kOhm  $\pm$  5% to ground connected to USB\_DP and USB\_DM.

### 3.2.7 Oscillator Pins

*Note: It is strongly recommended to measure the oscillation allowance (negative resistance) in the final target system (layout) to determine the optimal parameters for the oscillator operation. Please refer to the limits specified by the crystal or ceramic resonator supplier.*

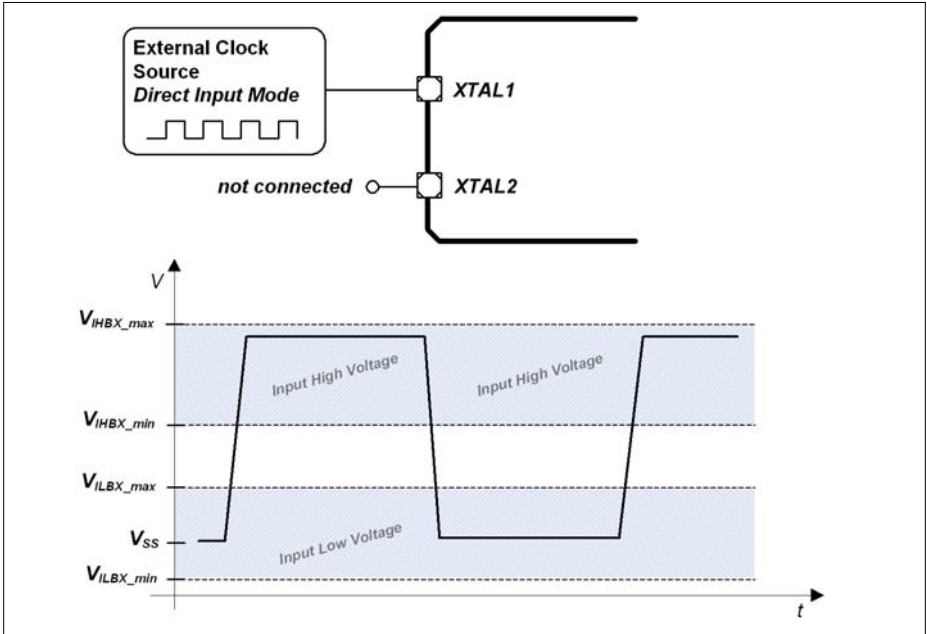
*Note: These parameters are not subject to production test, but verified by design and/or characterization.*

The oscillator pins can be operated with an external crystal (see [Figure 20](#)) or in direct input mode (see [Figure 21](#)).



**Figure 20 Oscillator in Crystal Mode**





**Figure 21** Oscillator in Direct Input Mode

**Table 30 OSC\_XTAL Parameters**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input frequency	$f_{\text{OSC}}$ SR	4	–	40	MHz	Direct Input Mode selected
		4	–	25	MHz	External Crystal Mode selected
Oscillator start-up time <sup>1)2)</sup>	$t_{\text{OSCS}}$ CC	–	–	10	ms	
Input voltage at XTAL1	$V_{\text{IX}}$ SR	-0.5	–	$V_{\text{DDP}} + 0.5$	V	
Input amplitude (peak-to-peak) at XTAL1 <sup>2)3)</sup>	$V_{\text{PPX}}$ SR	$0.4 \times V_{\text{DDP}}$	–	$V_{\text{DDP}} + 1.0$	V	
Input high voltage at XTAL1 <sup>4)</sup>	$V_{\text{IHBX}}$ SR	1.0	–	$V_{\text{DDP}} + 0.5$	V	
Input low voltage at XTAL1 <sup>4)</sup>	$V_{\text{ILBX}}$ SR	-0.5	–	0.4	V	
Input leakage current at XTAL1	$I_{\text{ILX1}}$ CC	-100	–	100	nA	Oscillator power down $0 \text{ V} \leq V_{\text{IX}} \leq V_{\text{DDP}}$

1)  $t_{\text{OSCS}}$  is defined from the moment the oscillator is enabled with SCU\_OSCHPCTRL.MODE until the oscillations reach an amplitude at XTAL1 of  $0.4 \times V_{\text{DDP}}$ .

2) The external oscillator circuitry must be optimized by the customer and checked for negative resistance and amplitude as recommended and specified by crystal suppliers.

3) If the shaper unit is enabled and not bypassed.

4) If the shaper unit is bypassed, dedicated DC-thresholds have to be met.

**Table 31 RTC\_XTAL Parameters**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input frequency	$f_{OSC}$ SR	–	32.768	–	kHz	
Oscillator start-up time <sup>1)2)3)</sup>	$t_{OSCS}$ CC	–	–	5	s	
Input voltage at RTC_XTAL1	$V_{IX}$ SR	-0.3	–	$V_{BAT} + 0.3$	V	
Input amplitude (peak-to-peak) at RTC_XTAL1 <sup>2)4)</sup>	$V_{PPX}$ SR	0.4	–	–	V	
Input high voltage at RTC_XTAL1 <sup>5)</sup>	$V_{IHBX}$ SR	$0.6 \times V_{BAT}$	–	$V_{BAT} + 0.3$	V	
Input low voltage at RTC_XTAL1 <sup>5)</sup>	$V_{ILBX}$ SR	-0.3	–	$0.36 \times V_{BAT}$	V	
Input Hysteresis for RTC_XTAL1 <sup>5)6)</sup>	$V_{HYSX}$ CC	$0.1 \times V_{BAT}$		–	V	$3.0 \text{ V} \leq V_{BAT} < 3.6 \text{ V}$
		$0.03 \times V_{BAT}$		–	V	$V_{BAT} < 3.0 \text{ V}$
Input leakage current at RTC_XTAL1	$I_{ILX1}$ CC	-100	–	100	nA	Oscillator power down $0 \text{ V} \leq V_{IX} \leq V_{BAT}$

- $t_{OSCS}$  is defined from the moment the oscillator is enabled by the user with SCU\_OSCULCTRL.MODE until the oscillations reach an amplitude at RTC\_XTAL1 of 400 mV.
- The external oscillator circuitry must be optimized by the customer and checked for negative resistance and amplitude as recommended and specified by crystal suppliers.
- For a reliable start of the oscillation in crystal mode it is required that  $V_{BAT} \geq 3.0 \text{ V}$ . A running oscillation is maintained across the full  $V_{BAT}$  voltage range.
- If the shaper unit is enabled and not bypassed.
- If the shaper unit is bypassed, dedicated DC-thresholds have to be met.
- Hysteresis is implemented to avoid metastable states and switching due to internal ground bounce. It can not be guaranteed that it suppresses switching due to external system noise.

### 3.2.8 Power Supply Current

The total power supply current defined below consists of a leakage and a switching component.

Application relevant values are typically lower than those given in the following tables, and depend on the customer's system operating conditions (e.g. thermal connection or used application configurations).

*Note: These parameters are not subject to production test, but verified by design and/or characterization.*

If not stated otherwise, the operating conditions for the parameters in the following table are:

$$V_{DDP} = 3.3 \text{ V}, T_A = 25 \text{ }^{\circ}\text{C}$$

**Table 32 Power Supply Parameters**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Active supply current <sup>(1)(10)</sup> Peripherals enabled Frequency: $f_{CPU} / f_{PERIPH} / f_{CCU}$ in MHz	$I_{DDPA}$ CC	–	122	–	mA	120 / 120 / 120
		–	110	–		120 / 60 / 60
		–	85	–		60 / 60 / 120
		–	65	–		24 / 24 / 24
		–	52	–		1 / 1 / 1
Active supply current Code execution from RAM Flash in Sleep mode	$I_{DDPA}$ CC	–	98	–	mA	120 / 120 / 120
		–	80	–		120 / 60 / 60
Active supply current <sup>(2)</sup> Peripherals disabled Frequency: $f_{CPU} / f_{PERIPH} / f_{CCU}$ in MHz	$I_{DDPA}$ CC	–	115	–	mA	120 / 120 / 120
		–	105	–		120 / 60 / 60
		–	80	–		60 / 60 / 120
		–	63	–		24 / 24 / 24
		–	50	–		1 / 1 / 1
Sleep supply current <sup>(3)</sup> Peripherals enabled Frequency: $f_{CPU} / f_{PERIPH} / f_{CCU}$ in MHz	$I_{DDPS}$ CC	–	115	–	mA	120 / 120 / 120
		–	105	–		120 / 60 / 60
		–	83	–		60 / 60 / 120
		–	60	–		24 / 24 / 24
		–	48	–		1 / 1 / 1
		$f_{CPU} / f_{PERIPH} / f_{CCU}$ in kHz	–	46		–

**Electrical Parameters**
**Table 32 Power Supply Parameters**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Sleep supply current <sup>4)</sup> Peripherals disabled Frequency: $f_{CPU} / f_{PERIPH} / f_{CCU}$ in MHz	$I_{DDPS}$ CC	-	110	-	mA	120 / 120 / 120
		-	100	-		120 / 60 / 60
		-	77	-		60 / 60 / 120
		-	59	-		24 / 24 / 24
		-	48	-		1 / 1 / 1
		-	46	-		100 / 100 / 100
$f_{CPU} / f_{PERIPH} / f_{CCU}$ in kHz Deep Sleep supply current <sup>5)</sup> Flash in Sleep mode Frequency: $f_{CPU} / f_{PERIPH} / f_{CCU}$ in MHz $f_{CPU} / f_{PERIPH} / f_{CCU}$ in kHz	$I_{DDPD}$ CC	-	20	-	mA	24 / 24 / 24
		-	12	-		4 / 4 / 4
		-	10	-		1 / 1 / 1
		-	6	-		100 / 100 / 100 <sup>6)</sup>
Hibernate supply current RTC on <sup>7)</sup>	$I_{DDPH}$ CC	-	10	-	$\mu$ A	$V_{BAT} = 3.3$ V
		-	7.5	-		$V_{BAT} = 2.4$ V
		-	6.2	-		$V_{BAT} = 2.0$ V
Hibernate supply current RTC off <sup>8)</sup>	$I_{DDPH}$ CC	-	9.2	-	$\mu$ A	$V_{BAT} = 3.3$ V
		-	6.7	-		$V_{BAT} = 2.4$ V
		-	5.6	-		$V_{BAT} = 2.0$ V
Worst case active supply current <sup>9)</sup>	$I_{DDPA}$ CC	-	-	180 <sup>10)</sup>	mA	$V_{DDP} = 3.6$ V, $T_J = 150$ °C
$V_{DDA}$ power supply current	$I_{DDA}$ CC	-	-	- <sup>11)</sup>	mA	
$I_{DDP}$ current at $\overline{PORST}$ Low	$I_{DDP\_PORST}$ CC	-	-	16	mA	$V_{DDP} = 3.6$ V, $T_J = 150$ °C
Power Dissipation	$P_{DISS}$ CC	-	-	1	W	$V_{DDP} = 3.6$ V, $T_J = 150$ °C
Wake-up time from Sleep to Active mode	$t_{SSA}$ CC	-	6	-	cycles	

**Table 32 Power Supply Parameters**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Wake-up time from Deep Sleep to Active mode		–	–	–	ms	Defined by the wake-up of the Flash module, see <a href="#">Section 3.2.9</a>
Wake-up time from Hibernate mode		–	–	–	ms	Wake-up via power-on reset event, see <a href="#">Section 3.3.2</a>

- 1) CPU executing code from Flash, all peripherals idle.
- 2) CPU executing code from Flash.
- 3) CPU in sleep, all peripherals idle, Flash in Active mode.
- 4) CPU in sleep, Flash in Active mode.
- 5) CPU in sleep, peripherals disabled, after wake-up code execution from RAM.
- 6) To wake-up the Flash from its Sleep mode,  $f_{CPU} \geq 1$  MHz is required.
- 7) OSC\_ULP operating with external crystal on RTC\_XTAL
- 8) OSC\_ULP off, Hibernate domain operating with OSC\_S1 clock
- 9) Test Power Loop:  $f_{SYS} = 120$  MHz, CPU executing benchmark code from Flash, all CCUs in 100kHz timer mode, all ADC groups in continuous conversion mode, USICs as SPI in internal loop-back mode, CAN in 500kHz internal loop-back mode, interrupt triggered DMA block transfers to parity protected RAMs and FCE, DTS measurements and FPU calculations.  
The power consumption of each customer application will most probably be lower than this value, but must be evaluated separately.
- 10)  $I_{DDP}$  decreases typically by approximately 6 mA when  $f_{SYS}$  decreases by 10 MHz, at constant  $T_J$
- 11) Sum of currents of all active converters (ADC and DAC)

### 3.2.9 Flash Memory Parameters

Note: These parameters are not subject to production test, but verified by design and/or characterization.

**Table 33 Flash Memory Parameters**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Erase Time per 256 Kbyte Sector	$t_{ERP}$ CC	–	5	5.5	s	
Erase Time per 64 Kbyte Sector	$t_{ERP}$ CC	–	1.2	1.4	s	
Erase Time per 16 Kbyte Logical Sector	$t_{ERP}$ CC	–	0.3	0.4	s	
Program time per page <sup>1)</sup>	$t_{PRP}$ CC	–	5.5	11	ms	
Erase suspend delay	$t_{FL\_ErSusp}$ CC	–	–	15	ms	
Wait time after margin change	$t_{FL\_MarginDel}$ CC	10	–	–	μs	
Wake-up time	$t_{WU}$ CC	–	–	270	μs	
Read access time	$t_a$ CC	22	–	–	ns	For operation with $1/f_{CPU} < t_a$ wait states must be configured <sup>2)</sup>
Data Retention Time, Physical Sector <sup>3)4)</sup>	$t_{RET}$ CC	20	–	–	years	Max. 1000 erase/program cycles
Data Retention Time, Logical Sector <sup>3)4)</sup>	$t_{RETL}$ CC	20	–	–	years	Max. 100 erase/program cycles
Data Retention Time, User Configuration Block (UCB) <sup>3)4)</sup>	$t_{RTU}$ CC	20	–	–	years	Max. 4 erase/program cycles per UCB

1) In case the Program Verify feature detects weak bits, these bits will be programmed once more. The reprogramming takes an additional time of 5.5 ms.

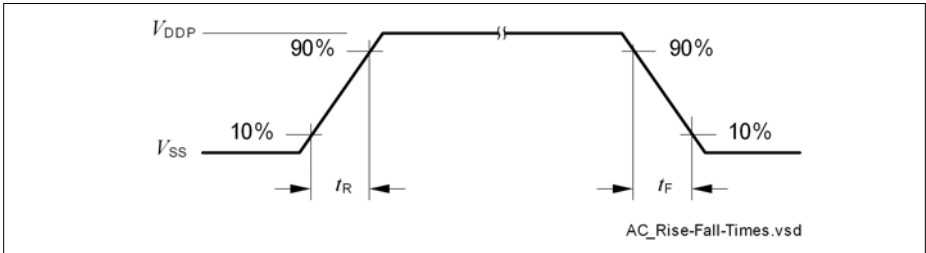
2) The following formula applies to the wait state configuration:  $FCON.WSPFLASH \times (1/f_{CPU}) \geq t_a$ .

3) Storage and inactive time included.

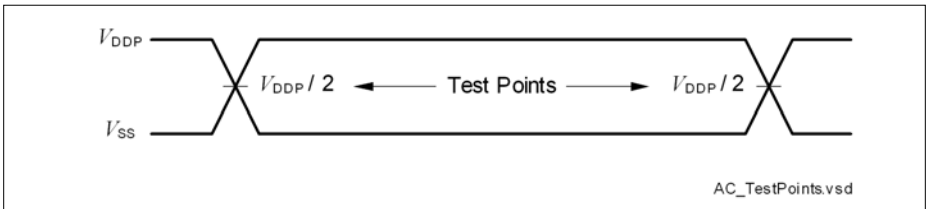
4) Values given are valid for an average weighted junction temperature of  $T_J = 110^\circ\text{C}$ .

### 3.3 AC Parameters

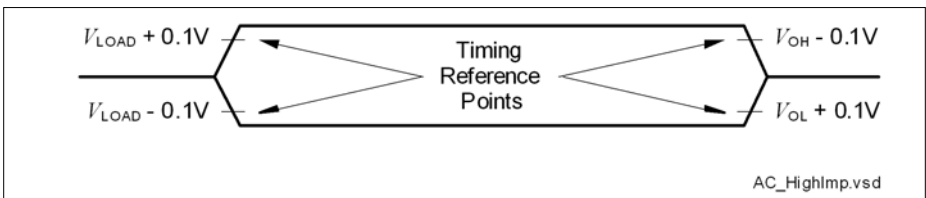
#### 3.3.1 Testing Waveforms



**Figure 22 Rise/Fall Time Parameters**



**Figure 23 Testing Waveform, Output Delay**



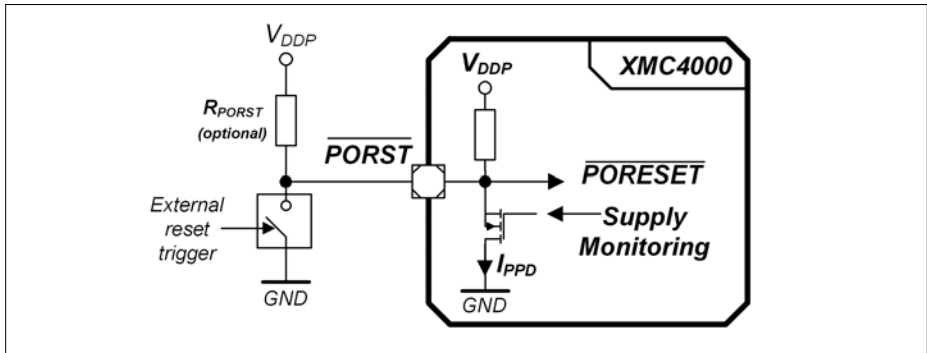
**Figure 24 Testing Waveform, Output High Impedance**



### 3.3.2 Power-Up and Supply Monitoring

$\overline{\text{PORST}}$  is always asserted when  $V_{\text{DDP}}$  and/or  $V_{\text{DDC}}$  violate the respective thresholds.

*Note: These parameters are not subject to production test, but verified by design and/or characterization.*



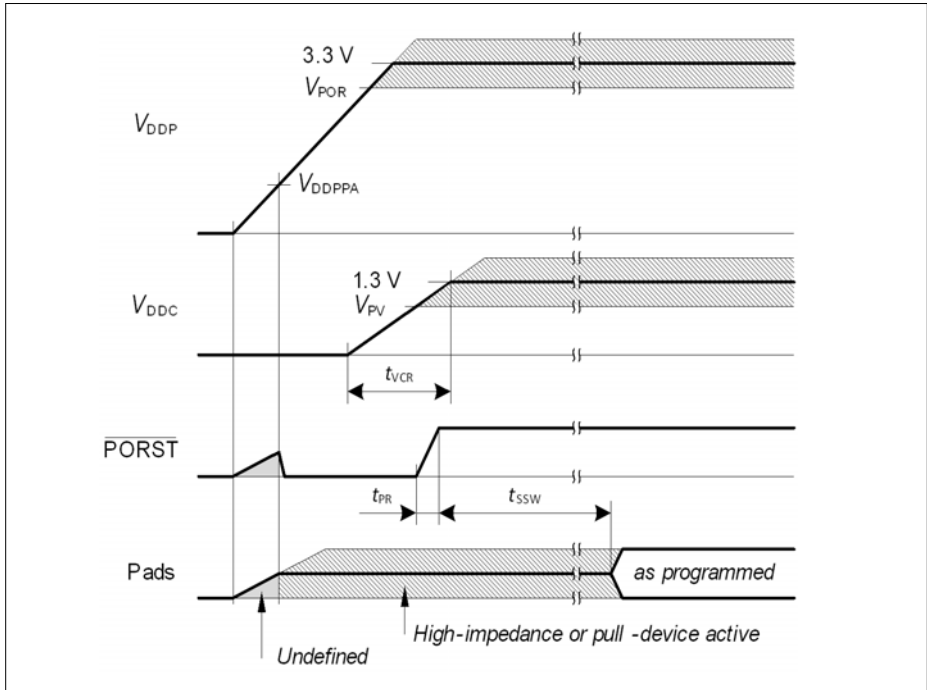
**Figure 25**  $\overline{\text{PORST}}$  Circuit

**Table 34** Supply Monitoring Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Digital supply voltage reset threshold	$V_{\text{POR}}$ CC	2.79 <sup>1)</sup>	–	3.05 <sup>2)</sup>	V	3)
Core supply voltage reset threshold	$V_{\text{PV}}$ CC	–	–	1.17	V	
$V_{\text{DDP}}$ voltage to ensure defined pad states	$V_{\text{DDPPA}}$ CC	–	1.0	–	V	
$\overline{\text{PORST}}$ rise time	$t_{\text{PR}}$ SR	–	–	2	$\mu\text{s}$	4)
Startup time from power-on reset with code execution from Flash	$t_{\text{SSW}}$ CC	–	2.5	3.5	ms	Time to the first user code instruction
$V_{\text{DDC}}$ ramp up time	$t_{\text{VCR}}$ CC	–	550	–	$\mu\text{s}$	Ramp up after power-on or after a reset triggered by a violation of $V_{\text{POR}}$ or $V_{\text{PV}}$

1) Minimum threshold for reset assertion.

- 2) Maximum threshold for reset deassertion.
- 3) The  $V_{DDP}$  monitoring has a typical hysteresis of  $V_{PORHYS} = 180\text{ mV}$ .
- 4) If  $t_{PR}$  is not met, low spikes on  $\overline{\text{PORST}}$  may be seen during start up (e.g. reset pulses generated by the supply monitoring due to a slow ramping  $V_{DDP}$ ).



**Figure 26 Power-Up Behavior**

### 3.3.3 Power Sequencing

While starting up and shutting down as well as when switching power modes of the system it is important to limit the current load steps. A typical cause for such load steps is changing the CPU frequency  $f_{CPU}$ . Load steps exceeding the below defined values may cause a power on reset triggered by the supply monitor.

*Note: These parameters are not subject to production test, but verified by design and/or characterization.*

**Table 35 Power Sequencing Parameters**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Positive Load Step Current	$\Delta I_{PLS}$ SR	-	-	50	mA	Load increase on $V_{DDP}$ $\Delta t \leq 10$ ns
Negative Load Step Current	$\Delta I_{NLS}$ SR	-	-	150	mA	Load decrease on $V_{DDP}$ $\Delta t \leq 10$ ns
$V_{DDC}$ Voltage Over- / Undershoot from Load Step	$\Delta V_{LS}$ CC	-	-	$\pm 100$	mV	For maximum positive or negative load step
Positive Load Step Settling Time	$t_{PLSS}$ SR	50	-	-	$\mu$ s	
Negative Load Step Settling Time	$t_{NLSS}$ SR	100	-	-	$\mu$ s	
External Buffer Capacitor on $V_{DDC}$	$C_{EXT}$ SR	-	10	-	$\mu$ F	In addition $C = 100$ nF capacitor on each $V_{DDC}$ pin

### Positive Load Step Examples

System assumptions:

$f_{CPU} = f_{SYS}$ , target frequency  $f_{CPU} = 120$  MHz, main PLL  $f_{VCO} = 480$  MHz, stepping done by K2 divider,  $t_{PLSS}$  between individual steps:

24 MHz - 48 MHz - 68 MHz - 96 MHz - 120 MHz (K2 steps 20 - 10 - 7 - 5 - 4)

24 MHz - 68 MHz - 96 MHz - 120 MHz (K2 steps 20 - 7 - 5 - 4)

24 MHz - 68 MHz - 120 MHz (K2 steps 20 - 7 - 4)

### 3.3.4 Phase Locked Loop (PLL) Characteristics

*Note: These parameters are not subject to production test, but verified by design and/or characterization.*

#### Main and USB PLL

**Table 36 PLL Parameters**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Accumulated Jitter	$D_p$ CC	–	–	±5	ns	accumulated over 300 cycles $f_{SYS} = 120$ MHz
Duty Cycle <sup>1)</sup>	$D_{DC}$ CC	46	50	54	%	Low pulse to total period, assuming an ideal input clock source
PLL base frequency	$f_{PLLBASE}$ CC	30	–	140	MHz	
VCO input frequency	$f_{REF}$ CC	4	–	16	MHz	
VCO frequency range	$f_{VCO}$ CC	260	–	520	MHz	
PLL lock-in time	$t_L$ CC	–	–	400	μs	

1) 50% for even K2 divider values,  $50 \pm (10/K2)$  for odd K2 divider values.

### 3.3.5 Internal Clock Source Characteristics

*Note: These parameters are not subject to production test, but verified by design and/or characterization.*

#### Fast Internal Clock Source

**Table 37 Fast Internal Clock Parameters**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Nominal frequency	$f_{\text{OFINC}}$ CC	–	36.5	–	MHz	not calibrated
		–	24	–	MHz	calibrated
Accuracy	$\Delta f_{\text{OFI}}$ CC	-0.5	–	0.5	%	automatic calibration <sup>1)2)</sup>
		-15	–	15	%	factory calibration, $V_{\text{DDP}} = 3.3 \text{ V}$
		-25	–	25	%	no calibration, $V_{\text{DDP}} = 3.3 \text{ V}$
		-7	–	7	%	Variation over voltage range <sup>3)</sup> $3.13 \text{ V} \leq V_{\text{DDP}} \leq 3.63 \text{ V}$
Start-up time	$t_{\text{OFIS}}$ CC	–	50	–	$\mu\text{s}$	

1) Error in addition to the accuracy of the reference clock.

2) Automatic calibration compensates variations of the temperature and in the  $V_{\text{DDP}}$  supply voltage.

3) Deviations from the nominal  $V_{\text{DDP}}$  voltage induce an additional error to the uncalibrated and/or factory calibrated oscillator frequency.

**Slow Internal Clock Source**

**Table 38 Slow Internal Clock Parameters**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Nominal frequency	$f_{OSI}$ CC	–	32.768	–	kHz	
Accuracy	$\Delta f_{OSI}$ CC	-4	–	4	%	$V_{BAT} = \text{const.}$ $0\text{ }^{\circ}\text{C} \leq T_A \leq 85\text{ }^{\circ}\text{C}$
		-5	–	5	%	$V_{BAT} = \text{const.}$ $T_A < 0\text{ }^{\circ}\text{C}$ or $T_A > 85\text{ }^{\circ}\text{C}$
		-5	–	5	%	$2.4\text{ V} \leq V_{BAT}$ , $T_A = 25\text{ }^{\circ}\text{C}$
		-10	–	10	%	$1.95\text{ V} \leq V_{BAT} < 2.4\text{ V}$ , $T_A = 25\text{ }^{\circ}\text{C}$
Start-up time	$t_{OSIS}$ CC	–	50	–	$\mu\text{s}$	

### 3.3.6 JTAG Interface Timing

The following parameters are applicable for communication through the JTAG debug interface. The JTAG module is fully compliant with IEEE1149.1-2000.

*Note: These parameters are not subject to production test, but verified by design and/or characterization.*

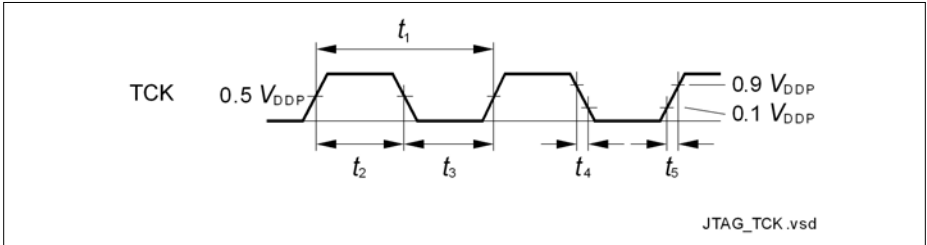
*Note: Operating conditions apply.*

**Table 39 JTAG Interface Timing Parameters**

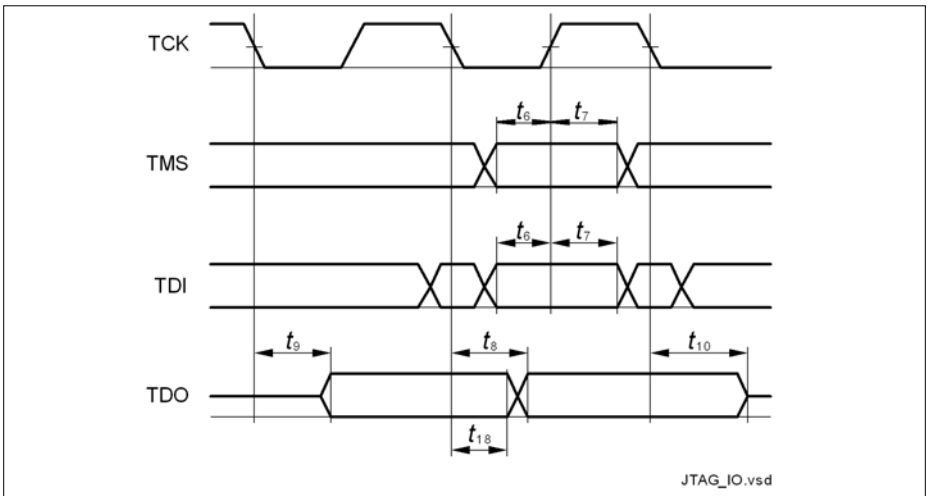
Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
TCK clock period	$t_1$ SR	25	–	–	ns	
TCK high time	$t_2$ SR	10	–	–	ns	
TCK low time	$t_3$ SR	10	–	–	ns	
TCK clock rise time	$t_4$ SR	–	–	4	ns	
TCK clock fall time	$t_5$ SR	–	–	4	ns	
TDI/TMS setup to TCK rising edge	$t_6$ SR	6	–	–	ns	
TDI/TMS hold after TCK rising edge	$t_7$ SR	6	–	–	ns	
TDO valid after TCK falling edge <sup>1)</sup> (propagation delay)	$t_8$ CC	–	–	13	ns	$C_L = 50$ pF
		3	–	–	ns	$C_L = 20$ pF
TDO hold after TCK falling edge <sup>1)</sup>	$t_{18}$ CC	2	–	–	ns	
TDO high imped. to valid from TCK falling edge <sup>1)2)</sup>	$t_9$ CC	–	–	14	ns	$C_L = 50$ pF
TDO valid to high imped. from TCK falling edge <sup>1)</sup>	$t_{10}$ CC	–	–	13.5	ns	$C_L = 50$ pF

1) The falling edge on TCK is used to generate the TDO timing.

2) The setup time for TDO is given implicitly by the TCK cycle time.



**Figure 27 Test Clock Timing (TCK)**



**Figure 28 JTAG Timing**



### 3.3.7 Serial Wire Debug Port (SW-DP) Timing

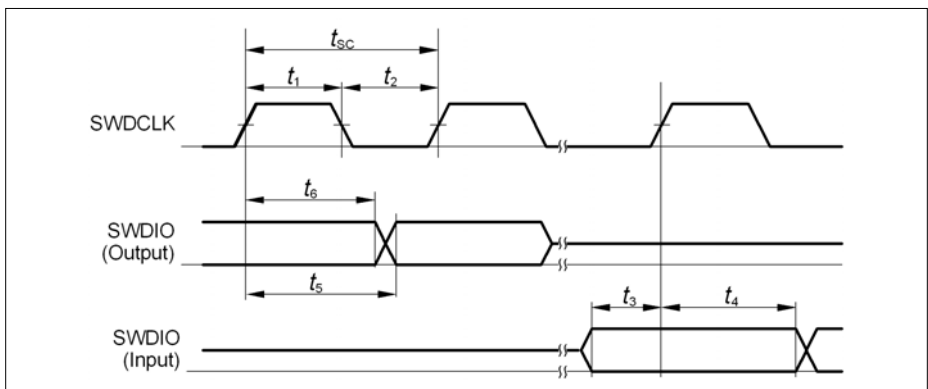
The following parameters are applicable for communication through the SW-DP interface.

*Note: These parameters are not subject to production test, but verified by design and/or characterization.*

*Note: Operating conditions apply.*

**Table 40 SWD Interface Timing Parameters** (Operating Conditions apply)

Parameter	Symbol	SR	Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
SWDCLK clock period	$t_{SC}$	SR	25	–	–	ns	$C_L = 30$ pF
			40	–	–	ns	$C_L = 50$ pF
SWDCLK high time	$t_1$	SR	10	–	500000	ns	
SWDCLK low time	$t_2$	SR	10	–	500000	ns	
SWDIO input setup to SWDCLK rising edge	$t_3$	SR	6	–	–	ns	
SWDIO input hold after SWDCLK rising edge	$t_4$	SR	6	–	–	ns	
SWDIO output valid time after SWDCLK rising edge	$t_5$	CC	–	–	17	ns	$C_L = 50$ pF
			–	–	13	ns	$C_L = 30$ pF
SWDIO output hold time from SWDCLK rising edge	$t_6$	CC	3	–	–	ns	



**Figure 29 SWD Timing**

### 3.3.8 Embedded Trace Macro Cell (ETM) Timing

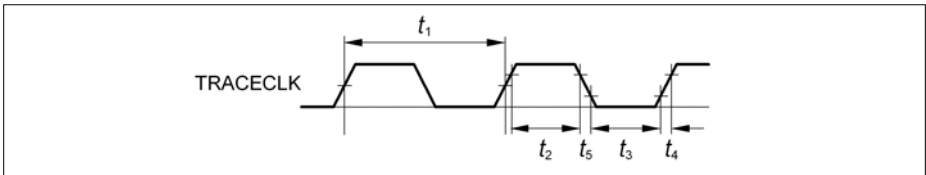
The data timing refers to the active clock edge. The XMC4500 ETM uses the half-rate clocking mode. In this mode both, the rising and falling clock edges are active clock edges.

*Note: These parameters are not subject to production test, but verified by design and/or characterization.*

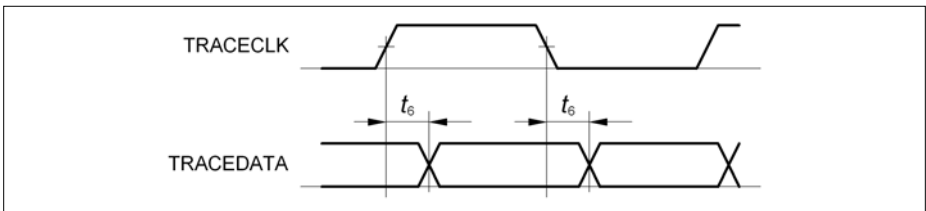
*Note: Operating conditions apply, with  $C_L \leq 15$  pF.*

**Table 41 ETM Interface Timing Parameters**

Parameter	Symbol	CC	Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
TRACECLK period	$t_1$	CC	16.7	–	–	ns	–
TRACECLK high time	$t_2$	CC	2	–	–	ns	–
TRACECLK low time	$t_3$	CC	2	–	–	ns	–
TRACECLK and TRACEDATA rise time	$t_4$	CC	–	–	3	ns	–
TRACECLK and TRACEDATA fall time	$t_5$	CC	–	–	3	ns	–
TRACEDATA output valid time	$t_6$	CC	-2	–	3	ns	–



**Figure 30 ETM Clock Timing**



**Figure 31 ETM Data Timing**

### 3.3.9 Peripheral Timing

#### 3.3.9.1 Delta-Sigma Demodulator Digital Interface Timing

The following parameters are applicable for the digital interface of the Delta-Sigma Demodulator (DSD).

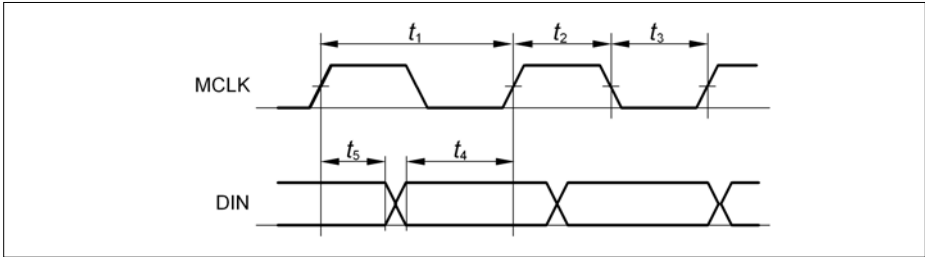
The data timing is relative to the active clock edge. Depending on the operation mode of the connected modulator that can be the rising and falling clock edge.

*Note: These parameters are not subject to production test, but verified by design and/or characterization.*

**Table 42 DSD Interface Timing Parameters**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
MCLK period in master mode	$t_1$ CC	33.3	–	–	ns	$t_1 \geq 4 \times t_{\text{PERIPH}}^{1)}$
MCLK high time in master mode	$t_2$ CC	9	–	–	ns	$t_2 > t_{\text{PERIPH}}^{1)}$
MCLK low time in master mode	$t_3$ CC	9	–	–	ns	$t_3 > t_{\text{PERIPH}}^{1)}$
MCLK period in slave mode	$t_1$ SR	33.3	–	–	ns	$t_1 \geq 4 \times t_{\text{PERIPH}}^{1)}$
MCLK high time in slave mode	$t_2$ SR	$t_{\text{PERIPH}}$	–	–	ns	<sup>1)</sup>
MCLK low time in slave mode	$t_3$ SR	$t_{\text{PERIPH}}$	–	–	ns	<sup>1)</sup>
DIN input setup time to the active clock edge	$t_4$ SR	$t_{\text{PERIPH}} + 4$	–	–	ns	<sup>1)</sup>
DIN input hold time from the active clock edge	$t_5$ SR	$t_{\text{PERIPH}} + 3$	–	–	ns	<sup>1)</sup>

<sup>1)</sup>  $t_{\text{PERIPH}} = 1 / f_{\text{PERIPH}}$



**Figure 32 DSD Data Timing**

### 3.3.9.2 Synchronous Serial Interface (USIC SSC) Timing

The following parameters are applicable for a USIC channel operated in SSC mode.

*Note: These parameters are not subject to production test, but verified by design and/or characterization.*

**Table 43 USIC SSC Master Mode Timing**

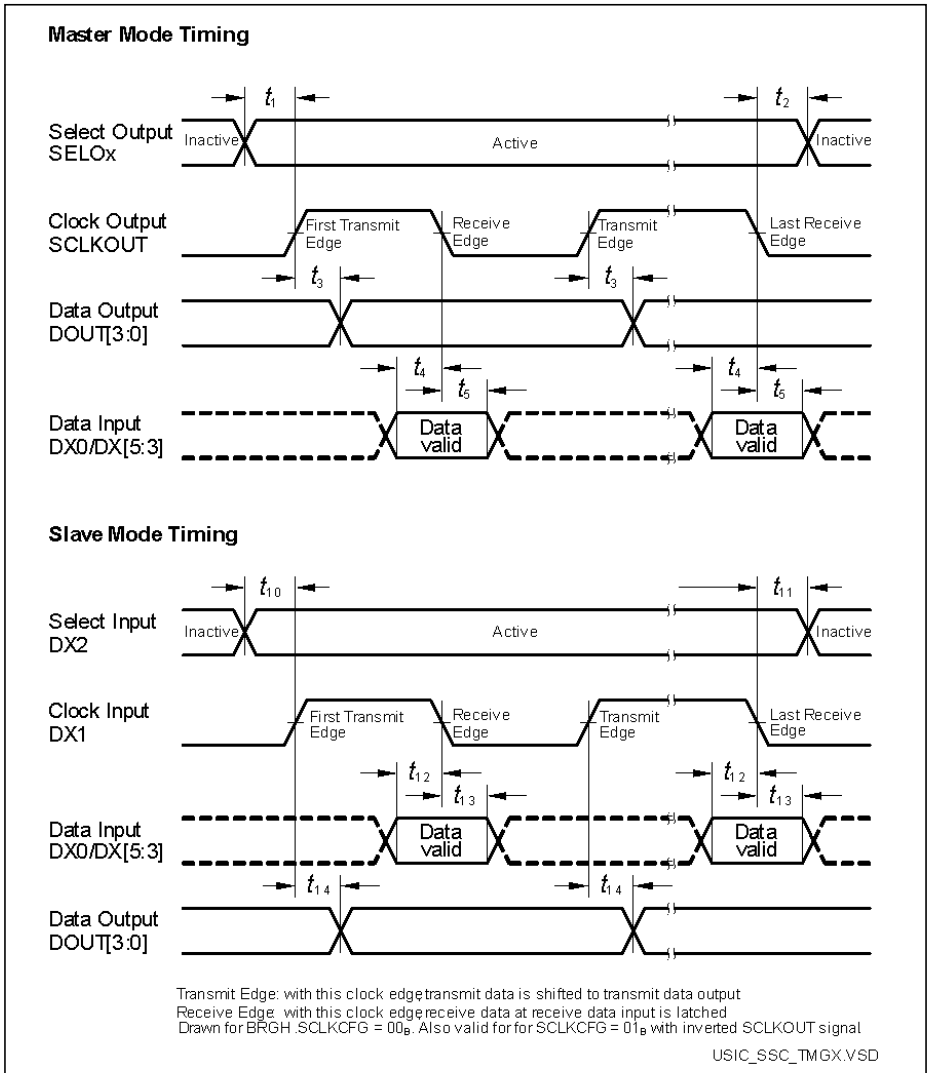
Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
SCLKOUT master clock period	$t_{CLK}$ CC	33.3	–	–	ns	
Slave select output SELO active to first SCLKOUT transmit edge	$t_1$ CC	$t_{PB} - 6.5^{1)}$	–	–	ns	
Slave select output SELO inactive after last SCLKOUT receive edge	$t_2$ CC	$t_{PB} - 8.5^{1)}$	–	–	ns	
Data output DOUT[3:0] valid time	$t_3$ CC	-6	–	8	ns	
Receive data input DX0/DX[5:3] setup time to SCLKOUT receive edge	$t_4$ SR	23	–	–	ns	
Data input DX0/DX[5:3] hold time from SCLKOUT receive edge	$t_5$ SR	1	–	–	ns	

1)  $t_{PB} = 1 / f_{PB}$

**Table 44 USIC SSC Slave Mode Timing**

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
DX1 slave clock period	$t_{CLK}$	SR	66.6	–	–	ns	
Select input DX2 setup to first clock input DX1 transmit edge <sup>1)</sup>	$t_{10}$	SR	3	–	–	ns	
Select input DX2 hold after last clock input DX1 receive edge <sup>1)</sup>	$t_{11}$	SR	4	–	–	ns	
Receive data input DX0/DX[5:3] setup time to shift clock receive edge <sup>1)</sup>	$t_{12}$	SR	6	–	–	ns	
Data input DX0/DX[5:3] hold time from clock input DX1 receive edge <sup>1)</sup>	$t_{13}$	SR	4	–	–	ns	
Data output DOUT[3:0] valid time	$t_{14}$	CC	0	–	24	ns	

1) This input timing is valid for asynchronous input signal handling of slave select input, shift clock input, and receive data input (bits DXnCR.DSEN = 0).



**Figure 33 USIC - SSC Master/Slave Mode Timing**

*Note: This timing diagram shows a standard configuration, for which the slave select signal is low-active, and the serial clock signal is not shifted and not inverted.*

### 3.3.9.3 Inter-IC (IIC) Interface Timing

The following parameters are applicable for a USIC channel operated in IIC mode.

*Note: These parameters are not subject to production test, but verified by design and/or characterization.*

**Table 45 USIC IIC Standard Mode Timing<sup>1)</sup>**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Fall time of both SDA and SCL	$t_1$ CC/SR	-	-	300	ns	
Rise time of both SDA and SCL	$t_2$ CC/SR	-	-	1000	ns	
Data hold time	$t_3$ CC/SR	0	-	-	μs	
Data set-up time	$t_4$ CC/SR	250	-	-	ns	
LOW period of SCL clock	$t_5$ CC/SR	4.7	-	-	μs	
HIGH period of SCL clock	$t_6$ CC/SR	4.0	-	-	μs	
Hold time for (repeated) START condition	$t_7$ CC/SR	4.0	-	-	μs	
Set-up time for repeated START condition	$t_8$ CC/SR	4.7	-	-	μs	
Set-up time for STOP condition	$t_9$ CC/SR	4.0	-	-	μs	
Bus free time between a STOP and START condition	$t_{10}$ CC/SR	4.7	-	-	μs	
Capacitive load for each bus line	$C_b$ SR	-	-	400	pF	

1) Due to the wired-AND configuration of an IIC bus system, the port drivers of the SCL and SDA signal lines need to operate in open-drain mode. The high level on these lines must be held by an external pull-up device, approximately 10 kOhm for operation at 100 kbit/s, approximately 2 kOhm for operation at 400 kbit/s.

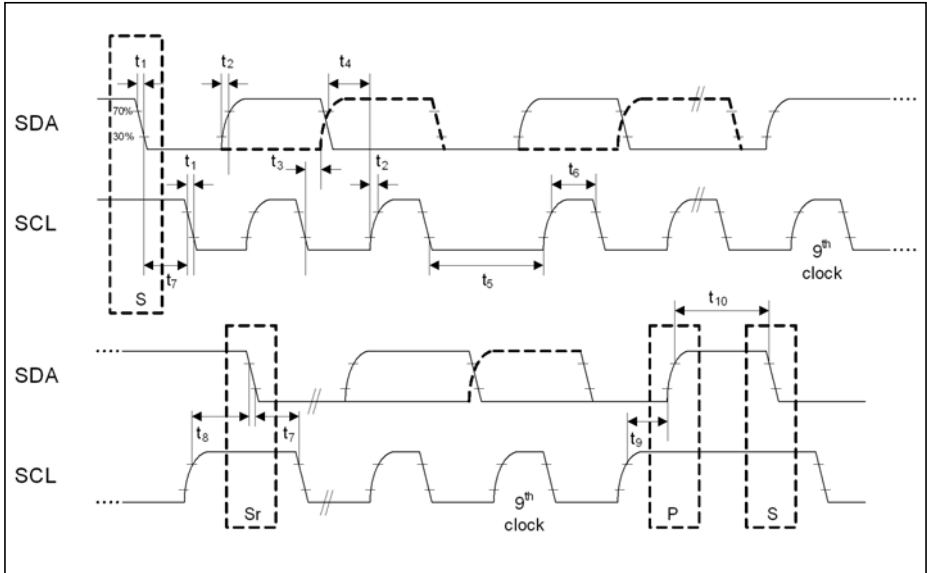
**Table 46 USIC IIC Fast Mode Timing<sup>1)</sup>**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Fall time of both SDA and SCL	$t_1$ CC/SR	20 + 0.1 * C <sub>b</sub> 2)	-	300	ns	
Rise time of both SDA and SCL	$t_2$ CC/SR	20 + 0.1 * C <sub>b</sub> 2)	-	300	ns	
Data hold time	$t_3$ CC/SR	0	-	-	μs	
Data set-up time	$t_4$ CC/SR	100	-	-	ns	
LOW period of SCL clock	$t_5$ CC/SR	1.3	-	-	μs	
HIGH period of SCL clock	$t_6$ CC/SR	0.6	-	-	μs	
Hold time for (repeated) START condition	$t_7$ CC/SR	0.6	-	-	μs	
Set-up time for repeated START condition	$t_8$ CC/SR	0.6	-	-	μs	
Set-up time for STOP condition	$t_9$ CC/SR	0.6	-	-	μs	
Bus free time between a STOP and START condition	$t_{10}$ CC/SR	1.3	-	-	μs	
Capacitive load for each bus line	C <sub>b</sub> SR	-	-	400	pF	

1) Due to the wired-AND configuration of an IIC bus system, the port drivers of the SCL and SDA signal lines need to operate in open-drain mode. The high level on these lines must be held by an external pull-up device, approximately 10 kOhm for operation at 100 kbit/s, approximately 2 kOhm for operation at 400 kbit/s.

2) C<sub>b</sub> refers to the total capacitance of one bus line in pF.





**Figure 34 USIC IIC Stand and Fast Mode Timing**

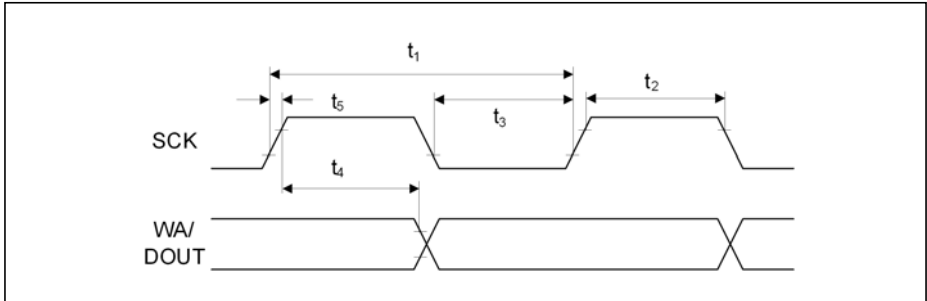
### 3.3.9.4 Inter-IC Sound (IIS) Interface Timing

The following parameters are applicable for a USIC channel operated in IIS mode.

*Note: These parameters are not subject to production test, but verified by design and/or characterization.*

**Table 47 USIC IIS Master Transmitter Timing**

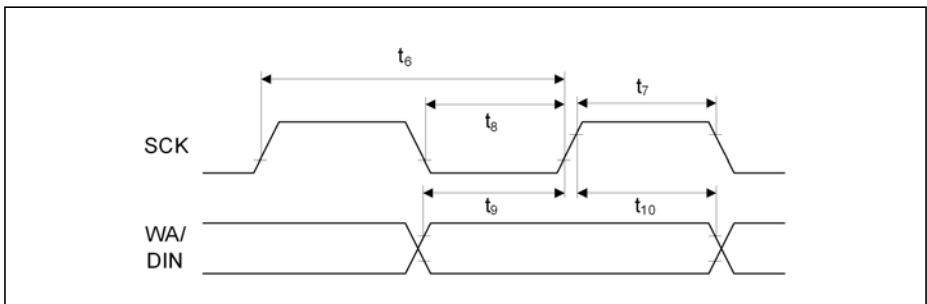
Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Clock period	$t_1$ CC	33.3	–	–	ns	
Clock high time	$t_2$ CC	0.35 x $t_{1min}$	–	–	ns	
Clock low time	$t_3$ CC	0.35 x $t_{1min}$	–	–	ns	
Hold time	$t_4$ CC	0	–	–	ns	
Clock rise time	$t_5$ CC	–	–	0.15 x $t_{1min}$	ns	



**Figure 35 USIC IIS Master Transmitter Timing**

**Table 48 USIC IIS Slave Receiver Timing**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Clock period	$t_6$ SR	66.6	–	–	ns	
Clock high time	$t_7$ SR	0.35 x $t_{6min}$	–	–	ns	
Clock low time	$t_8$ SR	0.35 x $t_{6min}$	–	–	ns	
Set-up time	$t_9$ SR	0.2 x $t_{6min}$	–	–	ns	
Hold time	$t_{10}$ SR	0	–	–	ns	



**Figure 36 USIC IIS Slave Receiver Timing**

### 3.3.9.5 SDMMC Interface Timing

Note: These parameters are not subject to production test, but verified by design and/or characterization.

Note: Operating Conditions apply, total external capacitive load  $C_L = 40$  pF.

#### AC Timing Specifications (Full-Speed Mode)

**Table 49 SDMMC Timing for Full-Speed Mode**

Parameter	Symbol	Values	Unit		Note/ Test Condition
			Min.	Max.	
Clock frequency in full speed transfer mode ( $1/t_{pp}$ )	$f_{pp}$ CC	0	24	MHz	
Clock cycle in full speed transfer mode	$t_{pp}$ CC	40	–	ns	
Clock low time	$t_{WL}$ CC	10	–	ns	
Clock high time	$t_{WH}$ CC	10	–	ns	
Clock rise time	$t_{TLH}$ CC	–	10	ns	
Clock fall time	$t_{THL}$ CC	–	10	ns	
Inputs setup to clock rising edge	$t_{ISU\_F}$ SR	2	–	ns	
Inputs hold after clock rising edge	$t_{IH\_F}$ SR	2	–	ns	
Outputs valid time in full speed mode	$t_{ODLY\_F}$ CC	–	10	ns	
Outputs hold time in full speed mode	$t_{OH\_F}$ CC	0	–	ns	

**Table 50 SD Card Bus Timing for Full-Speed Mode<sup>1)</sup>**

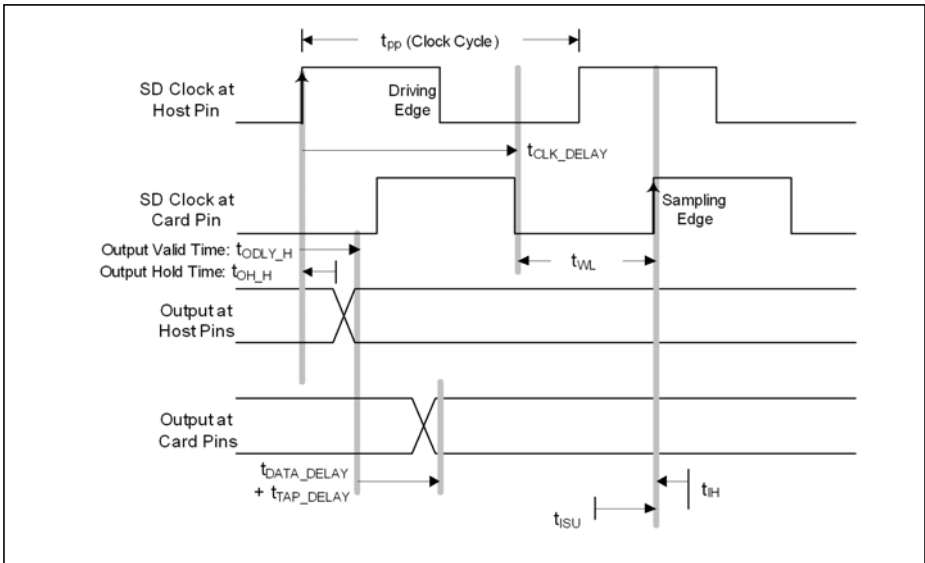
Parameter	Symbol	Values		Unit	Note/ Test Condition
		Min.	Max.		
SD card input setup time	$t_{ISU}$	5	–	ns	
SD card input hold time	$t_{IH}$	5	–	ns	

**Table 50 SD Card Bus Timing for Full-Speed Mode<sup>1)</sup> (cont'd)**

Parameter	Symbol	Values		Unit	Note/ Test Condition
		Min.	Max.		
SD card output valid time	$t_{ODLY}$	–	14	ns	
SD card output hold time	$t_{OH}$	0	–	ns	

1) Reference card timing values for calculation examples. Not subject to production test and not characterized.

**Full-Speed Output Path (Write)**



**Figure 37 Full-Speed Output Path**

**Full-Speed Write Meeting Setup (Maximum Delay)**

The following equations show how to calculate the allowed skew range between the SD\_CLK and SD\_DAT/CMD signals on the PCB.

No clock delay:

(1)

$$t_{ODLY\_F} + t_{DATA\_DELAY} + t_{TAP\_DELAY} + t_{ISU} < t_{WL}$$

With clock delay:

$$t_{ODLY\_F} + t_{DATA\_DELAY} + t_{TAP\_DELAY} + t_{ISU} < t_{WL} + t_{CLK\_DELAY} \quad (2)$$

$$t_{DATA\_DELAY} + t_{TAP\_DELAY} + t_{WL} < t_{PP} + t_{CLK\_DELAY} - t_{ISU} - t_{ODLY\_F} \quad (3)$$

$$t_{DATA\_DELAY} + t_{TAP\_DELAY} + 20 < 40 + t_{CLK\_DELAY} - 5 - 10$$

$$t_{DATA\_DELAY} < 5 + t_{CLK\_DELAY} - t_{TAP\_DELAY}$$

The data can be delayed versus clock up to 5 ns in ideal case of  $t_{WL} = 20$  ns.

### Full-Speed Write Meeting Hold (Minimum Delay)

The following equations show how to calculate the allowed skew range between the SD\_CLK and SD\_DAT/CMD signals on the PCB.

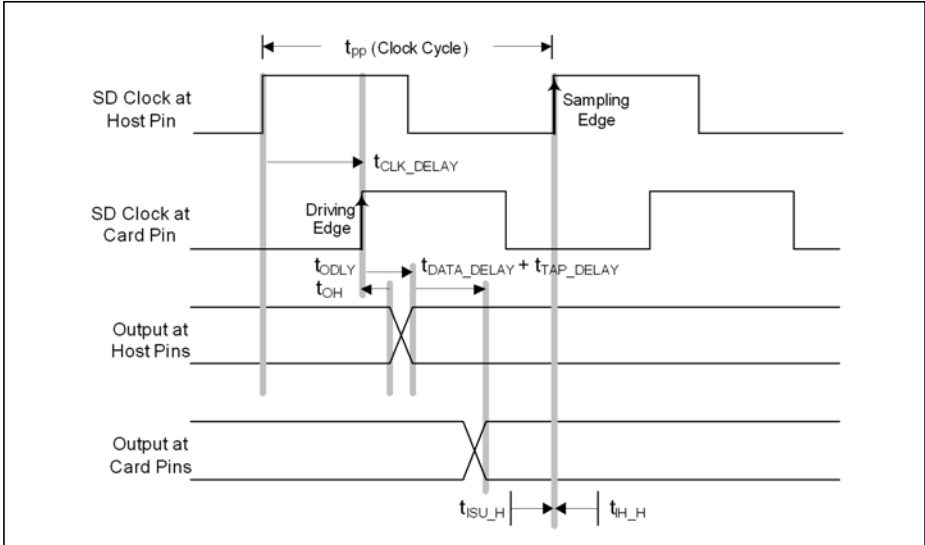
$$t_{CLK\_DELAY} < t_{WL} + t_{OH\_F} + t_{DATA\_DELAY} + t_{TAP\_DELAY} - t_{IH} \quad (4)$$

$$t_{CLK\_DELAY} < 20 + t_{DATA\_DELAY} + t_{TAP\_DELAY} - 5$$

$$t_{DATA\_DELAY} < 15 + t_{CLK\_DELAY} + t_{TAP\_DELAY}$$

The clock can be delayed versus data up to 18.2 ns (external delay line) in ideal case of  $t_{WL} = 20$  ns, with maximum  $t_{TAP\_DELAY} = 3.2$  ns programmed.

**Full-Speed Input Path (Read)**



**Figure 38 Full-Speed Input Path**

**Full-Speed Read Meeting Setup (Maximum Delay)**

The following equations show how to calculate the allowed combined propagation delay range of the SD\_CLK and SD\_DAT/CMD signals on the PCB.

(5)

$$t_{CLK\_DELAY} + t_{DATA\_DELAY} + t_{TAP\_DELAY} + t_{ODLY} + t_{ISU\_F} < 0.5 \times t_{pp}$$

$$t_{CLK\_DELAY} + t_{DATA\_DELAY} < 0.5 \times t_{pp} - t_{ODLY} - t_{ISU\_F} - t_{TAP\_DELAY}$$

$$t_{CLK\_DELAY} + t_{DATA\_DELAY} < 20 - 14 - 2 - t_{TAP\_DELAY}$$

$$t_{CLK\_DELAY} + t_{DATA\_DELAY} < 4 - t_{TAP\_DELAY}$$

The data + clock delay can be up to 4 ns for a 40 ns clock cycle.

**Electrical Parameters**

**Full-Speed Read Meeting Hold (Minimum Delay)**

The following equations show how to calculate the allowed combined propagation delay range of the SD\_CLK and SD\_DAT/CMD signals on the PCB.

(6)

$$t_{\text{CLK\_DELAY}} + t_{\text{OH}} + t_{\text{DATA\_DELAY}} + t_{\text{TAP\_DELAY}} > t_{\text{IH\_F}}$$

$$t_{\text{CLK\_DELAY}} + t_{\text{DATA\_DELAY}} > t_{\text{IH\_F}} - t_{\text{OH}} - t_{\text{TAP\_DELAY}}$$

$$t_{\text{CLK\_DELAY}} + t_{\text{DATA\_DELAY}} > 2 - t_{\text{TAP\_DELAY}}$$

The data + clock delay must be greater than 2 ns if  $t_{\text{TAP\_DELAY}}$  is not used.

If the  $t_{\text{TAP\_DELAY}}$  is programmed to at least 2 ns, the data + clock delay must be greater than 0 ns (or less). This is always fulfilled.

**AC Timing Specifications (High-Speed Mode)**

**Table 51 SDMMC Timing for High-Speed Mode**

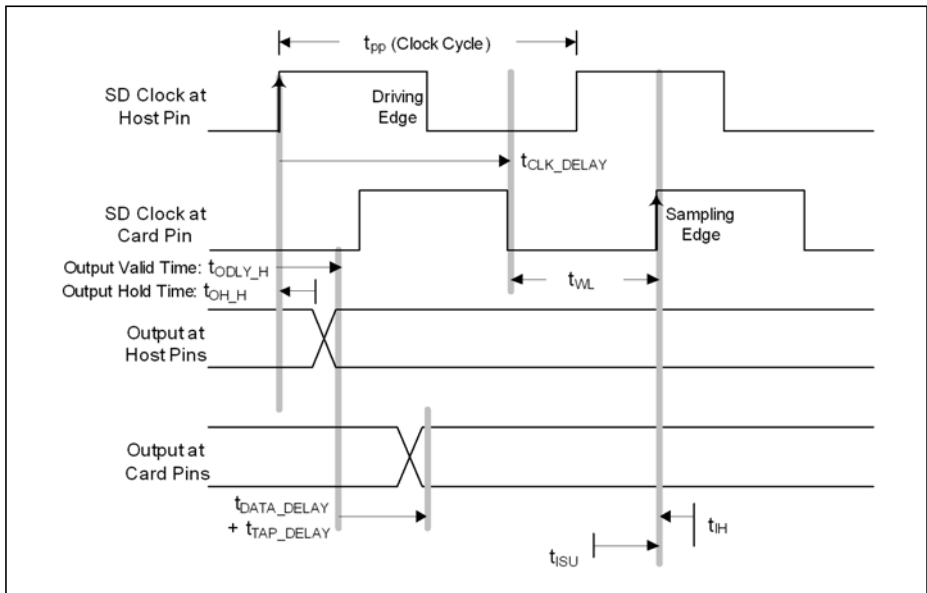
Parameter	Symbol		Values		Unit	Note/ Test Condition
			Min.	Max.		
Clock frequency in high speed transfer mode ( $1/t_{\text{pp}}$ )	$f_{\text{pp}}$	CC	0	48	MHz	
Clock cycle in high speed transfer mode	$t_{\text{pp}}$	CC	20	–	ns	
Clock low time	$t_{\text{WL}}$	CC	7	–	ns	
Clock high time	$t_{\text{WH}}$	CC	7	–	ns	
Clock rise time	$t_{\text{TLH}}$	CC	–	3	ns	
Clock fall time	$t_{\text{THL}}$	CC	–	3	ns	
Inputs setup to clock rising edge	$t_{\text{ISU\_H}}$	SR	2	–	ns	
Inputs hold after clock rising edge	$t_{\text{IH\_H}}$	SR	2	–	ns	
Outputs valid time in high speed mode	$t_{\text{ODLY\_H}}$	CC	–	14	ns	
Outputs hold time in high speed mode	$t_{\text{OH\_H}}$	CC	2	–	ns	

**Table 52 SD Card Bus Timing for High-Speed Mode<sup>1)</sup>**

Parameter	Symbol	Values		Unit	Note/ Test Condition
		Min.	Max.		
SD card input setup time	$t_{ISU}$	6	–	ns	
SD card input hold time	$t_{IH}$	2	–	ns	
SD card output valid time	$t_{ODLY}$	–	14	ns	
SD card output hold time	$t_{OH}$	2.5	–	ns	

1) Reference card timing values for calculation examples. Not subject to production test and not characterized.

### High-Speed Output Path (Write)



**Figure 39 High-Speed Output Path**

### High-Speed Write Meeting Setup (Maximum Delay)

The following equations show how to calculate the allowed skew between the SD\_CLK and SD\_DAT/CMD signals on the PCB.



**Electrical Parameters**

No clock delay:

$$t_{ODLY\_H} + t_{DATA\_DELAY} + t_{TAP\_DELAY} + t_{ISU} < t_{WL} \quad (7)$$

With clock delay:

$$t_{ODLY\_H} + t_{DATA\_DELAY} + t_{TAP\_DELAY} + t_{ISU} < t_{WL} + t_{CLK\_DELAY} \quad (8)$$

$$t_{DATA\_DELAY} + t_{TAP\_DELAY} - t_{CLK\_DELAY} < t_{WL} - t_{ISU} - t_{ODLY\_H} \quad (9)$$

$$t_{DATA\_DELAY} - t_{CLK\_DELAY} < t_{WL} - t_{ISU} - t_{ODLY\_H} - t_{TAP\_DELAY}$$

$$t_{DATA\_DELAY} - t_{CLK\_DELAY} < 10 - 6 - 14 - t_{TAP\_DELAY}$$

$$t_{DATA\_DELAY} - t_{CLK\_DELAY} < -10 - t_{TAP\_DELAY}$$

The data delay is less than the clock delay by at least 10 ns in the ideal case where  $t_{WL} = 10$  ns.

**High-Speed Write Meeting Hold (Minimum Delay)**

The following equations show how to calculate the allowed skew range between the SD\_CLK and SD\_DAT/CMD signals on the PCB.

$$t_{CLK\_DELAY} < t_{WL} + t_{OH\_H} + t_{DATA\_DELAY} + t_{TAP\_DELAY} - t_{IH} \quad (10)$$

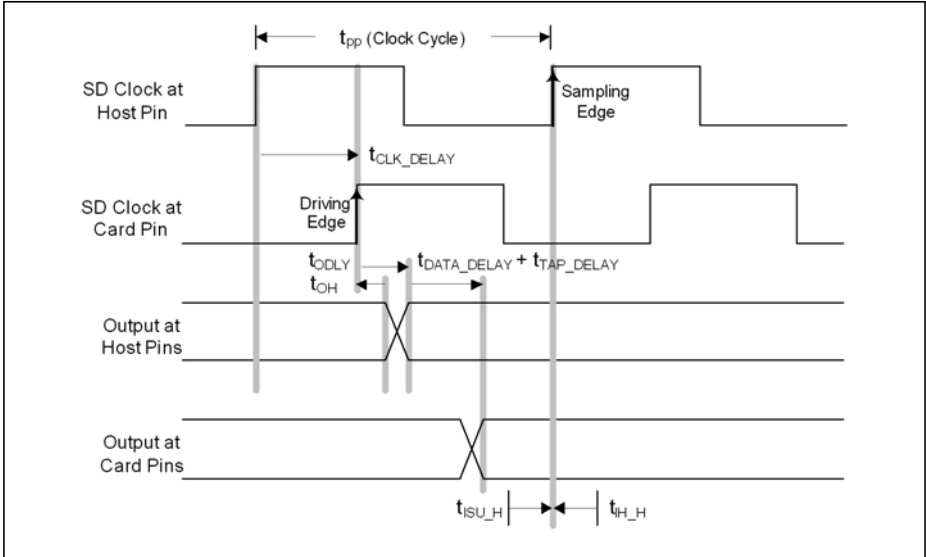
$$t_{CLK\_DELAY} - t_{DATA\_DELAY} < t_{WL} + t_{OH\_H} + t_{TAP\_DELAY} - t_{IH}$$

$$t_{CLK\_DELAY} - t_{DATA\_DELAY} < 10 + 2 + t_{TAP\_DELAY} - 2$$

$$t_{CLK\_DELAY} - t_{DATA\_DELAY} < 10 + t_{TAP\_DELAY}$$

The clock can be delayed versus data up to 13.2 ns (external delay line) in ideal case of  $t_{WL} = 10$  ns, with maximum  $t_{TAP\_DELAY} = 3.2$  ns programmed.

**High-Speed Input Path (Read)**



**Figure 40 High-Speed Input Path**

**High-Speed Read Meeting Setup (Maximum Delay)**

The following equations show how to calculate the allowed combined propagation delay range of the SD\_CLK and SD\_DAT/CMD signals on the PCB.

(11)

$$t_{CLK\_DELAY} + t_{DATA\_DELAY} + t_{TAP\_DELAY} + t_{ODLY} + t_{ISU\_H} < t_{pp}$$

$$t_{CLK\_DELAY} + t_{DATA\_DELAY} < t_{pp} - t_{ODLY} - t_{ISU\_H} - t_{TAP\_DELAY}$$

$$t_{CLK\_DELAY} + t_{DATA\_DELAY} < 20 - 14 - 2 - t_{TAP\_DELAY}$$

$$t_{CLK\_DELAY} + t_{DATA\_DELAY} < 4 - t_{TAP\_DELAY}$$

The data + clock delay can be up to 4 ns for a 20 ns clock cycle.

### High-Speed Read Meeting Hold (Minimum Delay)

The following equations show how to calculate the allowed combined propagation delay range of the SD\_CLK and SD\_DAT/CMD signals on the PCB.

(12)

$$t_{\text{CLK\_DELAY}} + t_{\text{OH}} + t_{\text{DATA\_DELAY}} + t_{\text{TAP\_DELAY}} > t_{\text{IH\_H}}$$

$$t_{\text{CLK\_DELAY}} + t_{\text{DATA\_DELAY}} > t_{\text{IH\_H}} - t_{\text{OH}} - t_{\text{TAP\_DELAY}}$$

$$t_{\text{CLK\_DELAY}} + t_{\text{DATA\_DELAY}} > 2 - 2.5 - t_{\text{TAP\_DELAY}}$$

$$t_{\text{CLK\_DELAY}} + t_{\text{DATA\_DELAY}} > -0.5 - t_{\text{TAP\_DELAY}}$$

The data + clock delay must be greater than -0.5 ns for a 20 ns clock cycle. This is always fulfilled.

### 3.3.10 EBU Timing

*Note: These parameters are not subject to production test, but verified by design and/or characterization.*

*Note: Operating Conditions apply, with Class A2 pins and  $C_L = 16$  pF.*

#### 3.3.10.1 EBU Asynchronous Timing

*Note: For each timing, the accumulated PLL jitter must be added separately.*

**Table 53 Common Timing Parameters for all Asynchronous Timings**

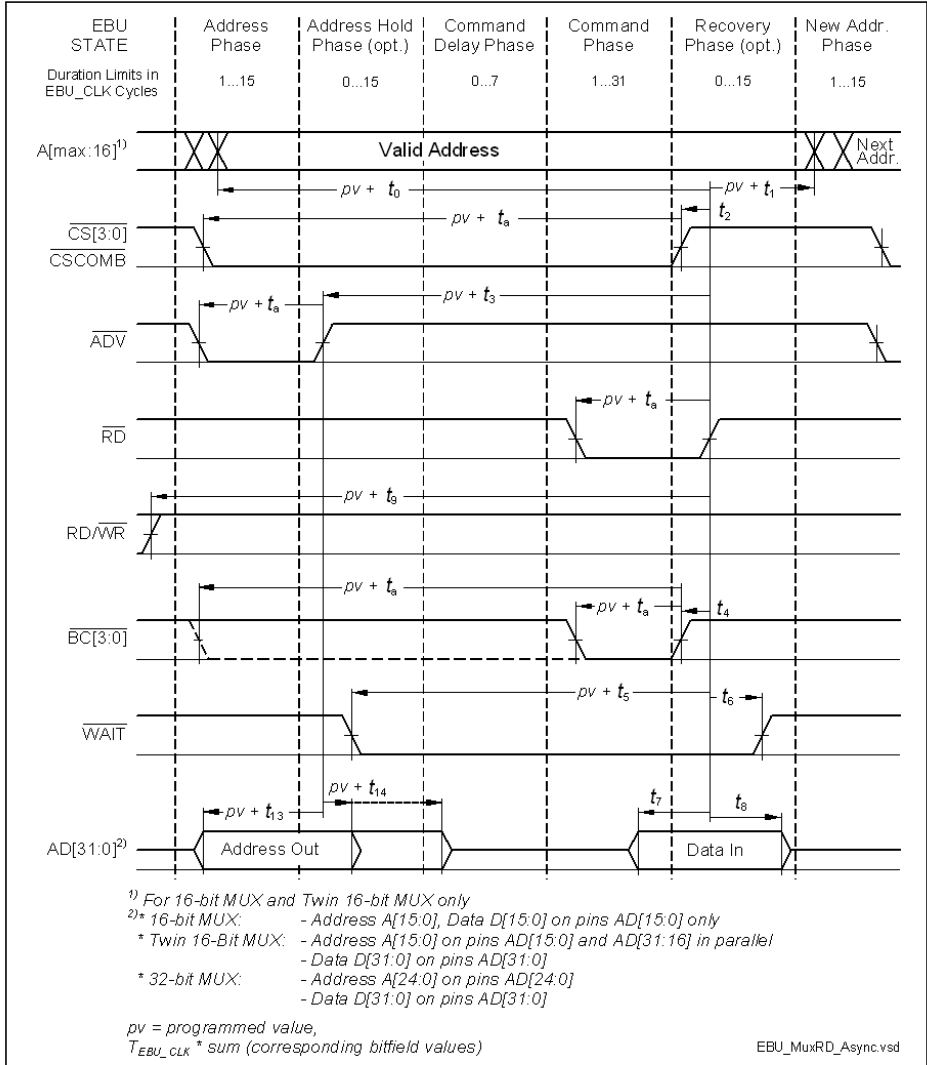
Parameter		Symbol	Limit Values		Unit	Edge Setting
			Min.	Max.		
Pulse width deviation from the ideal programmed width due to the A2 pad asymmetry, strong driver mode, rise delay - fall delay. $C_L = 16$ pF.	CC	$t_a$	-1	1.5	ns	sharp
			-2	1		medium
AD(24:16) output delay	to $\overline{\text{ADV}}$ rising edge, multiplexed read / write	CC	$t_{13}$	-5.5	2	–
AD(24:16) output delay		CC	$t_{14}$	-5.5	2	–

**Read Timing**

**Table 54 Asynchronous Read Timing, Multiplexed and Demultiplexed**

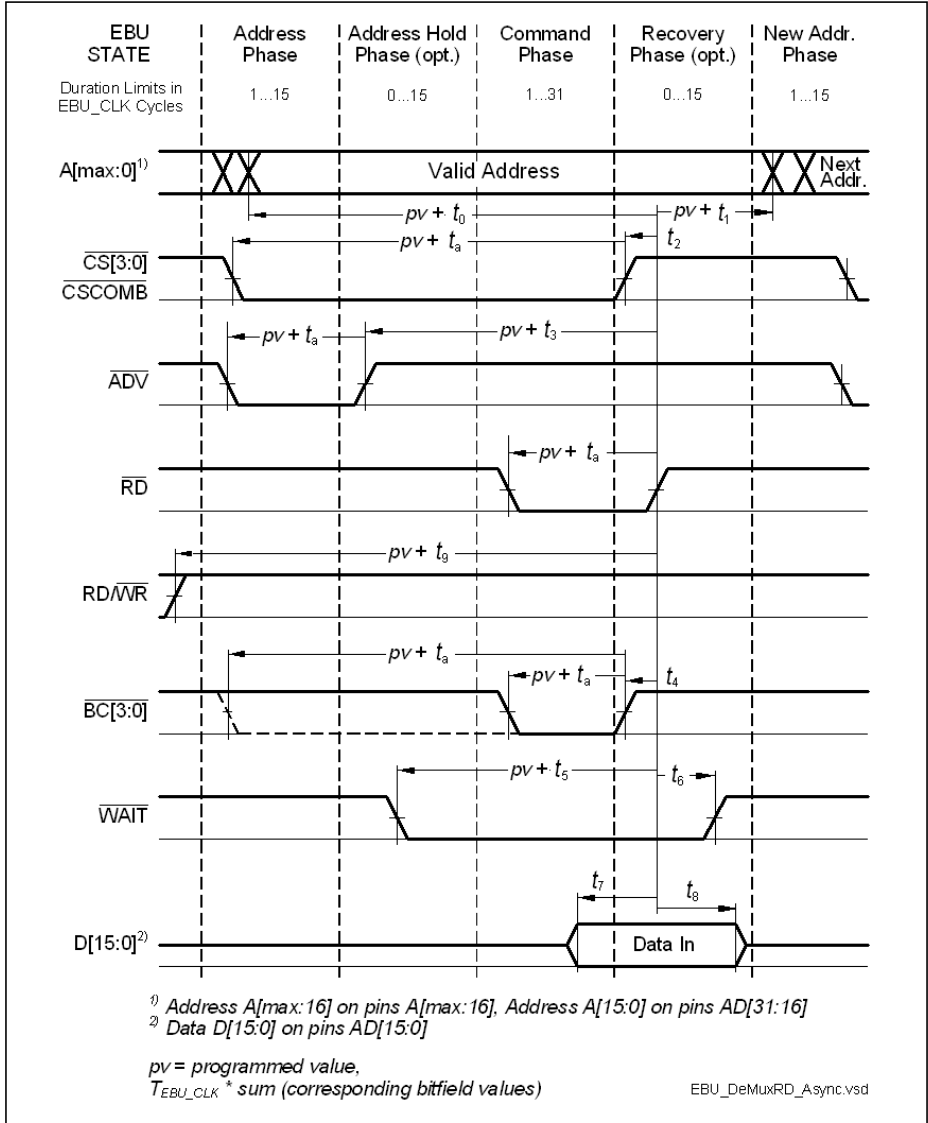
Parameter		Symbol	Limit Values		Unit	
			Min.	Max.		
A(24:16) output delay	to $\overline{RD}$ rising edge, deviation from the ideal programmed value.	CC	$t_0$	-2.5	2.5	ns
A(24:16) output delay		CC	$t_1$	-2.5	2.5	
$\overline{CS}$ rising edge		CC	$t_2$	-2	2.5	
$\overline{ADV}$ rising edge		CC	$t_3$	-1.5	4.5	
$\overline{BC}$ rising edge		CC	$t_4$	-2.5	2.5	
$\overline{WAIT}$ input setup		SR	$t_5$	12	–	
$\overline{WAIT}$ input hold		SR	$t_6$	0	–	
Data input setup		SR	$t_7$	12	–	
Data input hold		SR	$t_8$	0	–	
RD / $\overline{WR}$ output delay		CC	$t_9$	-2.5	1.5	

**Multiplexed Read Timing**



**Figure 41 Multiplexed Read Access**

Demultiplexed Read Timing



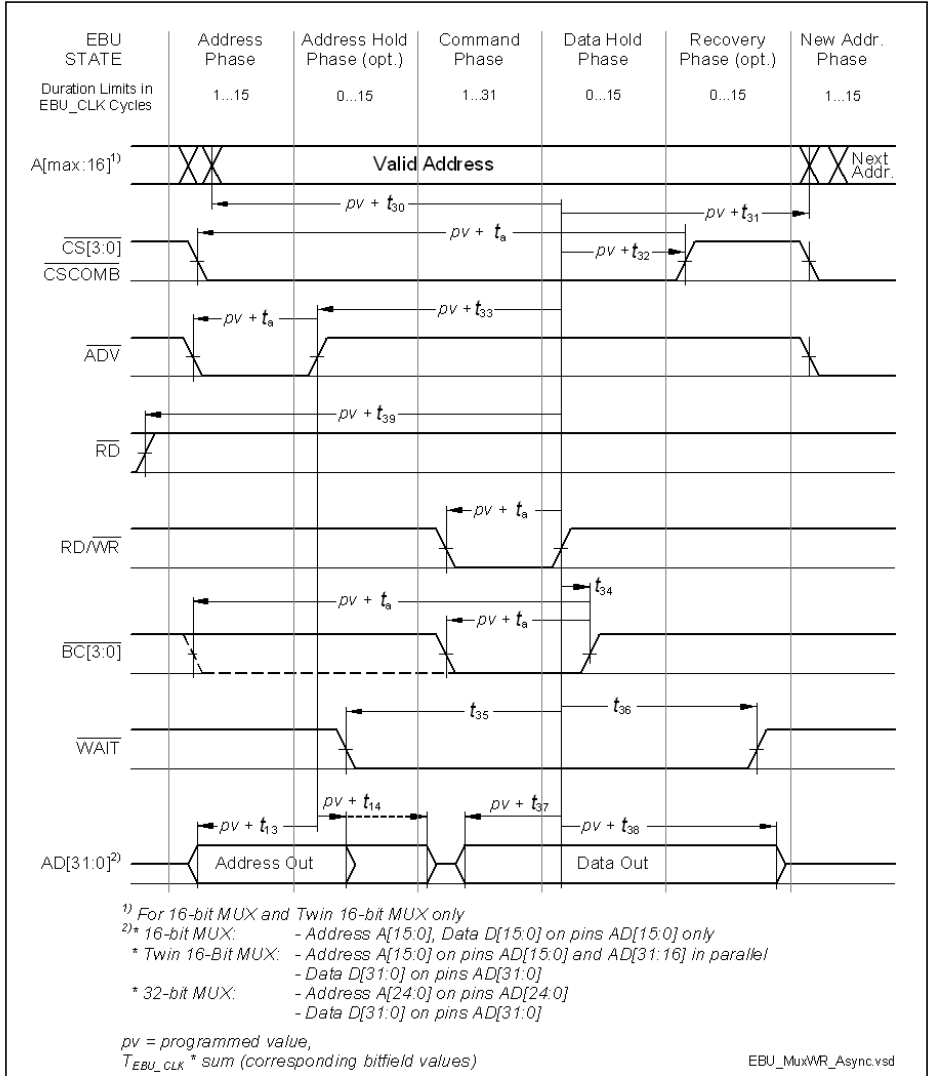
**Figure 42 Demultiplexed Read Access**

**Write Timing**

**Table 55 Asynchronous Write Timing, Multiplexed and Demultiplexed**

Parameter		Symbol	Limit Values		Unit
			Min.	Max.	
A(24:0) output delay	to RD/ $\overline{\text{WR}}$ rising edge, deviation from the ideal programmed value.	CC $t_{30}$	-2.5	2.5	ns
A(24:0) output delay		CC $t_{31}$	-2.5	2.5	
$\overline{\text{CS}}$ rising edge		CC $t_{32}$	-2	2	
$\overline{\text{ADV}}$ rising edge		CC $t_{33}$	-2	4.5	
$\overline{\text{BC}}$ rising edge		CC $t_{34}$	-2.5	2	
$\overline{\text{WAIT}}$ input setup		SR $t_{35}$	12	–	
$\overline{\text{WAIT}}$ input hold		SR $t_{36}$	0	–	
Data output delay		CC $t_{37}$	-5.5	2	
Data output delay		CC $t_{38}$	-5.5	2	
RD / $\overline{\text{WR}}$ output delay		CC $t_{39}$	-2.5	1.5	

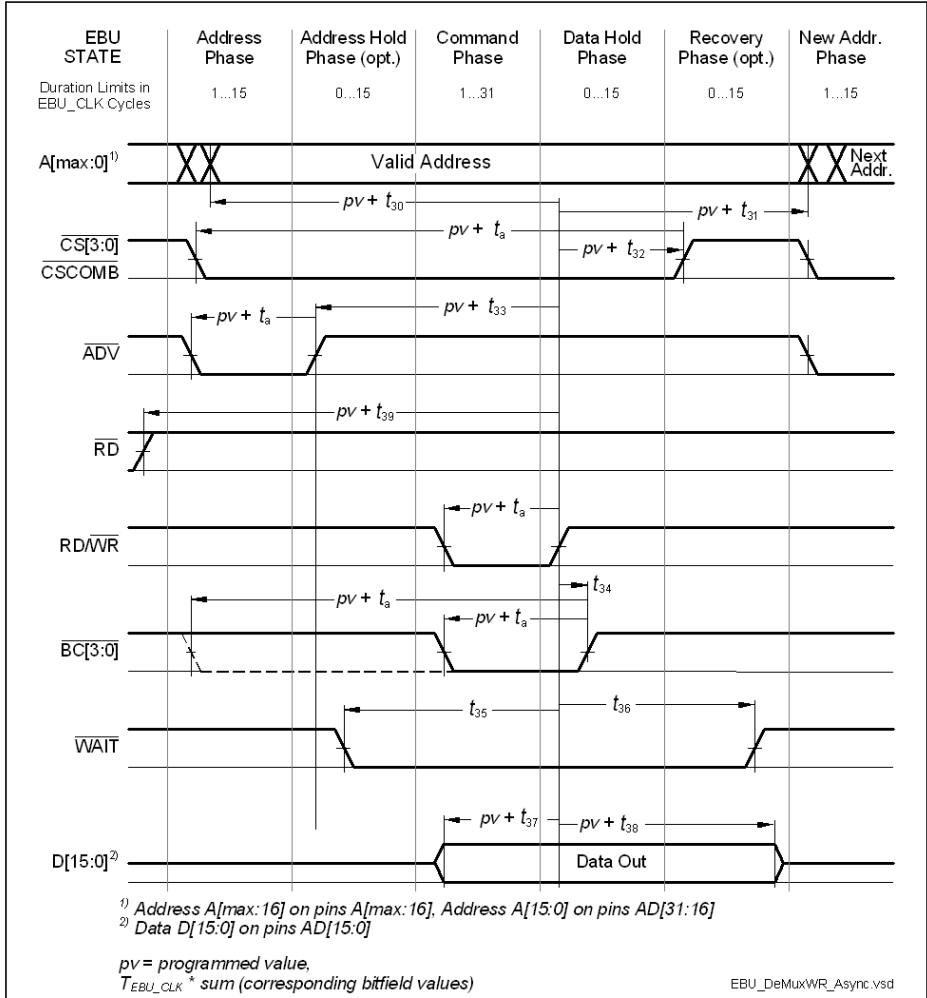
**Multiplexed Write Timing**



**Figure 43 Multiplexed Write Access**



**Demultiplexed Write Timing**



**Figure 44 Demultiplexed Write Access**

### 3.3.10.2 EBU Burst Mode Access Timing

*Note: These parameters are not subject to production test, but verified by design and/or characterization.*

*Note: Operating Conditions apply, with Class A2 pins and  $C_L = 16$  pF.*

**Table 56 EBU Burst Mode Read / Write Access Timing Parameters**

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
Output delay from BFCLKO rising edge	$t_{10}$	CC	-2	–	2	ns	–
$\overline{RD}$ and RD/W $\overline{R}$ active/inactive after BFCLKO active edge <sup>1)</sup>	$t_{12}$	CC	-2	–	2	ns	–
$\overline{CSx}$ output delay from BFCLKO active edge <sup>1)</sup>	$t_{21}$	CC	-2.5	–	1.5	ns	–
$\overline{ADV}$ active/inactive after BFCLKO active edge <sup>2)</sup>	$t_{22}$	CC	-2	–	2	ns	–
$\overline{BAA}$ active/inactive after BFCLKO active edge <sup>2)</sup>	$t_{22a}$	CC	-2.5	–	1.5	ns	–
Data setup to BFCLKI rising edge <sup>3)</sup>	$t_{23}$	SR	3	–	–	ns	–
Data hold from BFCLKI rising edge <sup>3)</sup>	$t_{24}$	SR	0	–	–	ns	–
$\overline{WAIT}$ setup (low or high) to BFCLKI rising edge <sup>3)</sup>	$t_{25}$	SR	3	–	–	ns	–
$\overline{WAIT}$ hold (low or high) from BFCLKI rising edge <sup>3)</sup>	$t_{26}$	SR	0	–	–	ns	–

1) An active edge can be a rising or falling edge, depending on the settings of bits BFCON.EBSE / ECSE and the clock divider ratio.

Negative minimum values for these parameters mean that the last data read during a burst may be corrupted. However, with clock feedback enabled, this value is an oversampling not required for the internal bus transaction, and will be discarded.

2) This parameter is valid for BUSCONx.EBSE = 1 and BUSAPx.EXTCLK = 00<sub>B</sub>.

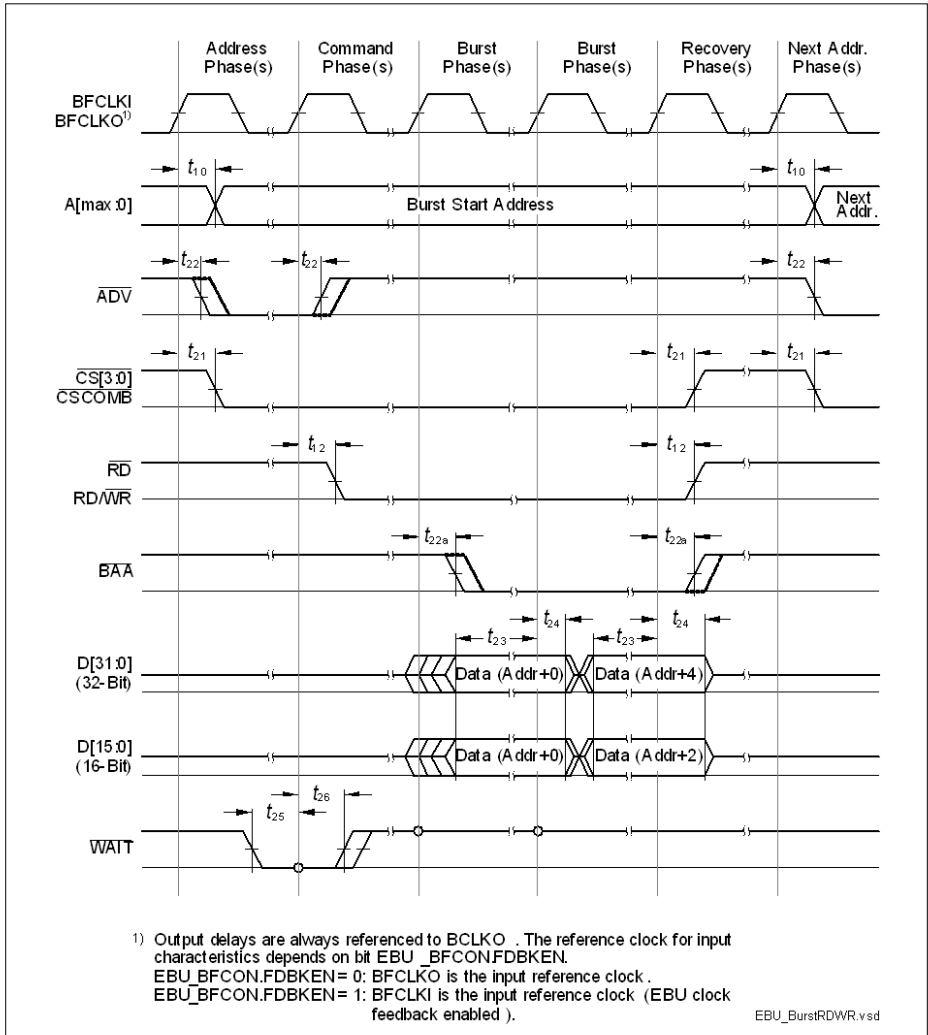
For BUSCONx.EBSE = 1 and other values of BUSAPx.EXTCLK, ADV and BAA will be delayed by 1/2 of the internal bus clock period  $T_{CPU} = 1 / f_{CPU}$ .

For BUSCONx. EBSE = 0 and BUSAPx.EXTCLK = 11<sub>B</sub>, add 2 internal bus clock periods.

For BUSCONx. EBSE = 0 and other values of BUSAPx.EXTCLK, add 1 internal bus clock period.

**Electrical Parameters**

3) If the clock feedback is not enabled, the input signals are latched using the internal clock in the same way as for asynchronous access. Thus,  $t_5$ ,  $t_6$ ,  $t_7$  and  $t_8$  from the asynchronous timing apply.



**Figure 45 EBU Burst Mode Read / Write Access Timing**

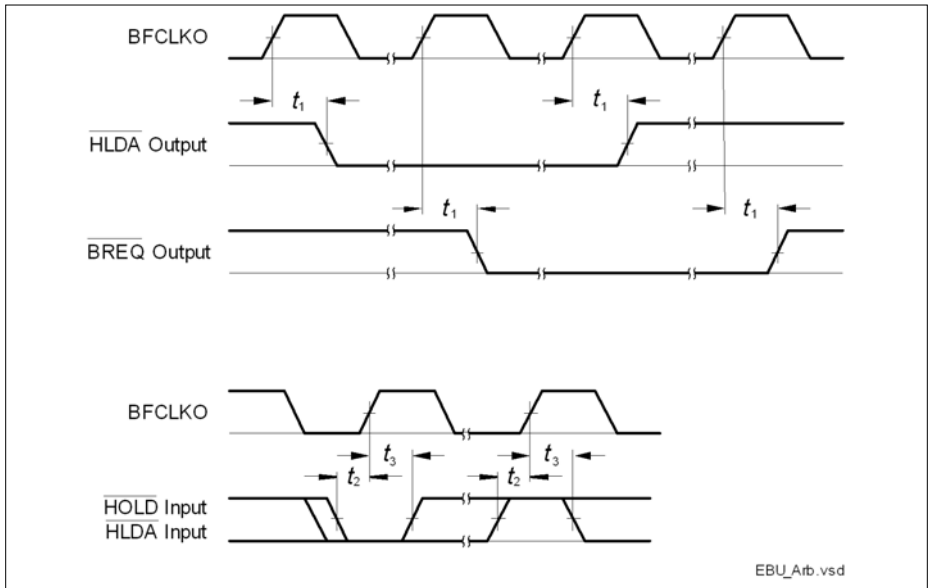
### 3.3.10.3 EBU Arbitration Signal Timing

*Note: These parameters are not subject to production test, but verified by design and/or characterization.*

*Note: Operating Conditions apply.*

**Table 57 EBU Arbitration Signal Timing Parameters**

Parameter	Symbol	CC	Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
Output delay from BFCLKO rising edge	$t_1$	CC	–	–	16	ns	$C_L = 50 \text{ pF}$
Data setup to BFCLKO falling edge	$t_2$	SR	11	–	–	ns	–
Data hold from BFCLKO falling edge	$t_3$	SR	2	–	–	ns	–



**Figure 46 EBU Arbitration Signal Timing**

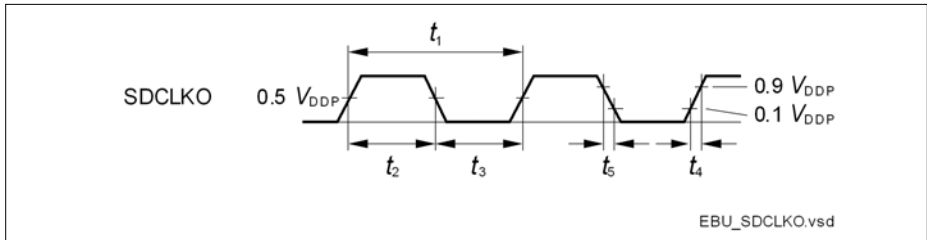
### 3.3.10.4 EBU SDRAM Access Timing

*Note: These parameters are not subject to production test, but verified by design and/or characterization.*

*Note: Operating Conditions apply, with Class A2 pins and  $C_L = 16$  pF.*

**Table 58 EBU SDRAM Access SDCLKO Signal Timing Parameters**

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
SDCLKO period	$t_1$	CC	12.5	–	–	ns	–
SDCLKO high time	$t_2$	SR	5.5	–	–	ns	–
SDCLKO low time	$t_3$	SR	3.75	–	–	ns	–
SDCLKO rise time	$t_4$	SR	–	–	3.0	ns	–
SDCLKO fall time	$t_5$	SR	–	–	3.0	ns	–

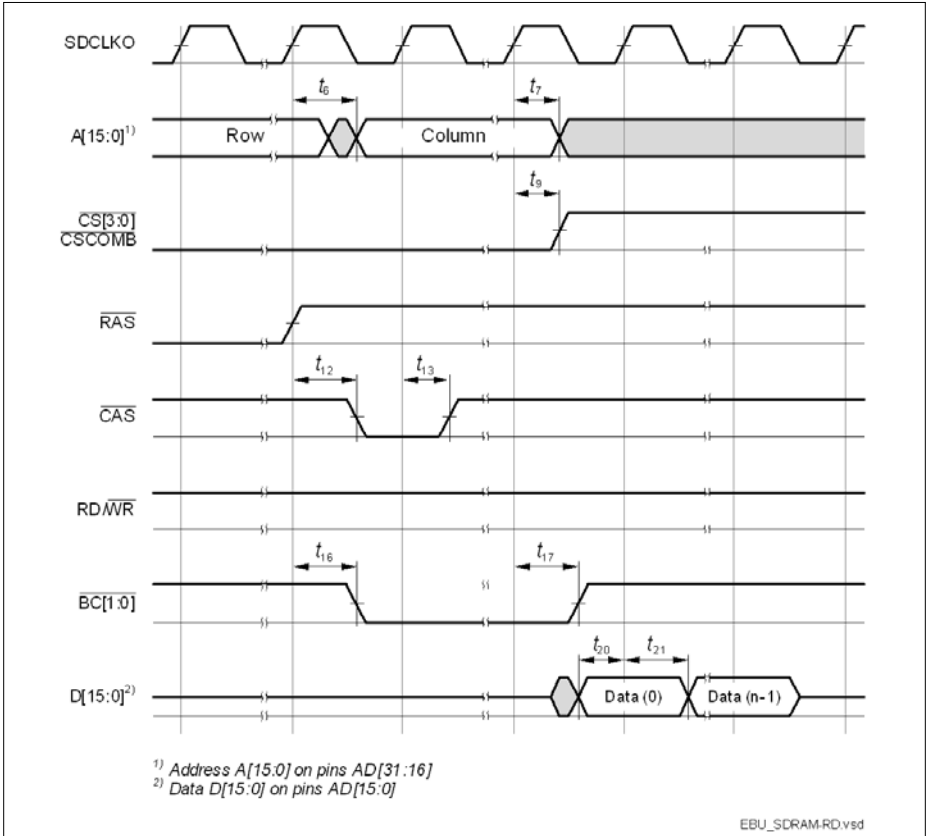


**Figure 47 EBU SDRAM Access CLKOUT Timing**

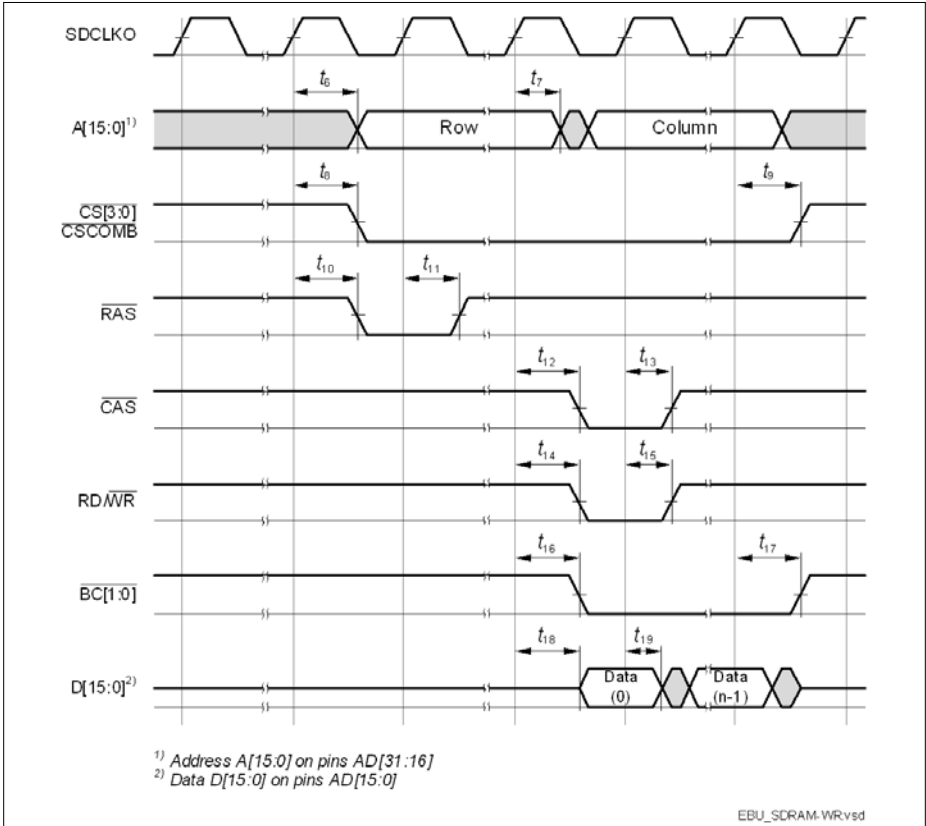
**Table 59 EBU SDRAM Access Signal Timing Parameters**

Parameter		Symbol	Limit Values		Unit
			Min.	Max.	
A(15:0) output valid	from SDCLKO low-to-high transition	CC $t_6$	–	9	ns
A(15:0) output hold		CC $t_7$	3	–	
$\overline{\text{CS}}(3:0)$ low		CC $t_8$	–	9	
$\overline{\text{CS}}(3:0)$ high		CC $t_9$	3	–	
$\overline{\text{RAS}}$ low		CC $t_{10}$	–	9	
$\overline{\text{RAS}}$ high		SR $t_{11}$	3	–	
$\overline{\text{CAS}}$ low		SR $t_{12}$	–	9	
$\overline{\text{CAS}}$ high		CC $t_{13}$	3	–	
$\overline{\text{RD}}/\overline{\text{WR}}$ low		CC $t_{14}$	–	9	
$\overline{\text{RD}}/\overline{\text{WR}}$ high		CC $t_{15}$	3	–	
$\overline{\text{BC}}(3:0)$ low		CC $t_{16}$	–	9	
$\overline{\text{BC}}(3:0)$ high		CC $t_{17}$	3	–	
D(15:0) output valid		CC $t_{18}$	–	9	
D(15:0) output hold		CC $t_{19}$	3	–	
CKE output valid <sup>1)</sup>		CC $t_{22}$	–	7	
CKE output hold <sup>1)</sup>		CC $t_{23}$	2	–	
D(15:0) input hold		SR $t_{21}$	3	–	
D(15:0) input setup to SDCLKO low-to-high transition	SR $t_{20}$	4	–		

1) Not depicted in the read and write access timing figures below.



**Figure 48 EBU SDRAM Read Access Timing**



**Figure 49 EBU SDRAM Write Access Timing**



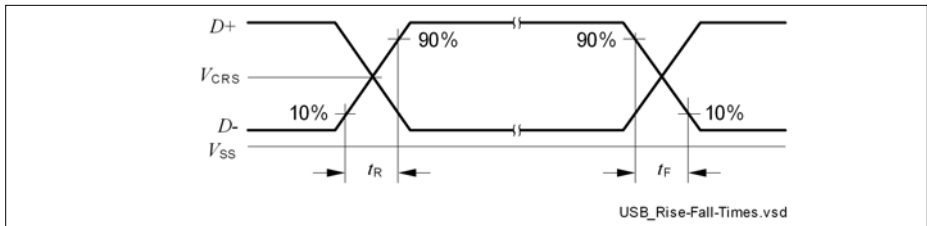
### 3.3.11 USB Interface Characteristics

The Universal Serial Bus (USB) Interface is compliant to the USB Rev. 2.0 Specification and the OTG Specification Rev. 1.3. High-Speed Mode is not supported.

*Note: These parameters are not subject to production test, but verified by design and/or characterization.*

**Table 60 USB Timing Parameters** (operating conditions apply)

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
Rise time	$t_R$	CC	4	–	20	ns	$C_L = 50$ pF
Fall time	$t_F$	CC	4	–	20	ns	$C_L = 50$ pF
Rise/Fall time matching	$t_R/t_F$	CC	90	–	111.11	%	$C_L = 50$ pF
Crossover voltage	$V_{CRS}$	CC	1.3	–	2.0	V	$C_L = 50$ pF



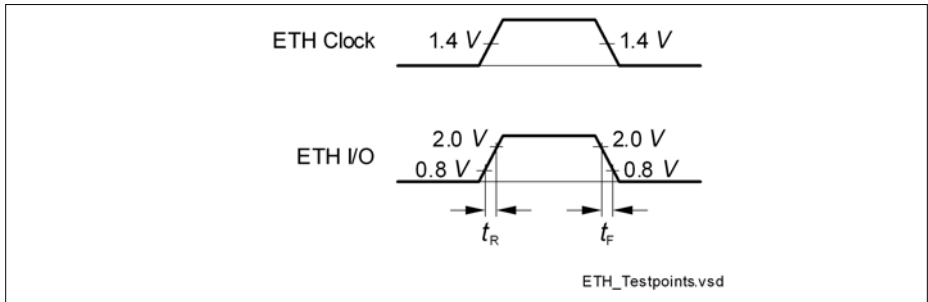
**Figure 50 USB Signal Timing**

### 3.3.12 Ethernet Interface (ETH) Characteristics

For proper operation of the Ethernet Interface it is required that  $f_{SYS} \geq 100$  MHz.

*Note: These parameters are not subject to production test, but verified by design and/or characterization.*

#### 3.3.12.1 ETH Measurement Reference Points

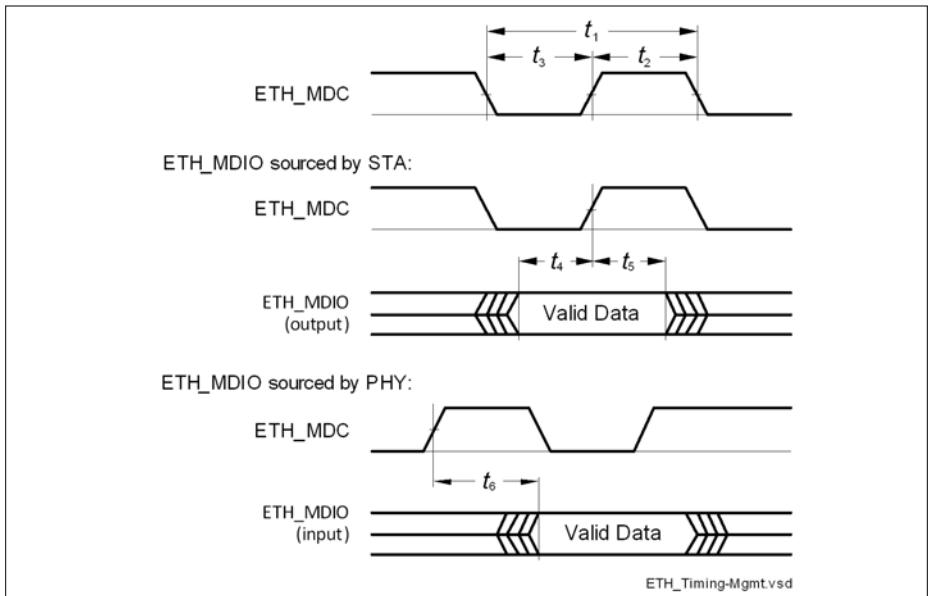


**Figure 51 ETH Measurement Reference Points**

**3.3.12.2 ETH Management Signal Parameters (ETH\_MDC, ETH\_MDIO)**

**Table 61 ETH Management Signal Timing Parameters**

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
ETH_MDC period	$t_1$	CC	400	–	–	ns	$C_L = 25 \text{ pF}$
ETH_MDC high time	$t_2$	CC	160	–	–	ns	
ETH_MDC low time	$t_3$	CC	160	–	–	ns	
ETH_MDIO setup time (output)	$t_4$	CC	10	–	–	ns	
ETH_MDIO hold time (output)	$t_5$	CC	10	–	–	ns	
ETH_MDIO data valid (input)	$t_6$	SR	0	–	300	ns	



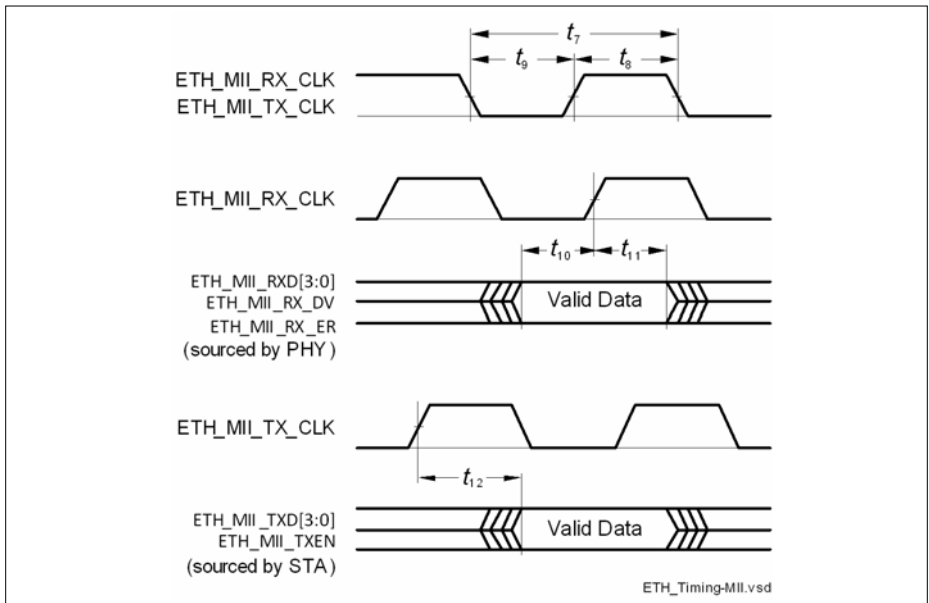
**Figure 52 ETH Management Signal Timing**

### 3.3.12.3 ETH MII Parameters

In the following, the parameters of the MII (Media Independent Interface) are described.

**Table 62 ETH MII Signal Timing Parameters**

Parameter	Symbol	SR	Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
Clock period, 10 Mbps	$t_7$	SR	400	–	–	ns	$C_L = 25 \text{ pF}$
Clock high time, 10 Mbps	$t_8$	SR	140	–	260	ns	
Clock low time, 10 Mbps	$t_9$	SR	140	–	260	ns	
Clock period, 100 Mbps	$t_7$	SR	40	–	–	ns	
Clock high time, 100 Mbps	$t_8$	SR	14	–	26	ns	
Clock low time, 100 Mbps	$t_9$	SR	14	–	26	ns	
Input setup time	$t_{10}$	SR	10	–	–	ns	
Input hold time	$t_{11}$	SR	10	–	–	ns	
Output valid time	$t_{12}$	CC	0	–	25	ns	



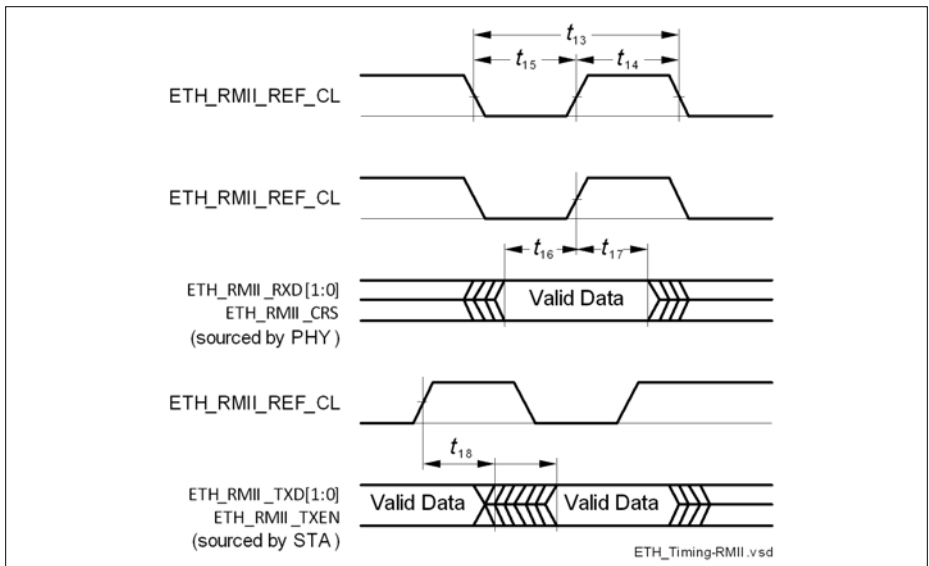
**Figure 53 ETH MII Signal Timing**

### 3.3.12.4 ETH RMII Parameters

In the following, the parameters of the RMII (Reduced Media Independent Interface) are described.

**Table 63 ETH RMII Signal Timing Parameters**

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
ETH_RMII_REF_CL clock period	$t_{13}$	SR	20	–	–	ns	$C_L = 25 \text{ pF}$ ; 50 ppm
ETH_RMII_REF_CL clock high time	$t_{14}$	SR	7	–	13	ns	$C_L = 25 \text{ pF}$
ETH_RMII_REF_CL clock low time	$t_{15}$	SR	7	–	13	ns	
ETH_RMII_RXD[1:0], ETH_RMII_CRS setup time	$t_{16}$	SR	4	–	–	ns	
ETH_RMII_RXD[1:0], ETH_RMII_CRS hold time	$t_{17}$	SR	2	–	–	ns	
ETH_RMII_TXD[1:0], ETH_RMII_TXEN data valid	$t_{18}$	CC	4	–	15	ns	



**Figure 54 ETH RMII Signal Timing**

## 4 Package and Reliability

The XMC4500 is a member of the XMC4000 Family of microcontrollers. It is also compatible to a certain extent with members of similar families or subfamilies.

Each package is optimized for the device it houses. Therefore, there may be slight differences between packages of the same pin-count but for different device types. In particular, the size of the Exposed Die Pad may vary.

If different device types are considered or planned for an application, it must be ensured that the board layout fits all packages under consideration.

### 4.1 Package Parameters

**Table 64** provides the thermal characteristics of the packages used in XMC4500.

**Table 64 Thermal Characteristics of the Packages**

Parameter	Symbol	Limit Values		Unit	Package Types
		Min.	Max.		
Exposed Die Pad Dimensions (including U-Groove where applicable)	$E_x \times E_y$ CC	-	$6.5 \times 6.5$	mm	PG-LQFP-144-24
		-	$7.0 \times 7.0$	mm	PG-LQFP-100-25
Exposed Die Pad Dimensions	-	-	$7.0 \times 7.0$	mm	PG-LQFP-100-29
		-	$6.5 \times 6.5$	mm	PG-LQFP-144-26
Thermal resistance Junction-Ambient $T_j \leq 150 \text{ }^\circ\text{C}$	$R_{\Theta JA}$ CC	-	40.5	K/W	PG-LFBGA-144-10
		-	19.5	K/W	PG-LQFP-144-24 <sup>1)</sup>
		-	21.0	K/W	PG-LQFP-100-25 <sup>1)</sup>
		-	21.0	K/W	PG-LQFP-100-29 <sup>1)</sup>
		-	19.5	K/W	PG-LQFP-144-26 <sup>1)</sup>

1) Device mounted on a 4-layer JEDEC board (JESD 51-7) with thermal vias; exposed pad soldered.

*Note: For electrical reasons, it is required to connect the exposed pad to the board ground  $V_{SS}$ , independent of EMC and thermal requirements.*

### 4.1.1 Thermal Considerations

When operating the XMC4500 in a system, the total heat generated in the chip must be dissipated to the ambient environment to prevent overheating and the resulting thermal damage.

The maximum heat that can be dissipated depends on the package and its integration into the target board. The “Thermal resistance  $R_{\Theta JA}$ ” quantifies these parameters. The power dissipation must be limited so that the average junction temperature does not exceed 150 °C.

The difference between junction temperature and ambient temperature is determined by  $\Delta T = (P_{INT} + P_{IOSTAT} + P_{IODYN}) \times R_{\Theta JA}$

The internal power consumption is defined as

$$P_{INT} = V_{DDP} \times I_{DDP} \text{ (switching current and leakage current).}$$

The static external power consumption caused by the output drivers is defined as

$$P_{IOSTAT} = \Sigma((V_{DDP} - V_{OH}) \times I_{OH}) + \Sigma(V_{OL} \times I_{OL})$$

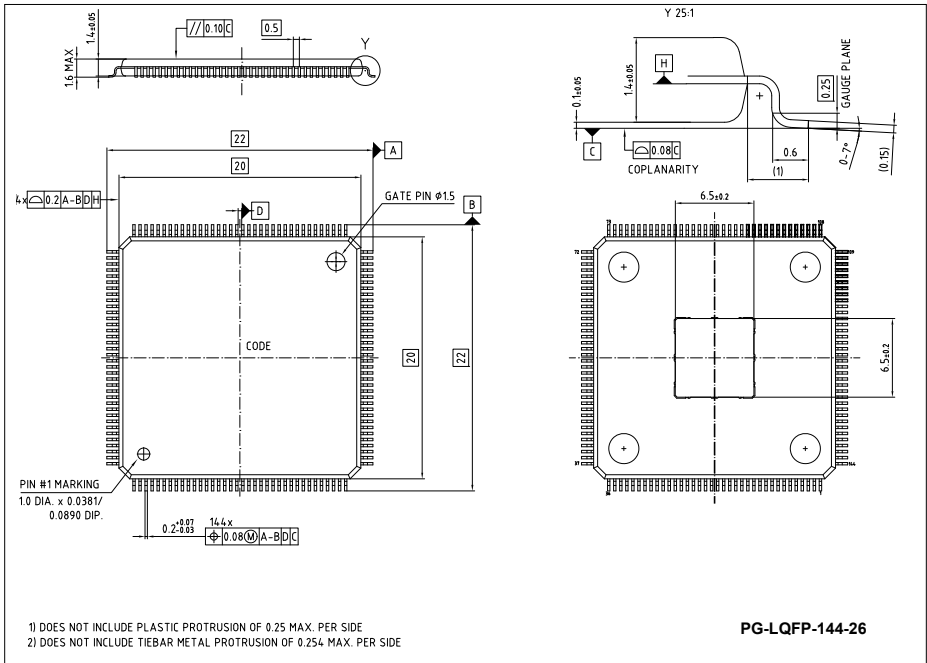
The dynamic external power consumption caused by the output drivers ( $P_{IODYN}$ ) depends on the capacitive load connected to the respective pins and their switching frequencies.

If the total power dissipation for a given system configuration exceeds the defined limit, countermeasures must be taken to ensure proper system operation:

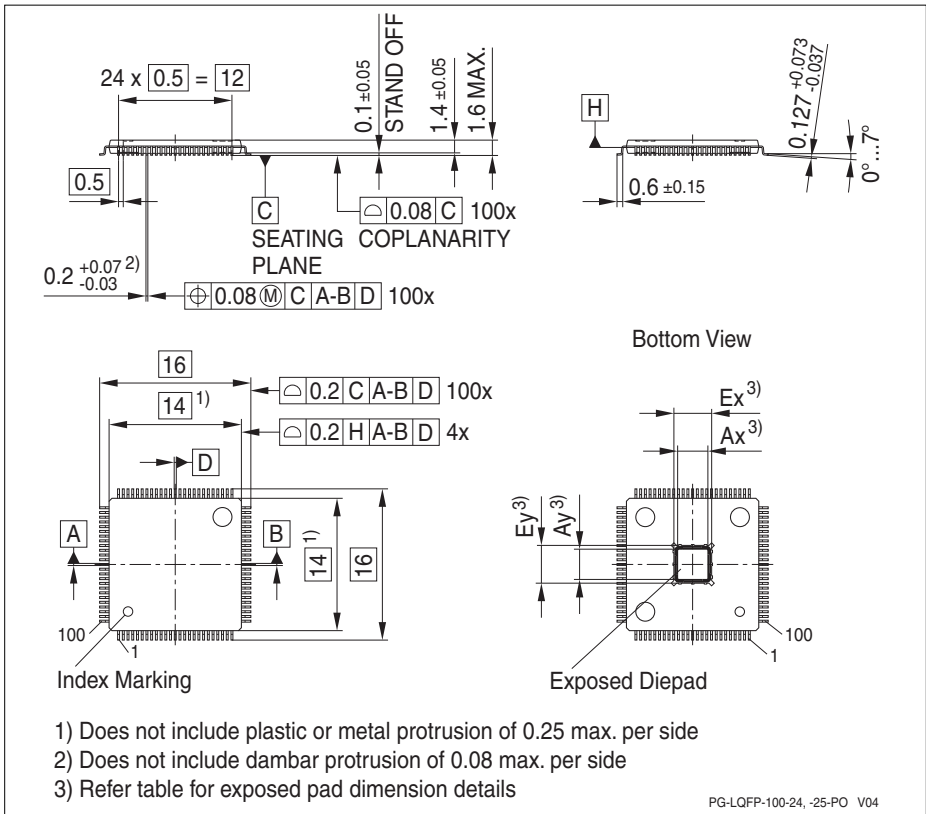
- Reduce  $V_{DDP}$ , if possible in the system
- Reduce the system frequency
- Reduce the number of output pins
- Reduce the load on active output drivers



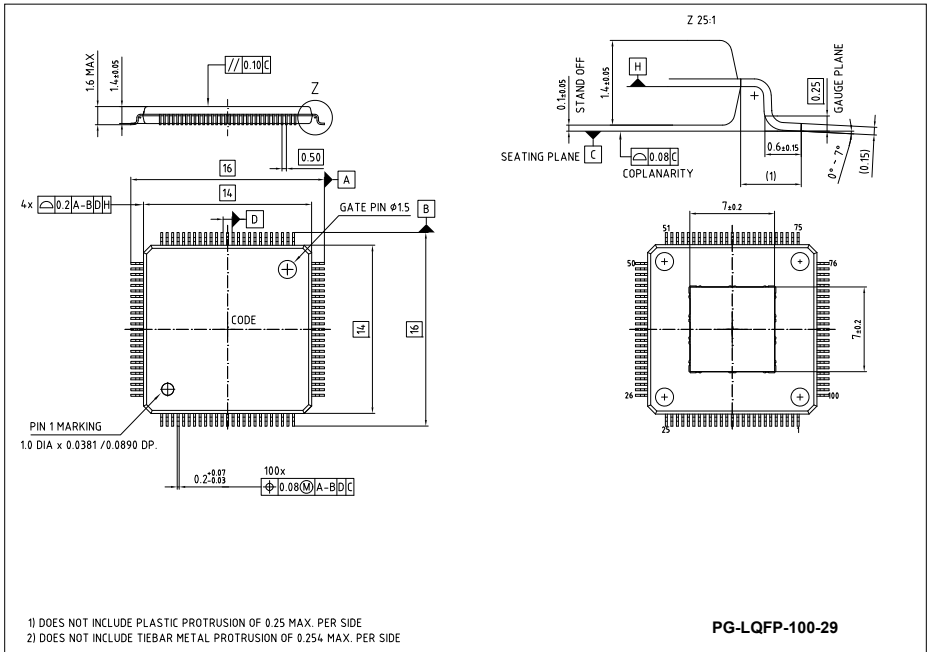




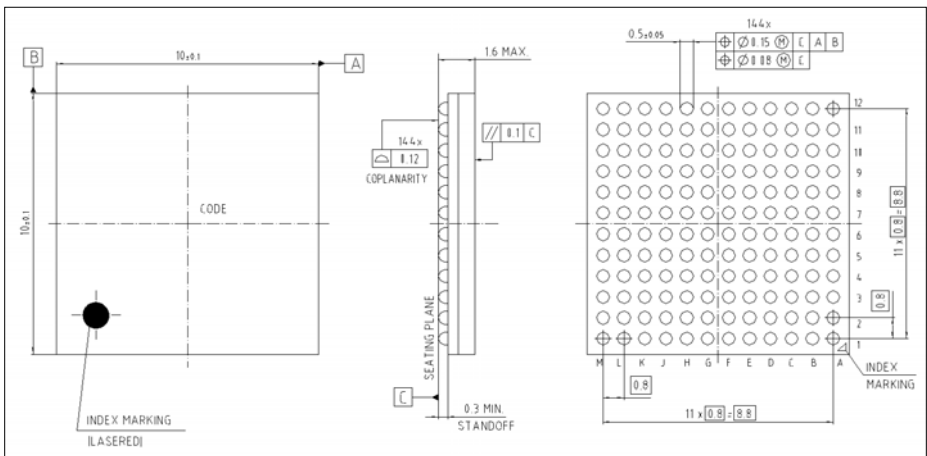
**Figure 56 PG-LQFP-144-26 (Plastic Green Low Profile Quad Flat Package)**



**Figure 57 PG-LQFP-100-25 (Plastic Green Low Profile Quad Flat Package)**



**Figure 58 PG-LQFP-100-29 (Plastic Green Low Profile Quad Flat Package)**



**Figure 59 PG-LFBGA-144-10 (Plastic Green Low Profile Fine Pitch Ball Grid Array)**

All dimensions in mm.

You can find complete information about Infineon packages, packing and marking in our Infineon Internet Page “Packages”: <http://www.infineon.com/packages>.

### 4.3 Quality Declarations

The qualification of the XMC4500 is executed according to the JEDEC standard JESD47H.

*Note: For automotive applications refer to the Infineon automotive microcontrollers.*

**Table 65 Quality Parameters**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Operation lifetime	$t_{OP}$ CC	20	–	–	a	$T_J \leq 109^\circ\text{C}$ , device permanent on
ESD susceptibility according to Human Body Model (HBM)	$V_{HBM}$ SR	–	–	2 000	V	EIA/JESD22-A114-B
ESD susceptibility according to Charged Device Model (CDM)	$V_{CDM}$ SR	–	–	500	V	Conforming to JESD22-C101-C
Moisture sensitivity level	$MSL$ CC	–	–	3	–	JEDEC J-STD-020D
Soldering temperature	$T_{SDR}$ SR	–	–	260	$^\circ\text{C}$	Profile according to JEDEC J-STD-020D

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